SiWN917 Wi-Fi® and Bluetooth® LE Network Co-Processor Connectivity Module Data Sheet

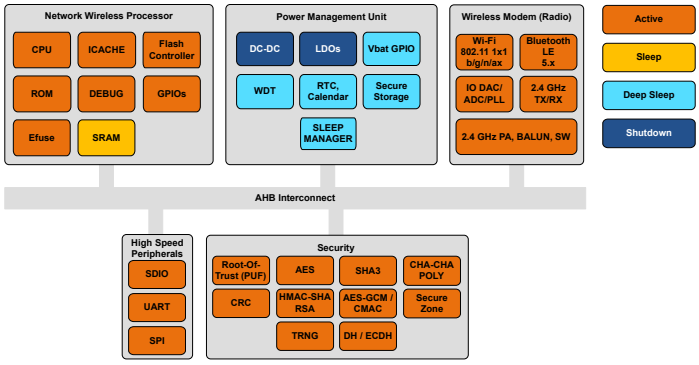
Silicon Labs SiWN917 Network Co-Processor Connectivity module is based on our SiWN917M, which is our lowest power Wi-Fi 6 silicon, ideal for ultra-low power IoT wireless devices using Wi-Fi®, Bluetooth, and IP networking for secure cloud connectivity. It has an integrated built-in wireless subsystem, advanced security, and integrated power-management. It has a multi-threaded Network Wireless Processor (NWP) running up to 160 MHz. All the networking and wireless stacks run on independent threads of the multi-threaded processor. SiWN917 includes an ultra-low power Wi-Fi 6 plus Bluetooth Low Energy (LE) 5.4 wireless CPU subsystem, baseband digital signal processing, analog front end, 2.4 GHz RF transceiver and integrated power amplifier, embedded SRAM, FLASH and power management subsystem all in a single 16 x 21.1 x 2.3 mm PCB module package thus providing a fully integrated solution that is ready for a wide range of embedded wireless IoT applications. The SiWN917 module is a complete solution offered with robust and fully-upgradeable software stacks, global regulatory certifications, advanced development and debugging tools, and documentation that simplifies and minimizes the development cycle of your end-product, helping to accelerate its time-to-market. The modules come with modular radio type approvals for various countries, including USA (FCC), Canada (IC/ISED) and Japan (MIC), and are in compliance with the relevant EN standards (including EN 300 328 v2.2.2) for the conformity with the directives and regulations in EU and UK.

SiWN917 applications include:

- Smart Home
- Security Cameras
- HVAC
- Smart Sensors
- Smart Appliances
- Health and Fitness
- Pet Tracker
- Smart Cities
- Smart Meters
- Industrial Wearable
- Smart Buildings
- Asset Tracking
- Smart hospitals

KEY FEATURES

- Wi-Fi 6 Single Band 2.4 GHz 20 MHz 1x1 stream IEEE 802.11 b/g/n/ax
- Bluetooth LE 5.4
- Wi-Fi 6 Benefits: TWT for improved efficiency and longer battery life, MU-MIMO/OFDMA for Higher Throughput, network capacity and low latency
- Best in Class Device and Wireless Security
- WLAN Tx power up to +17.5 dBm with integrated PA
- Bluetooth LE Tx power up to +17 dBm with integrated PA
- WLAN Rx sensitivity as low as -95.5 dBm
- Wi-Fi 4 Standby Associated mode current: 71 µA @ 1-second beacon listen interval
- In-package Flash up to 4MB
- Embedded Wi-Fi, Bluetooth LE and networking stacks supporting wireless coexistence
- Operating temperature: -40 to +85 ºC
- Operating supply range: 3.0 to 3.63 V
- Supply voltage for GPIOs: 1.71 to 3.63 V



1. Feature List

- **Memory**
  - Embedded Static Random Access Memory (SRAM) up to 672 KB total
  - Flash up to 4 MB (in-package)
- **Security**
  - Secure Boot
  - Secure firmware upgrade through boot-loader, Secure OTA.
  - Secure Key storage and HW device identity with PUF
  - Secure Zone
  - Encrypted XiP (Execute in place) from flash
  - Secure Attestation
  - Hardware Accelerators: Advanced Encryption Standard (AES) 128/256/192, Secure Hash Algorithm (SHA) 256/384/512, Hash Message Authentication Code (HMAC), Random Number Generator (RNG), Cyclic Redundancy Check (CRC), SHA3, AES-Galois Counter Mode (GCM)/ Cipher based Message Authentication Code (CMAC), Cha-Cha-poly, True Random Number Generator (TRNG)
  - Software Implementation: RSA, ECC
  - Anti Rollback
  - Debug Lock
- **Wi-Fi**[1]
  - Compliant to single-spatial stream IEEE 802.11 b/g/n/ax with single band (2.4 GHz) support
  - Support for 20 MHz channel bandwidth for 802.11n and 802.11ax
  - Operating Modes: Wi-Fi 4 STA, Wi-Fi 6 (802.11ax) STA, Wi-Fi 4 AP, Enterprise STA, Wi-Fi 6 STA + Wi-Fi 4 AP, Wi-Fi STA + BLE
  - Support for 802.11ax 20 MHz non-AP STA mandatory features (such as OFDMA, MU-MIMO) and optional features of individual Target wake-up time (iTWT), Broadcast TWT (bTWT), Intra PPDU power save, SU extended range (ER), DCM (Dual Carrier Modulation). DL MU-MIMO, DL/UL OFDMA, MBSSID, BFRP, Spatial Re-use , BSS Coloring, and NDP feedback up to 4 antennas
  - Transmit power up to +17.5 dBm with integrated PA
  - Receive sensitivity as low as -95.5 dBm
  - Data Rates: 802.11b: 1, 2, 5.5, 11 Mbps; 802.11g: 6, 9, 12, 18, 24, 36, 48, 54 Mbps ; 802.11n: MCS0 to MCS7; 802.11ax: MCS0 to MCS7
  - Operating Frequency Range [MHz]: 2412 - 2462 (North America, default), 2412 - 2472 (Europe, and other countries where applicable), 2412 - 2484 (Japan)
  - PTA Coexistence with Zigbee/Thread/Bluetooth
- **Host Interface Peripherals**
  - SPI - up to 100 MHz
  - SDIO[1] - up to 50 MHz
  - UART - up to 921600 Baud
- **Bluetooth**
  - Transmit power up to +17 dBm with integrated PA
  - Receive sensitivity — LE 1 Mbps: -94 dBm, LE 2 Mbps: -91.5 dBm, LR 500 kbps: -101.5 dBm, LR 125 kbps: -105.5 dBm
  - Operating Frequency Range: 2.402 - 2.480 GHz
  - Supports Bluetooth® Low Energy (LE): High Speed (1 Mbps and 2 Mbps) and Long Range (LE Coded PHYs, 125 kbps and 500 kbps; these are referred to as "LR" throughout this data sheet)
  - Extended Advertising
  - Extended Advertising scanning
  - Periodic Advertising
  - Periodic Advertising scanning
  - Periodic Advertising list
  - Periodic Advertising synchronization
  - Data length extensions
  - LL privacy 1.2
  - LE Secure connections
  - LE channel selection algorithm 2 (CSA#2)
  - LE dual role
  - BLE acceptlist
  - Two simultaneous BLE connections (2 peripheral or 2 central, or 1 central and 1 peripheral)
- **RF Features**
  - Integrated baseband processor with calibration memory
  - Integrated RF transceiver, high-power amplifier, balun and T/R switch
- **Embedded Wi-Fi Stack**[1]
  - Support for Embedded Wi-Fi STA mode, Wi-Fi Access point mode and Concurrent (AP+STA) mode
  - Supports advanced Wi-Fi Security features: WPA Personal, WPA2 Personal, WPA3 Personal, WPA/WPA2/WPA3 Enterprise in STA mode
  - Networking: Integrated IPv4/IPv6 stack, TCP, UDP, ICMP, ICMPv6, ARP, DHCP Client/Server, DHCPv6 Client/Server, DNS Client, SSL3.0/TLS1.3 Client, SNTP, mDNS, SNI
  - Applications: HTTP/s Client, HTTP/s Server, MQTT/s Client, AWS Client, Azure Client
  - Sockets: BSD Sockets, IoT Sockets
  - Over-the-Air (OTA) firmware update
  - Provisioning using Wi-Fi AP or BLE
- **Embedded Bluetooth Stack**
  - Support GAP profile
  - Support GATT profile
  - Support SMP
  - Support LE L2CAP
- **Wireless Sub-System Power Consumption**
  - Wi-Fi 4 Standby Associated mode current: 71 µA @ 1-second beacon listen interval
  - Wi-Fi 1 Mbps Listen current: 16.5 mA
  - Wi-Fi LP mode Rx current: 22 mA
  - Deep sleep current 4.5 µA, Standby current (352K RAM retention) 11 µA

- **Intelligent Power Management**
  - Power optimizations leveraging multiple power domains and partitioned sub systems
  - Many system-level, component-level, and circuit-level innovations and optimizations
  - Multiple Power Modes
  - Deep sleep mode with only timer active – with and without RAM retention
- **Software and Regulatory Certifications**
  - Wi-Fi Alliance: Wi-Fi 4, Wi-Fi 6
  - Bluetooth 5.4 Qualification
  - Regulatory certifications: FCC (USA), IC/ISED (Canada), CE (EU), UKCA (UK), MIC (Japan), KC (South Korea), NCC (Taiwan), SRRC (China), ACMA (Australia), RSM (New Zealand)
- **Operating Conditions**
  - Operating supply range: 3.0 to 3.63 V
  - Supply voltage for GPIOs: 1.71 to 3.63 V
  - Operating temperature: -40 to +85 ºC

Note:

1. For information about software roadmap features and lists of available features and profiles, contact Silicon Labs or refer to the Release Notes and Reference Manual.
2. All power and performance numbers are under ideal conditions.

2. Ordering Information

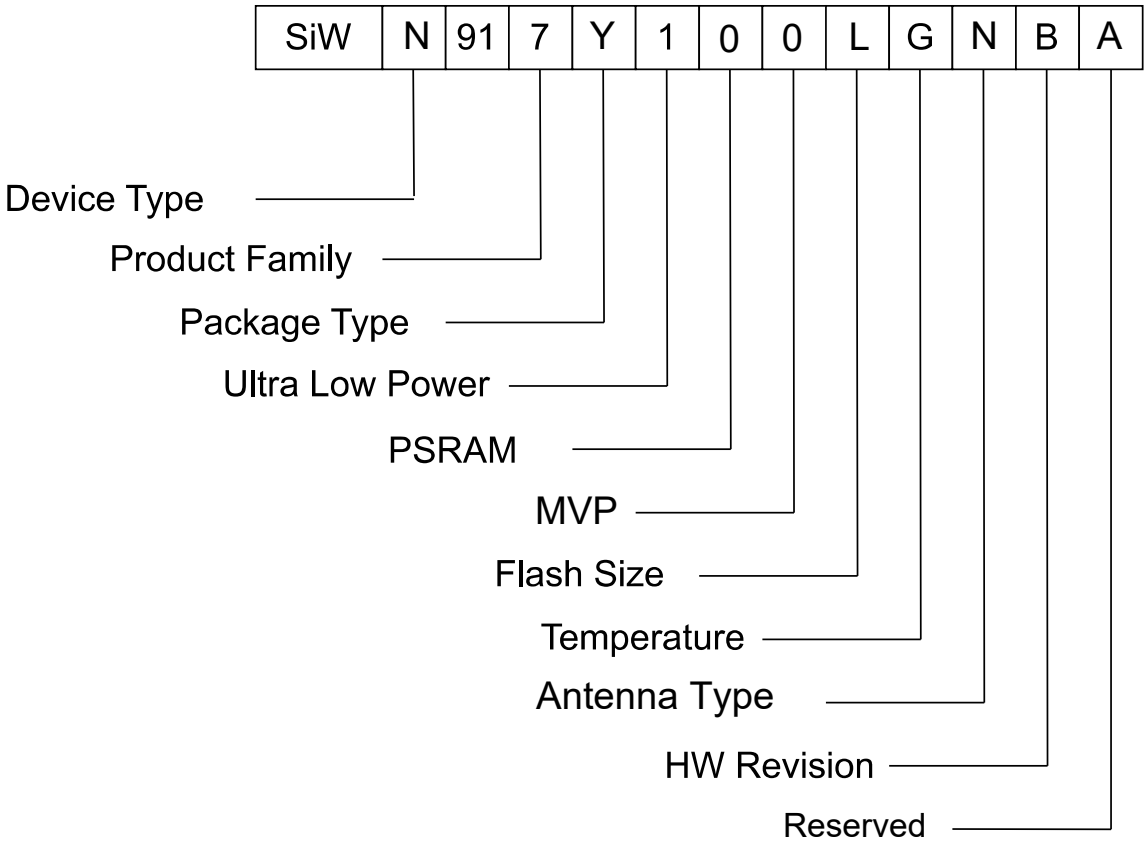


Figure 2.1. Ordering Guide

Table 2.1. Orderable Part Number (OPN) Decoder

Field	Options
Device Type	**T**: RCP (Transceiver) **N**: NCP **G**: SoC
Product Family	**7**: Ultra-low power
Package Type	**Y**: PCB Modules
Ultra-low Power	**1**: ULP Features enabled
PSRAM	**0**: No PSRAM Support **1**: External PSRAM **2**: 2 MB In-package PSRAM
MVP	**0**: MVP features disabled **1**: MVP Features enabled
Flash Size	**L**: 4 MB In-package Flash **M**: 8 MB In-package Flash

Field	Options
Temperature	**G**: -40 to +85 ºC
Antenna Type	**N**: No antenna **A**: Built-in antenna
HW Revision	**B**: Revision B
Reserved	**A**: Reserved

Table 2.2. Part Ordering Options

Ordering Code	Protocol Stack	Freq Band	Antenna	MWP	Flash/ RAM (kB)	GPIO	Temp Range	Pack-aging
SiWN917Y100LGNBA	BLE 5.4 Wi-Fi 6	2.4 GHz	No Anten-na	No	4 MB/ No PSRAM	43	-40 to +85 °C	Tape and Reel
SiWN917Y100LGABA	BLE 5.4 Wi-Fi 6	2.4 GHz	Built in Antenna	No	4 MB/ No PSRAM	43	-40 to +85 °C	Tape and Reel

Note:

1. Devices are shipped without firmware loaded. For custom parts with pre-loaded firmware, please contact Silicon Labs.
2. Throughout this document, the modules are referred to by their ordering codes above, or by their model names of SiW917Y1GN and SiW917Y1GA, respectively for the hardware variants with no antenna and with integral antenna, or by their marketing/friendly name of SiWN917.

Table of Contents

3. Applications

Smart Home

Smart Locks, Motion/Entrance Sensors, Water Leak sensors, Smart plugs/switches, Light Emitting Diode (LED) lights, Door-bell cameras, Washers/Dryers, Refrigerators, Thermostats, Consumer Security cameras, Voice Assistants, etc.

Other Consumer Applications

Toys, Anti-theft tags, Smart dispensers, Weighing scales, Fitness Monitors, Blood pressure monitors, Blood sugar monitors, Portable cameras, etc.

Other Applications (Medical, Industrial, Retail, Agricultural, Smart City, etc.)

Healthcare Tags, Industrial Wearables, Infusion pumps, Sensors/actuators in Manufacturing, Electronic Shelf labels, Agricultural sensors, Product tracking tags, Smart Meters, Parking sensors, Street LED lighting, Automotive After-market, Security Cameras, Gateways, etc.

4. Block Diagrams

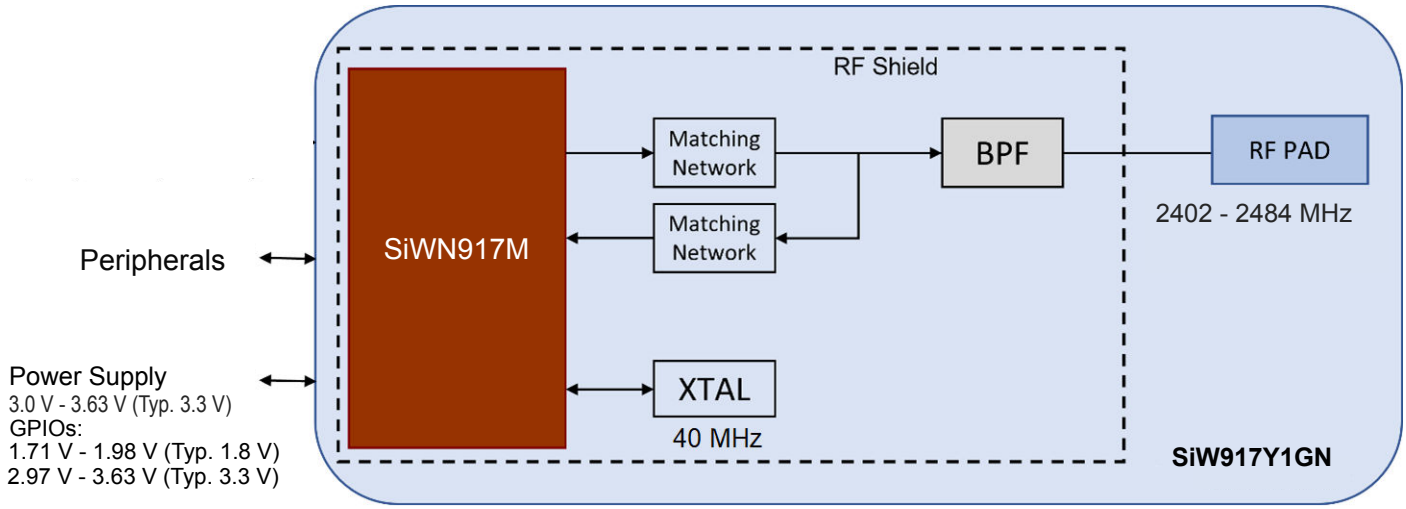


Figure 4.1. SiW917Y1GN (Without Antenna) Module Block Diagram

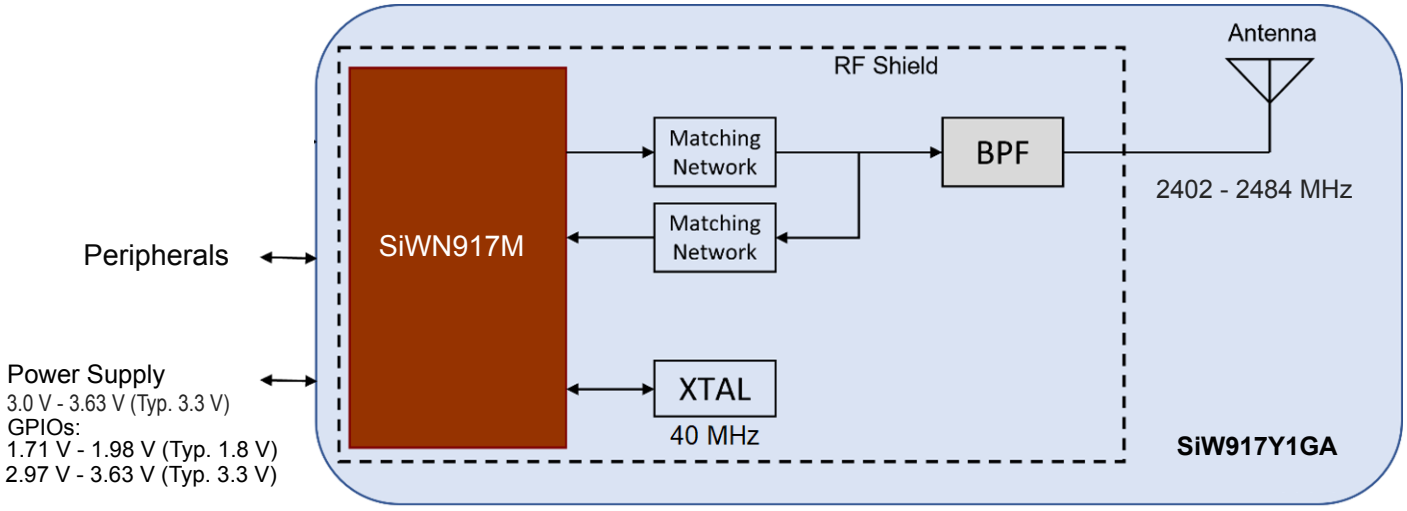


Figure 4.2. SiW917Y1GA (With Antenna) Module Block Diagram

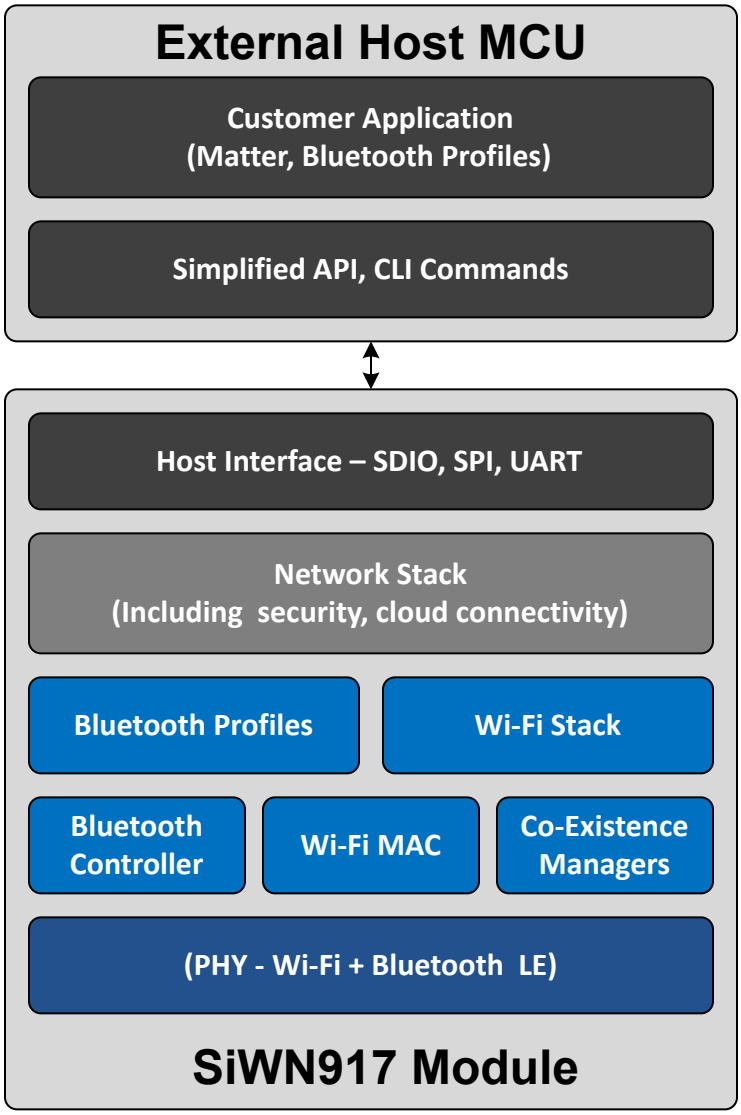


Figure 4.3. SiWN917 NCP Software Architecture

Note: Customer can connect multiple hosts, but only one host interface can be active after power-on.

5. System Overview

5.1 Introduction

When SiWN917 module operating in NCP mode, includes a four-threaded Network Wireless Processor (NWP) running at up to 160 MHz. All the networking and wireless stacks run on independent threads of the NWP. In addition, the NWP subsystem also acts as the secure processing domain and takes care of secure boot, secure firmware update and provides access to security accelerators and secure peripherals through pre-defined APIs. The NWP based "Networking, Security and Wireless subsystem" have power, clocks/ PLLs, bus-matrices, and memory.

5.2 WLAN

- Compliant to single-spatial stream IEEE 802.11 b/g/n/ax with single band (2.4 GHz) support
- Supports 20 MHz channel bandwidth for both 802.11n and 802.11ax modes.
- Operating Modes: Wi-Fi 4 STA, Wi-Fi 6 (802.11ax) STA, Wi-Fi 4 AP, Enterprise STA, Wi-Fi 6 STA + Wi-Fi 4 AP, Wi-Fi STA + BLE
- Wi-Fi 6 Features: Individual Target wake-up time (iTWT), Broadcast TWT (bTWT),SU extended range (ER), DCM (Dual Carrier Modulation), DL MU-MIMO, DL/UL OFDMA, MBSSID, BFRP, Spatial Re-use, BSS Coloring, and NDP feedback up to 4 antennas
- Integrated PA
- Data Rates — 802.11b: up to 11 Mbps; 802.11g: up to 54 Mbps; 802.11n: MCS0 to MCS7; 802.11ax: MCS0 to MCS7
- Operating Frequency Range [MHz]: 2412 - 2462 (North America, default), 2412 - 2472 (Europe, and other countries where applicable), 2412 - 2484 (Japan)

5.2.1 MAC

- Conforms to IEEE 802.11b/g/n/ax standards for MAC
- Hardware accelerators for AES
- WPA, WPA2, WPA3 and WMM support
- AMPDU aggregation for high performance
- Firmware downloaded from host based on application
- Hardware accelerators for DH (for WPS) and ECDH

5.2.2 Baseband Processing

- Supports 11b: DSSS for 1, 2 Mbps and CCK for 5.5, 11 Mbps
- Supports all OFDM data rates:
  - 802.11g: 6, 9, 12, 18, 24, 36, 48, 54 Mbps
  - 802.11ax, 802.11n: MCS 0 to MCS 7
- High-performance multipath handling in OFDM, DSSS, and CCK modes

5.3 Bluetooth

Key Features

- Transmit power up to +17 dBm with integrated PA
- Receive sensitivity — LE 1 Mbps: -94 dBm, LE 2 Mbps: -91.5 dBm, LR 500 kbps: -101.5 dBm, LR 125 kbps: -105.5 dBm
- Operating Frequency Range: 2.402 - 2.480 GHz
- Supports Bluetooth® Low Energy (LE): High Speed (1 Mbps and 2 Mbps) and Long Range (LE Coded PHYs, 125 kbps and 500 kbps; these are referred to as "LR" throughout this data sheet)
- Extended Advertising
- Extended Advertising scanning
- Periodic Advertising
- Periodic Advertising scanning
- Periodic Advertising list
- Periodic Advertising synchronization
- Data length extensions
- LL privacy 1.2
- LE Secure connections
- LE channel selection algorithm 2 (CSA#2)
- LE dual role
- BLE acceptlist
- Two simultaneous BLE connections (2 peripheral or 2 central, or 1 central and 1 peripheral)

5.3.1 MAC

Link Manager

- Creation, modification & release of physical links
- Connection establishment between Link managers of two Bluetooth devices
- Link supervision is implemented in Link Manager
- Link power control is done depending on the inputs from Link Controller
- Enabling & disabling of encryption & decryption on logical links
- AES hardware acceleration

Link Controller

- Encodes and decodes header of BLE packets
- Manages flow control, acknowledgment, re-transmission requests, etc.
- Stores the last packet status for all physical transports
- Indicates the success status of packet transmission to upper layers
- Indicates the link quality to the LMP layer

Device Manager

- Executes HCI Commands
- Controls Scan & Connection processes
- Controls all BLE Device operations except data transport operations
- BLE Controller state transition management
- Anchor point synchronization & management
- Scheduler

5.3.2 Baseband Processing

- Supports BLE 1 Mbps, 2 Mbps and Long Range 125 kbps, 500 kbps

5.4 RF Transceiver

- The SiWN917 features two highly configurable RF transceivers supporting WLAN 11b/g/n/ax and Bluetooth LE wireless protocols. Both RF transceivers together operating in multiple modes covering High Performance (HP) and Low Power (LP) operations. List of operating modes are given in next section.
- It contains two fully integrated fractional-N frequency synthesizers having reference from internal oscillator with 40 MHz crystal. One of the synthesizer is a low power architecture which also caters single-bit data modulation feature for Bluetooth LE protocols.

5.4.1 Receiver and Transmitter Operating Modes

The available radio operating modes are as follows:

- WLAN HP TX - WLAN High-Performance Transmitter
- WLAN HP RX - WLAN High-Performance Receiver
- WLAN LP RX - WLAN Low-Power Receiver
- BLE HP TX - Bluetooth LE High-Performance Transmitter
- BLE HP RX - Bluetooth LE High-Performance Receiver
- BLE LP TX - Bluetooth LE Low-Power Transmitter
- BLE LP RX - Bluetooth LE Low-Power Receiver

Note: All the TX / RX modes are automatically controlled by radio firmware and not individually selectable.

5.5 Host Interfaces

Three host interfaces are supported:

- SDIO
  - Version 2.0-compatible
  - Supports SD-SPI
  - 1-bit, and 4-bit SDIO modes
  - Operation up to a maximum clock speed of 50 MHz
- SPI
  - Operation up to a maximum clock speed of 100 MHz
- UART
  - Supports various baud rates up to 921600 bps

5.5.1 Auto Host Detection

The SiWN917 detects the host interface automatically after connecting to respective host controllers like SDIO, SPI, UART. The SDIO / SPI host interface is detected through hardware packet exchanges. The UART host interface is detected through the software based on received packets on the UART interface. This Host configuration is stored in always-on domain registers after detection (on power up) and the information is reused at each wakeup.

5.6 Security Features

- Secure Boot
- Secure OTA Firmware update
- TRNG: Generates high-entropy random numbers based on RF noise, increasing the effort/time needed to expose secret keys
- Secure Zone
- Secure Key storage: HW device identity and key storage with PUF
- Debug Lock
- Anti Rollback: Firmware downgrade to a lower security version is prohibited through OTP bits to prevent the use of older, potentially vulnerable and/or potentially uncompliant FW version
- Encrypted XIP from flash with XTS/CTR mode
- Secure Attestation: Allows a device to authenticate its identity using a cryptographically signed token and exchange of secret keys
- Hardware Accelerators: AES128/256/192, SHA256/384/512, HMAC, RNG, CRC, SHA3, AES-GCM/ CMAC, ChaCha-poly
- Software Implementation: RSA and ECC

5.7 Embedded Wi-Fi Software

- The wireless software package supports Embedded Wi-Fi (802.11 b/g/n/ax) Client mode, Wi-Fi Access point mode (up to 4 clients), and Enterprise Security in client mode.
- The software package includes complete firmware and application profiles.
- It has a wireless coexistence manager to arbitrate between protocols.

5.7.1 Security

Wireless software supports multiple levels of security capabilities available for the development of IoT devices.

- Accelerators: AES128/256
- WPA/WPA2/WPA3-Personal, WPA/WPA2/WPA3 Enterprise for Client

5.8 Power Architecture

The Power Control Hardware implements the control sequences for transitioning between different power states (Active/Standby/Sleep/Shutdown).

5.8.1 Highlights

- Two integrated buck switching regulators (High performance and ULP) to enable efficient Voltage Scaling across wide operating mode currents ranging from <1 µA to 170 mA
- Multiple voltage domains with Independent voltage scaling of each domain.
- Fine grained power-gating including peripherals, buses and pads, thereby reducing power consumption when the peripheral/buses/pads are inactive.
- Flexible switching between different Active states with controls from Software.
- Hardware based wakeup from Standby/Sleep/Shutdown states.
- All the peripherals are clock gated by default thereby reducing the power consumption in inactive state.
- Low wakeup times as configurable by Software.

5.8.2 System Power Supply Configurations

SiWN917 module support highly flexible power supply configurations for various application scenarios. Two application scenarios are listed below.

- 3.3 V single supply - A single 3.3 V supply derived from the system PMU can be input to all I/O supplies.
- 1.8 V and 3.3 V supply - A 1.8 V supply derived from the system PMU can be input to all I/O supplies except VBATT. A 3.3 V supply derived from system Power Management Unit (PMU) can be fed to the power amplifier supply pin VBATT.

5.8.3 Power Management

The SiWN917 module have an internal power management subsystem, including DC-DC converters and linear regulators. This subsystem generates all the voltages required by the module to operate from a wide variety of input sources.

- Input voltage (3.3 V) on pin VBATT
- Input voltage (1.8 V or 3.3 V) on pin IO_VDD, SDIO_IO_VDD and ULP_IO_VDD
- Input voltage (1.8 V) on pin FLASH_IO_VDD
- Nominal Output - 1.8 V and 48 mA maximum load on pin 1V8_LDO

5.9 Memory Architecture

There are on chip Read Only Memory(ROM), Random Access Memory(RAM) and in-package flash connectivity. Sizes of ROM/RAM/flash will vary depending on the chip configuration.

The NWP processor has the following memory:

- Embedded SRAM up to 672 KB total
- 448 KB of ROM which holds the Secure primary bootloader, Network Stack, Wireless stacks and security functions
- 16 KB of Instruction cache (I cache)
- Flash up to 4 MB (in-package)
- eFuse of 1024 bytes (used to store primary boot configuration, security and calibration parameters)

5.10 Low Power Modes

It supports ultra-low power consumption with multiple power modes to reduce system energy consumption.

- Voltage and Frequency Scaling
- Deep sleep (ULP) mode with only the sleep timer active – with and without RAM retention
- Wi-Fi standby associated mode with automatic periodic wake-up
- Automatic clock gating of the unused blocks or transit the system from Normal to ULP mode.

5.10.1 ULP Mode

In Ultra Low Power mode, the deep sleep manager has control over the processors and subsystems and controls their active and sleep states. During deep sleep, the always-on logic domain operates on a lowered supply and a low-frequency clock to reduce power consumption. The ULP mode supports the following wake-up options:

- Timeout wakeup - Exit sleep state after programmed timeout value.
- GPIO Based Wakeup: Exit sleep state when GPIO goes High/Low based on programmed polarity.

6. Pinout and Pin Description

6.1 Pin Diagram

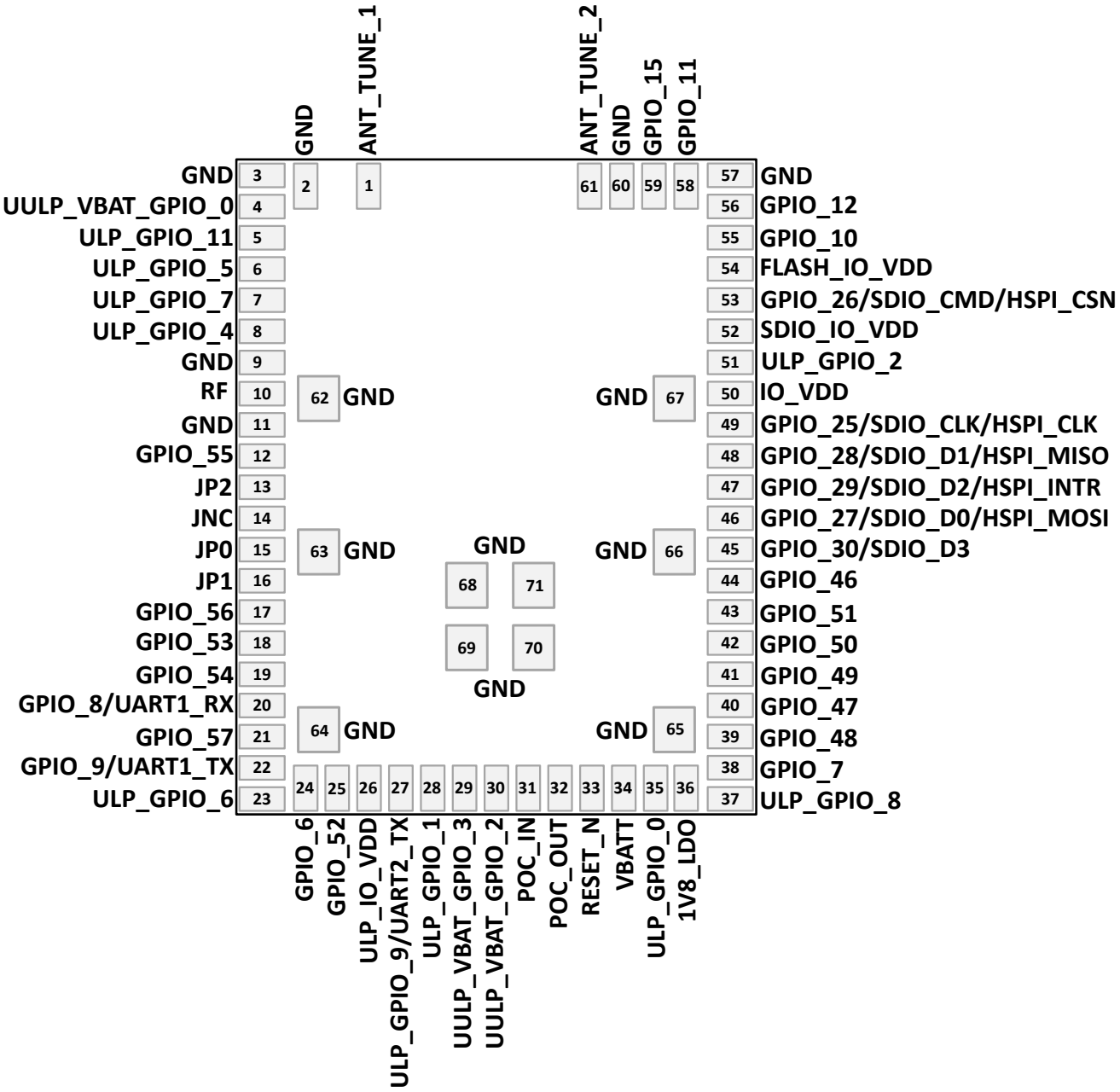


Figure 6.1. SiWN917 Pin Diagram

6.2 Pin Description

Table 6.1. List of Pins in IC (SiWN917M), Not Available in the Modules

Pin Name	QFN I/O Supply Domain	Direction	Initial State (Power up, Active Reset)	Description
RF_BLETX	RF_AVDD	Output	NA	BLE 8 dBm RF Output
ULP_GPIO_10	ULP_IO_VDD	Inout	HighZ	Default: HighZ Sleep: HighZ
XTAL_32KHZ_P	NA	Inout	NA	Analog Pin. 32KHZ XTAL Connection
XTAL_32KHZ_N	NA	Inout	NA	Analog Pin. 32KHZ XTAL Connection
UULP_VBAT_GPIO_1	VBATT	Inout	HighZ	Default: High Sleep: High

6.2.1 RF and Control Interfaces

Table 6.2. Chip Packages - RF and Control Interfaces

Pin Name	Pin No.	I/O Supply Domain	Direction	Initial State (Power up Active Reset)	Description
ANT_TUNE_1	1	N/A	Input	N/A	**SiW917Y1GA:** External fine-tuning option for the integral antenna; connect same tuning circuit on both ANT_TUNE1 and ANT_TUNE2 pins; leave floating if no fine-tuning is desired on the integral antenna; **SiW917Y1GN:** leave this pin floating
RF[1]	10	VBATT	Inout	N/A	Connect to antenna with a 50-Ω impedance as per the reference schematics
POC_IN	31	VBATT	Input	NA	This is an input to the chip which resets all analog and digital blocks in the device. It should be made high only after supplies are valid.
POC_OUT	32	VBATT	Output	NA	This is internally generated. Initially, it is low. But it becomes high when the supply (VBATT) is valid.
RESET_N	33	VBATT	Inout	NA	Active-low reset asynchronous reset signal, which resets only digital blocks. The system pulls RESET_N low whenever POC_IN is low.
ANT_TUNE_2	61	N/A	Input	N/A	**SiW917Y1GA:** External fine-tuning option for the integral antenna; connect same tuning circuit on both ANT_TUNE1 and ANT_TUNE2 pins; leave floating if no fine-tuning is desired on the integral antenna; **SiW917Y1GN:** leave this pin floating

Note:

1. The SiW917Y1GN module does not have an internal antenna.

6.2.2 Power and Ground Pins

Table 6.3. Chip Packages - Power and Ground Pins

Pin Name	Pin No.	Type	Direction	Description
ULP_IO_VDD	26	Power	Input	I/O supply for ULP I/Os. Refer to 6.2.3 Peripheral Interfaces section for details on which GPIOs have this as the I/O supply.
VBATT	34	Power	Input	Power supply for the module.
1V8_LDO	36	Power	Output	Output of 1.8 V LDO which is used for Flash supply.
IO_VDD	50	Power	Input	I/O Supply for GPIOs. Refer to GPIOs section for details on which GPIOs have this as the I/O supply.
SDIO_IO_VDD	52	Power	Input	I/O Supply for SDIO I/Os. Refer to GPIOs section for details on which GPIOs have this as the I/O supply.
FLASH_IO_VDD	54	Power	Input	I/O Supply for module embedded flash. Connect to 1V8_LDO as per Reference Schematics.
GND	2, 3, 9, 11, 57, 60, 62-71	Ground		Common ground pins.

6.2.3 Peripheral Interfaces

Table 6.4. Chip Packages - Peripheral Interfaces

Pin Name	Pin No.	I/O Supply Domain	Direction	Initial State (Power up Active Reset)	Description
UULP_VBAT_GPIO_0	4	VBATT	Output	High	**Default**: High **Sleep**: High This pin can be configured by software to be any of the following. • SLEEP_IND_FROM_DEV: This signal is used to send an indication to the Host processor. An indication is sent when the chip enters (logic low) and exits (logic high) the ULP Sleep mode. Supply domain for UULP_VBAT_GPIOs is VBATT and the supported voltage range is defined in Table 7.2 Recommended Operating Conditions on page 28.
ULP_GPIO_11	5	ULP_IO_VDD	Inout	HighZ	**Default**: HighZ **Sleep**: HighZ
ULP_GPIO_5	6	ULP_IO_VDD	Inout	HighZ	**Default**: HighZ **Sleep**: HighZ
ULP_GPIO_7	7	ULP_IO_VDD	Inout	HighZ	**Default**: HighZ **Sleep**: HighZ
ULP_GPIO_4	8	ULP_IO_VDD	Inout	HighZ	**Default**: HighZ **Sleep**: HighZ
GPIO_55	12	IO_VDD	Inout	HighZ	**Default**: HighZ **Sleep**: HighZ
JP2	13	IO_VDD	Input	Pullup	**Default:** JP2 **Sleep**: HighZ JP2 - Reserved. Connect to a test point for debugging purposes
JNC	14	IO_VDD	Output	Pullup	**Default:** JNC **Sleep**: HighZ JNC - Reserved. Connect to a test point for debugging purposes
JP0	15	IO_VDD	Input	Pullup	**Default:** JP0 **Sleep**: HighZ JP0 - Reserved. Connect to a test point for debugging purposes

<table>
<tr><th>Pin Name</th><th>Pin No.</th><th>I/O Supply Domain</th><th>Direction</th><th>Initial State (Power up Active Reset)</th><th>Description</th></tr>
<tr><td>JP1</td><td>16</td><td>IO_VDD</td><td>Input</td><td>Pullup</td><td>Default: JP1
Sleep: HighZ
JP1 - Reserved. Connect to a test point for debugging purposes</td></tr>
<tr><td>GPIO_56</td><td>17</td><td>IO_VDD</td><td>Inout</td><td>HighZ</td><td>Default: HighZ
Sleep: HighZ</td></tr>
<tr><td>GPIO_53</td><td>18</td><td>IO_VDD</td><td>Inout</td><td>HighZ</td><td>Default: HighZ
Sleep: HighZ</td></tr>
<tr><td>GPIO_54</td><td>19</td><td>IO_VDD</td><td>Inout</td><td>HighZ</td><td>Default: HighZ
Sleep: HighZ</td></tr>
<tr><td>GPIO_8/UART1_RX</td><td>20</td><td>IO_VDD</td><td>Inout</td><td>HighZ</td><td><table><tr><th>Host</th><th>Default</th><th>Sleep</th></tr><tr><td>UART</td><td>UART1_RX - UART Host interface serial input.</td><td>HighZ</td></tr><tr><td>Non UART</td><td>HighZ</td><td>HighZ</td></tr></table></td></tr>
<tr><td>GPIO_57</td><td>21</td><td>IO_VDD</td><td>Inout</td><td>HighZ</td><td>Default: HighZ
Sleep: HighZ</td></tr>
<tr><td>GPIO_9/UART1_TX</td><td>22</td><td>IO_VDD</td><td>Inout</td><td>HighZ</td><td><table><tr><th>Host</th><th>Default</th><th>Sleep</th></tr><tr><td>UART</td><td>UART1_TX - UART Host interface serial output.</td><td>HighZ</td></tr><tr><td>Non UART</td><td>HighZ</td><td>HighZ</td></tr></table></td></tr>
<tr><td>ULP_GPIO_6</td><td>23</td><td>ULP_IO_VDD</td><td>Inout</td><td>HighZ</td><td>Default: HighZ
Sleep: HighZ
This pin can be configured by software to be any of the following.
PTA_PRIO: "PTA Priority" input signal is part of 3-wire coexistence (Packet Traffic Arbitration) interface.</td></tr>
<tr><td>GPIO_6</td><td>24</td><td>IO_VDD</td><td>Inout</td><td>HighZ</td><td>Default: HighZ
Sleep: HighZ</td></tr>
<tr><td>GPIO_52</td><td>25</td><td>IO_VDD</td><td>Inout</td><td>HighZ</td><td>Default: HighZ
Sleep: HighZ</td></tr>
<tr><td>ULP_GPIO_9/ UART2_TX</td><td>27</td><td>ULP_IO_VDD</td><td>Inout</td><td>HighZ</td><td>Default: UART2_TX- Debug UART Interface serial output
Sleep: HighZ</td></tr>
</table>

Pin Name	Pin No.	I/O Supply Domain	Direction	Initial State (Power up Active Reset)	Description
ULP_GPIO_1	28	ULP_IO_VDD	Inout	HighZ	**Default:** HighZ **Sleep**: HighZ This pin can be configured by software to be any of the following • PTA_REQ: "PTA Request" input signal is part of 3-wire coexistence (Packet Traffic Arbitration) interface.
UULP_VBAT_GPIO_3	29	VBATT	Inout	HighZ	**Default:** HighZ **Sleep:** EXT_32KHZ_IN This pin can be configured by software to be any of the following. • EXT_32KHZ_IN: This pin can be used to feed an external clock from a host processor or from an external crystal oscillator. The supply domain for UULP_VBAT_GPIOs is VBATT and the supported voltage range is defined in Table 7.2 Recommended Operating Conditions on page 28.
UULP_VBAT_GPIO_2	30	VBATT	Inout	HighZ	**Default:** HighZ **Sleep:** ULP_WAKEUP This pin can be configured by software to be any of the following. • HOST_BYP_ULP_WAKEUP: This signal has two functionalities – one during the bootloading process and one after the bootloading. During bootloading, this signal is an active-high input to indicate that the bootloader should bypass any inputs from the Host processor and continue to load the default firmware from Flash. After bootloading, this signal is an active-high input to indicate that the module should wakeup from its Ultra Low Power (ULP) sleep mode. Supply domain for UULP_VBAT_GPIOs is VBATT and the supported voltage range is defined in Table 7.2 Recommended Operating Conditions on page 28.
ULP_GPIO_0	35	ULP_IO_VDD	Inout	HighZ	**Default**: HighZ **Sleep**: HighZ
ULP_GPIO_8	37	ULP_IO_VDD	Inout	HighZ	**Default**: HighZ **Sleep**: HighZ

<table>
<tr><th>Pin Name</th><th>Pin No.</th><th>I/O Supply Domain</th><th>Direction</th><th>Initial State (Power up Active Reset)</th><th>Description</th></tr>
<tr><td>GPIO_7</td><td>38</td><td>IO_VDD</td><td>Inout</td><td>HighZ</td><td>Default:HighZ

Sleep: HighZ

This pin can be configured by software to be any of the following.

PTA_GRANT: "PTA Grant" output signal is part of 3-wire coexistence (Packet Traffic Arbitration) interface.</td></tr>
<tr><td>GPIO_48</td><td>39</td><td>IO_VDD</td><td>Inout</td><td>HighZ</td><td>Default: HighZ

Sleep: HighZ</td></tr>
<tr><td>GPIO_47</td><td>40</td><td>IO_VDD</td><td>Inout</td><td>HighZ</td><td>Default: HighZ

Sleep: HighZ</td></tr>
<tr><td>GPIO_49</td><td>41</td><td>IO_VDD</td><td>Inout</td><td>HighZ</td><td>Default: HighZ

Sleep: HighZ</td></tr>
<tr><td>GPIO_50</td><td>42</td><td>IO_VDD</td><td>Inout</td><td>HighZ</td><td>Default: HighZ

Sleep: HighZ</td></tr>
<tr><td>GPIO_51</td><td>43</td><td>IO_VDD</td><td>Inout</td><td>HighZ</td><td>Default: HighZ

Sleep: HighZ</td></tr>
<tr><td>GPIO_46</td><td>44</td><td>IO_VDD</td><td>Inout</td><td>HighZ</td><td>Default: HighZ

Sleep: HighZ</td></tr>
<tr><td>GPIO_30/SDIO_D3</td><td>45</td><td>SDIO_IO_VDD</td><td>Inout</td><td>Pullup</td><td><table><tr><th>Host</th><th>Default</th><th>Sleep</th></tr><tr><td>SDIO</td><td>SDIO_D3 - SDIO interface Data3 signal</td><td>HighZ</td></tr><tr><td>Non SDIO,SPI</td><td>HighZ</td><td>HighZ</td></tr></table></td></tr>
<tr><td>GPIO_27/SDIO_D0/ HSPI_MOSI</td><td>46</td><td>SDIO_IO_VDD</td><td>Inout</td><td>HighZ</td><td><table><tr><th>Host</th><th>Default</th><th>Sleep</th></tr><tr><td>SDIO</td><td>SDIO_D0 - SDIO interface Data0 signal</td><td>HighZ</td></tr><tr><td>SPI</td><td>HSPI_MOSI - SPI Slave interface Master-Out-Slave-In signal</td><td>HighZ</td></tr><tr><td>Non SDIO,SPI</td><td>HighZ</td><td>HighZ</td></tr></table></td></tr>
</table>

<table>
<tr><th>Pin Name</th><th>Pin No.</th><th>I/O Supply Domain</th><th>Direction</th><th>Initial State (Power up Active Reset)</th><th>Description</th></tr>
<tr><td>GPIO_29/SDIO_D2/ HSPI_INTR</td><td>47</td><td>SDIO_IO_VDD</td><td>Inout</td><td>HighZ</td><td>
<table>
<tr><th>Host</th><th>Default</th><th>Sleep</th></tr>
<tr><td>SDIO</td><td>SDIO_D2 - SDIO interface Data2 signal</td><td>HighZ</td></tr>
<tr><td>SPI</td><td>HSPI_INTR - SPI Slave interface Interrupt Signal to the Host</td><td>HighZ</td></tr>
<tr><td>Non SDIO,SPI</td><td>HighZ</td><td>HighZ</td></tr>
</table>
</td></tr>
<tr><td>GPIO_28/SDIO_D1/ HSPI_MISO</td><td>48</td><td>SDIO_IO_VDD</td><td>Inout</td><td>HighZ</td><td>
<table>
<tr><th>Host</th><th>Default</th><th>Sleep</th></tr>
<tr><td>SDIO</td><td>SDIO_D1 - SDIO interface Data1 signal</td><td>HighZ</td></tr>
<tr><td>SPI</td><td>HSPI_MISO - SPI Slave interface Master-In-Slave-Out signal</td><td>HighZ</td></tr>
<tr><td>Non SDIO,SPI</td><td>HighZ</td><td>HighZ</td></tr>
</table>
</td></tr>
<tr><td>GPIO_25/SDIO_CLK/ HSPI_CLK</td><td>49</td><td>SDIO_IO_VDD</td><td>Inout</td><td>HighZ</td><td>
<table>
<tr><th>Host</th><th>Default</th><th>Sleep</th></tr>
<tr><td>SDIO</td><td>SDIO_CLK - SDIO interface clock</td><td>HighZ</td></tr>
<tr><td>SPI</td><td>HSPI_CLK - SPI Slave interface clock</td><td>HighZ</td></tr>
<tr><td>Non SDIO,SPI</td><td>HighZ</td><td>HighZ</td></tr>
</table>
</td></tr>
<tr><td>ULP_GPIO_2</td><td>51</td><td>ULP_IO_VDD</td><td>Input</td><td>HighZ</td><td>Default: HighZ
Sleep: HighZ</td></tr>
</table>

<table>
<tr><th>Pin Name</th><th>Pin No.</th><th>I/O Supply Domain</th><th>Direction</th><th>Initial State (Power up Active Reset)</th><th>Description</th></tr>
<tr><td>GPIO_26/SDIO_CMD/ HSPI_CSN</td><td>53</td><td>SDIO_IO_VDD</td><td>Inout</td><td>HighZ</td><td>
<table>
<tr><th>Host</th><th>Default</th><th>Sleep</th></tr>
<tr><td>SDIO</td><td>SDIO_CMD - SDIO interface CMD signal</td><td>HighZ</td></tr>
<tr><td>SPI</td><td>HSPI_CSN - Active-low Chip Select signal of SPI Slave interface</td><td>HighZ</td></tr>
<tr><td>Non SDIO,SPI</td><td>HighZ</td><td>HighZ</td></tr>
</table>
</td></tr>
<tr><td>GPIO_10</td><td>55</td><td>IO_VDD</td><td>Inout</td><td>HighZ</td><td>Default: HighZ

Sleep: HighZ

This pin can be configured by software to be any of the following.
HOST_WAKEUP_IND: This is used as indication from host to dev that host is ready to take the packet and device can transfer the packet to host. This is supported only in UART host mode.
It is part of Wake-on-Wireless functionality. Please check with Silabs for availability of this functionality</td></tr>
<tr><td>GPIO_12</td><td>56</td><td>IO_VDD</td><td>Inout</td><td>HighZ</td><td>Default: HighZ

Sleep: HighZ

This pin can be configured by software to be any of the following.
UART1_RTS - UART interface Request to Send, if UART Host Interface flow control is enabled.</td></tr>
<tr><td>GPIO_11</td><td>58</td><td>IO_VDD</td><td>Inout</td><td>HighZ</td><td>Default: HighZ

Sleep: HighZ

This pin can be configured by software to be any of the following.
WAKEUP_FROM_DEV: Used as a wakeup indication to host from device.
It is part of Wake-on-Wireless functionality. It is recommended that one use an external weak pull-down resistor on this pin and software has to be configured suitably.
Please check with Silabs for availability of this functionality.</td></tr>
</table>

Pin Name	Pin No.	I/O Supply Domain	Direction	Initial State (Power up Active Reset)	Description
GPIO_15	59	IO_VDD	Inout	HighZ	**Default:** HighZ **Sleep**: HighZ This pin can be configured by software to be any of the following. • UART1_CTS - UART interface Clear to Send, if UART Host Interface flow control is enabled.

7. Electrical Specifications

7.1 Absolute Maximum Ratings

Stresses beyond those listed below may cause permanent damage to the device. This is a stress rating only and functional operation of the devices at those or any other conditions beyond those indicated in the operation listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability. For more information on the available quality and reliability data, see the Quality and Reliability Monitor Report at https://www.silabs.com/about-us/quality.

Table 7.1. Absolute Maximum Ratings

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Storage temperature	T_{store}		-40	—	125	°C
Maximum junction temperature	$T_{j(max)}$			—	125	°C
3.3 V power supply for the on-chip Buck, RF circuit, and UULP IOs	VBATT		-0.5	—	3.63	V
I/O supply for GPIOs	IO_VDD		-0.5	—	3.63	V
I/O supply for SDIO I/Os	SDIO_IO_VDD		-0.5	—	3.63	V
I/O supply for QSPI flash signals	FLASH_IO_VDD		-0.5	—	3.63	V
I/O supply for ULP I/Os	ULP_IO_VDD		-0.5	—	3.63	V
DC voltage on any I/O pin [1]	V_{IO_PIN}		-0.5	—	VDD + 0.5	V
Total average max current into chip	I_{pmax}		—	—	500	mA
Current per I/O pin	I_{IOMAX}	Sink	—	—	100	mA
		Source	—	—	100	mA

Note:
1. VDD = I/O supply domain pin. Refer to pin description tables for supply domain associated with each I/O.

7.2 Recommended Operating Conditions

Note: The device may operate continuously at the maximum allowable ambient $T_{ambient}$ rating as long as the maximum junction $T_{junction(max)}$ is not exceeded. For an application with significant power dissipation, the allowable $T_{ambient}$ may be lower than the maximum $T_{ambient}$ rating. $T_{ambient} = T_{junction(max)} - (\Theta_{JA} \times \text{Power Dissipation})$. Refer to the Thermal Characteristics table for Θ_{JA}.

Table 7.2. Recommended Operating Conditions

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Units
Ambient temperature	$T_{ambient}$		-40	25	85	°C
Junction temperature	$T_{junction}$				105	°C
3.3 V power supply for the on-chip Buck, RF Power Amplifier, UULP I/Os	VBATT		3.0	3.3	3.63	V
I/O supply for Flash	FLASH_IO_VDD		1.71	1.8	1.98	V
I/O supply for GPIOs	IO_VDD[1]	1.8 V nominal operation	1.71	1.8	1.98	V
		3.3 V nominal operation	2.97	3.3	3.63	
I/O supply for SDIO I/Os	SDIO_IO_VDD1	1.8 V nominal operation	1.71	1.8	1.98	V
		3.3 V nominal operation	2.97	3.3	3.63	
I/O supply for ULP I/Os	ULP_IO_VDD[1]	1.8 V nominal operation	1.71	1.8	1.98	V
		3.3 V nominal operation	2.97	3.3	3.63	

Note:
1. Supplies can operate at a nominal 3.3 V or 1.8 V level independent of the other supplies in the system.

7.3 DC Characteristics

7.3.1 RESET_N Pin and POC_IN Pins

Table 7.3. RESET_N Pin and POC_IN Pins

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
High level input voltage	V_{IH}	RESET_N pin, VBATT = 3.3 V	0.8 * VBATT	—	—	V
		POC_IN pin, VBATT = 3.3 V	2.76	—	—	V
Low level input voltage	V_{IL}	RESET_N pin, VBATT = 3.3 V	—	—	0.3 * VBATT	V
		POC_IN pin, VBATT = 3.3 V	—	—	1.10	V

7.3.2 Power On Control (POC) and Reset

There are three signals involved in power-on control and reset of the device:

- POC_IN: When pulled low, POC_IN will reset all of the internal blocks in the device. The POC_IN signal can be controlled either by external circuitry, by POC_OUT, or both.
- RESET_N: RESET_N is an open-drain signal which will be pulled low during a chip reset. It is released after POC_IN is high. RESET_N should be connected to an RC circuit to fulfill the timing requirements shown in Figure 7.1 Power Up Sequence on page 29.
- POC_OUT: The POC_OUT signal is the output of the internal blackout supply monitor. POC_OUT is distributed to all I/O cells to prevent the I/O cells from powering up in an undesired configuration and is also used inside the IC to place the IC in a safe state until a valid supply is available for proper operation. During power up, POC_OUT stays low until the VBATT reaches 1.6 V. After the VBATT supply exceeds 1.6 V, POC_OUT becomes high and normal operation begins. If VBATT becomes lower than the blackout threshold voltage, POC_OUT will return low. POC_OUT can be used to provide chip reset by connecting to POC_IN in a loopback configuration.

The recommended schematic for the reset signals is shown in Figure 8.4 Reset Configuration on page 53.

Figure 7.1 Power Up Sequence on page 29 shows the signal timing when POC_OUT, POC_IN, and RESET_N are connected per the recommended schematic. The POC_IN-to-RESET_N delay will occur when POC_IN transitions from low to high.

In this configuration the system only has to control the supply (VBATT) during power-up and power down and need not control POC_IN externally. On power-up the chip will be reset internally. The power-down sequence will follow VBATT and external control of POC_IN is not required.

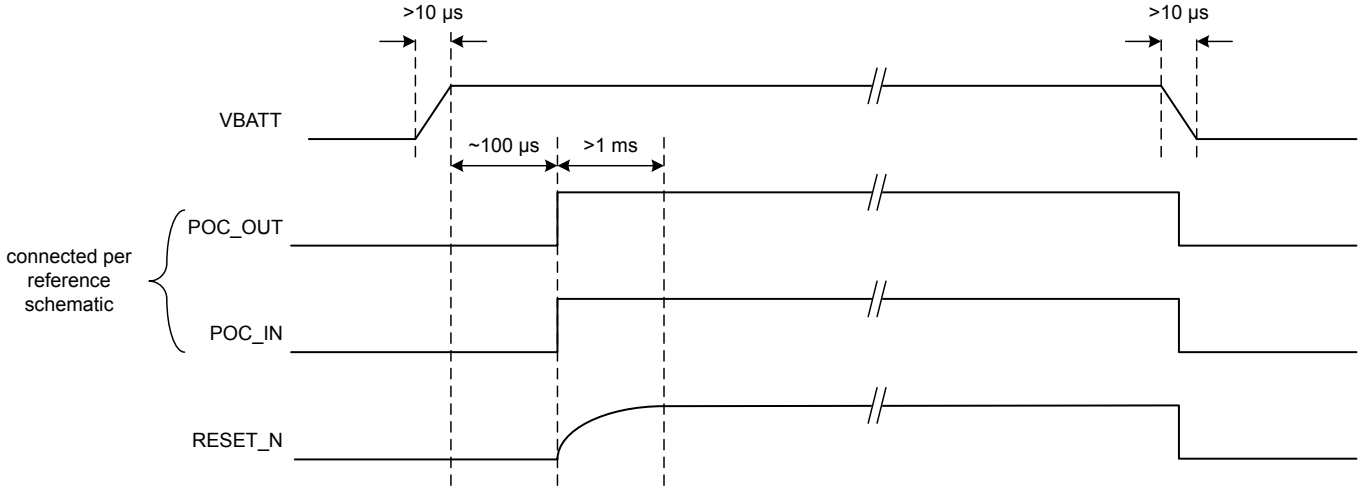


Figure 7.1. Power Up Sequence

If the chip is to be reset from an external host device while powered up, the POC_IN signal should be pulled low for at least 10 ms as shown in Figure 7.2 External Reset via POC_IN on page 29. Upon release of POC_IN, the POC_IN-to-RESET_N delay will occur.

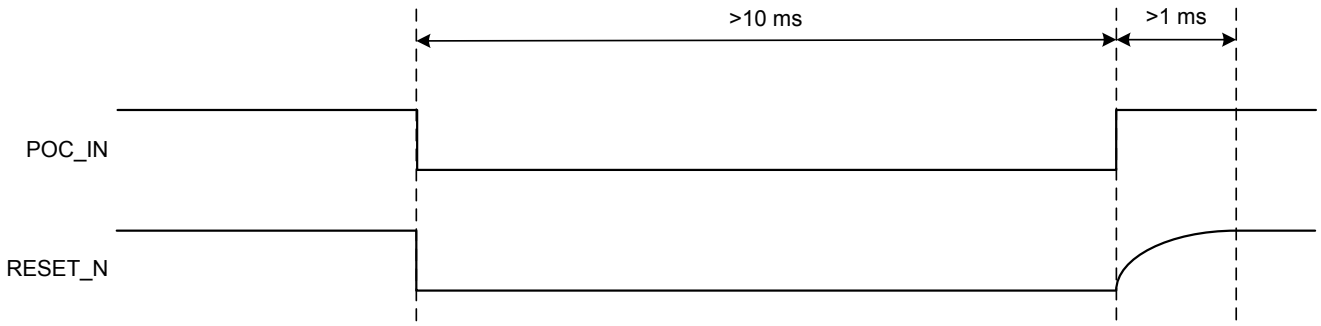


Figure 7.2. External Reset via POC_IN

In the above timing diagrams, it is assumed that all supplies including VBATT are connected together. If they are not connected together and independently controlled, then the guidance below must be followed.

- **Case1**: POC_OUT is looped back and there is no external control for POC_IN
  - All supplies can be enabled at the same time, if possible
  - If supplies cannot be enabled at the same time, the VBATT supplies should be powered up first and all other supplies should be powered on at least 1 ms before RESET_N is high. The RC circuit controlling RESET_N must be adjusted to provide the appropriate delay.
  - While powering down, supplies can be powered off simultaneously, or with VBATT the last to be disabled.
- **Case2**: POC_OUT is looped back and there is external control for POC_IN during power-up / power-down.
  - All supplies can be enabled at the same time, or VBATT may be enabled before other supplies.
  - POC_IN should be kept low for at least 600 us after all the supplies have settled.
  - On power-down, POC_IN can be driven low before disabling the supplies. Supplies can be powered off simultaneously, or with VBATT the last to be disabled.

7.3.3 Thermal Characteristics

Table 7.4. Thermal Characteristics

Package	Board	Parameter	Symbol	Test Condition (1)	Value	Units
Module	JEDEC- High Thermal Cond. (2s2p)	Thermal Resistance, Junction to Ambient	Θ_{JA}	Still Air (JESD51-2A)	66	°C/W

Note:
1. PCB: 76.2 mm x 114.3 mm x 1.6 mm (JEDEC High Effective); 2s2p = 2 signals, 2 planes.
2. The absolute maximum device currrent when transmitting at highest transmit power will not exceed 400 mA.

7.3.4 Digital I/O Signals

Table 7.5. Digital I/O Signals

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
High level input voltage	V_{IH}	IO_VDDx = 3.3 V	2	—	—	V
		IO_VDDx = 1.8 V	1.17	—	—	V
Low level input voltage	V_{IL}	IO_VDDx = 3.3 V	—	—	0.8	V
		IO_VDDx = 1.8 V	—	—	0.63	V
Low level output voltage	V_{OL}		—	—	0.4	V
High level output voltage	V_{OH}		IO_VDDx - 0.4	—	—	V
Low level output current	I_{OL}	GPIO_* and ULP_GPIO_* pins	2	4	12	mA
		UULP_GPIO_*	1	—	2	mA
High level output current	I_{OH}	GPIO_* and ULP_GPIO_* pins	2	4	12	mA
		UULP_GPIO_*	1	—	2	mA

7.3.5 Flash LDO Electrical Specifications - Regulation Mode

Table 7.6. Flash LDO Electrical Specifications - Regulation Mode

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Input Supply Voltage (VBATT)	V_{in}	Flash LDO in Regulation Mode	2.97	3.3	3.63	V
Output Voltage Range (1V8_LDO)	V_{out}		1.75	1.88	1.95	V
Load current	I_{load}		—	—	48	mA
Line Regulation	REG_{line}	V_{in} Changed from 2.97 V to 3.63 V	—	—	0.6	%
Load Regulation	REG_{load}	I_{load} changed from 0 mA to 48 mA	—	—	3	%

7.4 AC Characteristics

7.4.1 Clock Specifications

The SiWN917 modules require two primary clocks:

- Low frequency clock options for sleep manager and RTC
  - Internal 32 kHz RC clock may be used for applications with low timing accuracy requirements
  - 32.768 kHz LVCMOS rail-to-rail external oscillator input pin UULP_VBAT_GPIO_3 for external oscillator or host clock. **Required for MCU timing accuracy and all power-sensitive Wi-Fi, BLE, and Coex use cases.**
- High frequency 40 MHz clock for NWP, baseband subsystem and the radio
  - 40 MHz clock is integrated inside the module, and no external clock needs to be provided

7.4.1.1 Low Frequency Clock

Low-frequency clock selection can be done through software. The RC oscillator clock is not suited for high timing accuracy applications and may increase overall system current consumption in duty-cycled power modes.

32 kHz Internal RC Oscillator

Table 7.7. 32 kHz RC Oscillator

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Oscillator Frequency	F_{osc}			32.0		kHz
Frequency Variation across Temperature	F_{osc_Acc}			1.2		%

32.768 kHz External Oscillator

An external 32.768 kHz low-frequency clock can be fed through UULP_VBAT_GPIO_3.

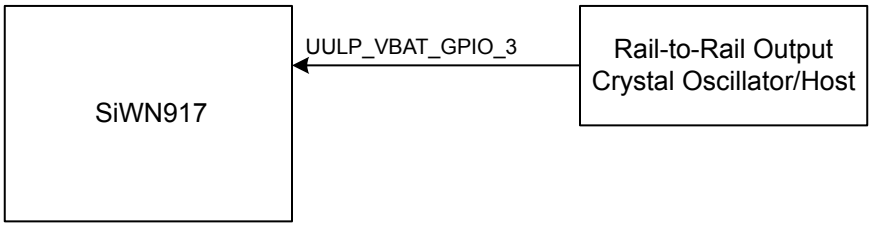


Figure 7.3. External 32.768 kHz Oscillator - Rail to Rail

Table 7.8. 32.768 kHz External Oscillator Specifications

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Oscillator Frequency	f_{osc}		—	32.768	—	kHz
Frequency Variation with Temp and Voltage	f_{osc_Acc}		-100	—	100	ppm
Input duty cycle	DC_{in}		30	50	70	%
Input AC peak-peak voltage swing at input pin.	V_{AC}		-0.3	—	VBATT +/- 10%	Vpp

7.4.1.2 High- Frequency Crystal (HFXO)

Table 7.9. High-Frequency Crystal (HFXO)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Crystal Oscillator Frequency	F_{osc}		—	40	—	MHz
Initial Calibrated Accuracy	F_{osc_Acc}		-5	—	+5	ppm
Frequency Variation across Temperature	F_{osc_Drift}		-14	—	+14	ppm

7.4.2 SDIO 2.0 Secondary

7.4.2.1 Full Speed Mode

Table 7.10. SDIO 2.0 Secondary Full Speed Mode

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
SDIO_CLK	f_{sdio_clk}		—	—	25	MHz
SDIO_DATA, SDIO_CMD input setup time	t_s		4	—	—	ns
SDIO_DATA, SDIO_CMD input hold time	t_h		1.2	—	—	ns
SDIO_DATA, clock to output delay	t_{od}		—	—	13	ns
Output Load	C_L		5	—	10	pF

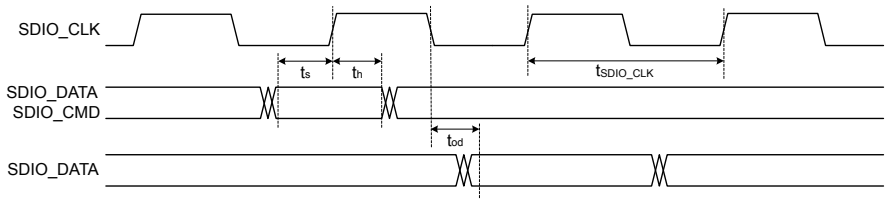


Figure 7.4. Interface Timing Diagram for SDIO 2.0 Secondary Full Speed Mode

7.4.2.2 High Speed Mode

Table 7.11. SDIO 2.0 Secondary High Speed Mode

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
SDIO_CLK	f_{sdio_clk}		25	—	50	MHz
SDIO_DATA, input setup time	t_s		4	—	—	ns
SDIO_DATA, input hold time	t_h		1.2	—	—	ns
SDIO_DATA, clock to output delay	t_{od}		2.5	—	13	ns
Output Load	C_L		5	—	10	pF

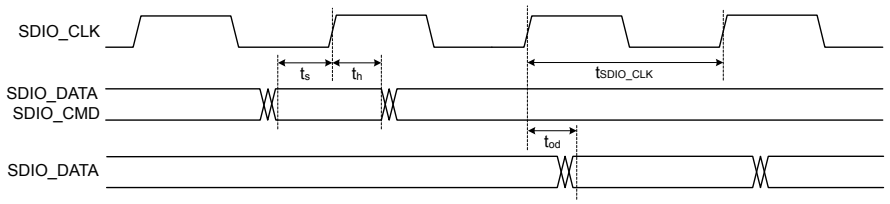


Figure 7.5. Interface Timing Diagram for SDIO 2.0 Secondary High Speed Mode

7.4.3 HSPI Secondary

7.4.3.1 Low Speed Mode

Table 7.12. HSPI Secondary Low Speed Mode

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
HSPI_CLK	f_{hspi}		0	—	25	MHz
HSPI_CSN to output delay	t_{cs}		—	—	7.5	ns
HSPI_CSN to input setup time	t_{cst}		4.5	—	—	ns
HSPI_MOSI, input setup time	t_s		1.4	—	—	ns
HSPI_MOSI, input hold time	t_h		1.5	—	—	ns
HSPI_MISO, clock to output delay	t_{od}		—	—	8.75	ns
Output Load	C_L		5	—	10	pF

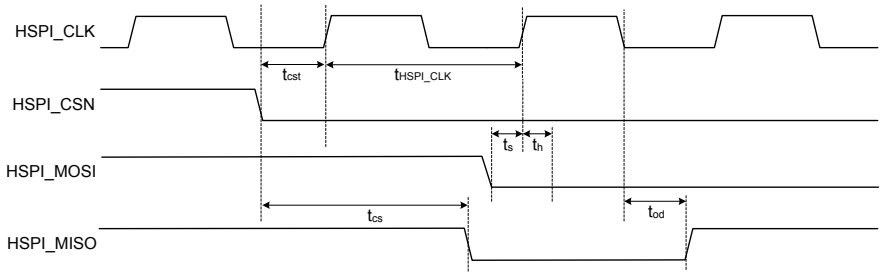


Figure 7.6. Interface Timing Diagram for HSPI Secondary Low Speed Mode

In low speed mode, HSPI_MISO data is driven on the falling edge of HSPI_CLK, and HSPI_MOSI is read on the rising edge of HSPI_CLK.

7.4.3.2 High Speed Mode

Table 7.13. HSPI Secondary High Speed Mode

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
HSPI_CLK	f_{hspi}		25	—	80	MHz
HSPI_CSN to output delay	t_{cs}		—	—	7.5	ns
HSPI_CSN to input setup time	t_{cst}		4.5	—	—	ns
HSPI_MOSI, input setup time	t_s		1.4	—	—	ns
HSPI_MOSI, input hold time	t_h		1.4	—	—	ns
HSPI_MISO, clock to output delay	t_{od}		1.5	—	8.75	ns
Output Load	C_L		5	—	10	pF

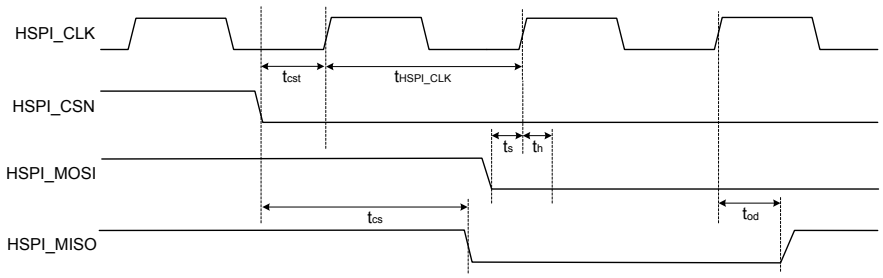


Figure 7.7. Interface Timing Diagram for HSPI Secondary High Speed Mode

In high speed mode, HSPI_MISO data is driven on the rising edge of HSPI_CLK, and HSPI_MOSI is read on the rising edge of HSPI_CLK.

7.4.3.3 Ultra High Speed Mode

Table 7.14. HSPI Secondary Ultra High Speed Mode

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
HSPI_CLK	f_{hspi}		80	—	100	MHz
HSPI_MOSI, input setup time	t_s		1.4	—	—	ns
HSPI_MOSI, input hold time	t_h		1.4	—	—	ns
HSPI_MISO, clock to output delay	t_{od}		1.5	—	8.75	ns
Output Load	C_L		5	—	10	pF

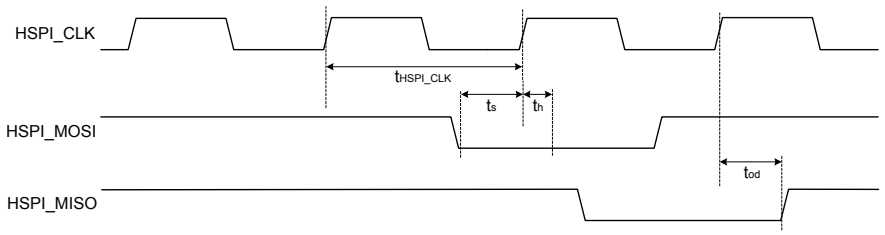


Figure 7.8. Interface Timing Diagram for HSPI Secondary Ultra High Speed Mode

In ultra high speed mode, HSPI_MISO data is driven on the rising edge of HSPI_CLK, and HSPI_MOSI is read on the rising edge of HSPI_CLK.

7.4.4 UART

Table 7.15. UART

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Baud Rate	f_{BAUD}		—	—	921600	bps

7.4.5 GPIO Pins

Table 7.16. GPIO Pins

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Rise time	t_{rf}	Pin configured as output	1	—	5	ns
Fall time	t_{ff}	Pin configured as output	0.9	—	5	ns
Rise time	t_r	Pin configured as input	0.3	—	1.3	ns
Fall time	t_f	Pin configured as input	0.2	—	1.2	ns

7.4.6 In-Package Flash Memory

Table 7.17. In-Package Flash Memory

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Endurance	N_{endu}	Sector erase/program	10000	—	—	cycles
		Page erase/program, page in large sector	10000	—	—	cycles
		Page erase/program, page in small sector	10000	—	—	cycles
Retention time	t_{ret}	Powered	10	—	—	years
		Unpowered	10	—	—	years
Block Erase time (32 KB)	t_{er}	Page, sector or multiple consecutive sectors	—	150	1400	ms
Page programming time	t_{prog}		—	0.5	3	ms
Chip Erase time	t_{ce}		—	20	65	s

7.5 RF Characteristics

In the sub-sections below,

- All numbers are measured at T_A = 25 °C, VBATT = 3.3 V
- Please refer to 8. Reference Schematics, BOM, and Layout Guidelines. The integrated RF front end includes the matching network, internal RF switch, and a band-pass filter.
- Supported WLAN channels for different regions include:
  - US: Channels 1 (2412 MHz) through 11 (2462 MHz)
  - Europe: Channels 1 (2412 MHz) through 13 (2472 MHz)
  - Japan: Channels 1 (2412 MHz) through 14 (2484 MHz), Channel 14 supports 1 and 2 Mbps data rates only

7.5.1 WLAN 2.4 GHz Transmitter Characteristics

7.5.1.1 Transmitter Characteristics with 3.3 V Supply

Unless otherwise indicated, typical conditions are: T_A = 25 °C, VBATT = 3.3 V. Remaining supplies are at typical operating conditions. Parameters are referred at RF pin.

Table 7.18. WLAN 2.4 GHz Transmitter Characteristics with 3.3 V Supply

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Transmit Power for 20 MHz Bandwidth, with EVM limits [1, 2, 5]	POUT	802.11b 1 Mbps DSSS, EVM< -9 dB	—	17	—	dBm
		802.11b 11 Mbps CCK, EVM< -9 dB	—	17	—	dBm
		802.11g 6 Mbps OFDM, EVM< -5 dB [3]	—	17	—	dBm
		802.11g 54 Mbps OFDM, EVM< -25 dB [3]	—	13.5	—	dBm
		802.11n HT20 MCS0 Mixed Mode, EVM< -5 dB[3]	—	17.5	—	dBm
		802.11n HT20 MCS7 Mixed Mode, EVM< -27 dB[3]	—	12.5	—	dBm
		802.11ax HE20 MCS0 SU, EVM< -5 dB[3, 4]	—	15.5	—	dBm
		802.11ax HE20 MCS7 SU, EVM< -27 dB[3, 4]	—	11	—	dBm
Power variation across channels	$POUT_{VAR\_CH}$		—	2	—	dB
Power variation across temperature	$POUT_{VAR\_T}$	-40 to +85 °C	—	3	—	dB

Note:

1. Transmit power listed in this table is average power across all channels.
2. TX power in edge channels will be limited by Restricted band edge in the FCC region.
3. 11g/n/ax TX power in edge channels will be limited by Unwanted Emissions in MIC region.
4. 11ax TX power will be limited by PSD in the ETSI region.
5. Channels 1 (2412 MHz) through 11 (2462 MHz) are supported for North America (FCC, ISED). Channels 1 (2412 MHz) through 13 (2472 MHz) are supported for Europe and Japan (CE, MIC). Channel 14 (2484 MHz) is additionally supported for Japan.

7.5.2 WLAN 2.4 GHz Receiver Characteristics on High-Performance (HP) Mode

Unless otherwise indicated, typical conditions are: T_A = 25 °C. VBATT = 3.3 V. Remaining supplies are at typical operating conditions. Parameters are referred at RF pin.

Table 7.19. WLAN 2.4 GHz Receiver Characteristics on HP Mode

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Sensitivity for 20 MHz Bandwidth [1, 2]	SENS	802.11b 1 Mbps DSSS [4]	—	-95.5	—	dBm
		802.11b 11 Mbps CCK [4]	—	-87	—	dBm
		802.11g 6 Mbps OFDM [5]	—	-91.5	—	dBm
		802.11g 54 Mbps OFDM [5]	—	-75	—	dBm
		802.11n HT20 MCS0 Mixed Mode [6]	—	-90.5	—	dBm
		802.11n HT20 MCS7 Mixed Mode [6]	—	-70.5	—	dBm
		802.11ax HE20 MCS0 SU [7]	—	-90	—	dBm
		802.11ax HE20 MCS7 SU [7]	—	-70	—	dBm
		802.11ax HE20 MCS0 ER [7]	—	-91.5	—	dBm
Maximum Input Level for PER below 10 %	RX_{SAT}	802.11b	—	3	—	dBm
		802.11g	—	-2.5	—	dBm
		802.11n	—	-4.5	—	dBm
		802.11ax	—	-2.5	—	dBm
RSSI Accuracy Range	$RSSI_{RNG}$		—	+/-4	—	dB
Adjacent Channel Interference [8]	ACI	802.11b 1 Mbps DSSS [4 9]	—	48	—	dB
		802.11b 11 Mbps CCK [4 9]	—	36	—	dB
		802.11g 6 Mbps OFDM [5 10]	—	41	—	dB
		802.11g 54 Mbps OFDM [5 10]	—	23	—	dB
		802.11n HT20 MCS0 Mixed Mode [6 10]	—	33	—	dB
		802.11n HT20 MCS7 Mixed Mode [6 10]	—	11	—	dB
		802.11ax HE20 MCS0 SU [7 10]	—	20	—	dB
		802.11ax HE20 MCS7 SU [7 10]	—	6	—	dB

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Alternate Adjacent Channel Interference [8]	AACI	802.11b 1 Mbps DSSS [4] [9]	—	50	—	dB
		802.11b 11 Mbps CCK [4] [9]	—	39	—	dB
		802.11g 6 Mbps OFDM [5] [10]	—	51	—	dB
		802.11g 54 Mbps OFDM [5] [10]	—	31	—	dB
		802.11n HT20 MCS0 Mixed Mode [6] [10]	—	51	—	dB
		802.11n HT20 MCS7 Mixed Mode [6] [10]	—	29	—	dB
		802.11ax HE20 MCS0 SU [7] [10]	—	50	—	dB
		802.11ax HE20 MCS7 SU [7] [10]	—	30	—	dB

Note:

1. RX Sensitivity Variation is up to 2 dB for channels (1, 2, 3, 4, 5, 9, and 10) at typical / room temperature.
2. RX Sensitivity may be degraded up to 3 dB for channels (6, 7, 8, 11, 12, 13 and 14) at typical / room temperature.
3. Sensitivity variation across temperature -40 °C to +85 °C is up to 3 dB
4. 802.11b, Packet size is 1024 bytes, < 8 % PER limit, Carrier modulation is non-DCM
5. 802.11g, Packet size is 1024 bytes, < 10 % PER limit, Carrier modulation is non-DCM
6. 802.11n, Packet size is 4096 bytes, < 10 % PER limit, Carrier modulation is non-DCM
7. 802.11ax, Packet size is 4096 bytes, < 10 % PER limit, Carrier modulation is non-DCM
8. ACI / AACI is calculated as Interferer Power (dBm) - Inband power (dBm)
9. Desired signal power is 6 dB above standard defined sensitivity level
10. Desired signal power is 3 dB above standard defined sensitivity level

7.5.3 WLAN 2.4 GHz Receiver Characteristics on Low-Power (LP) Mode

Unless otherwise indicated, typical conditions are: T_A = 25 °C. VBATT = 3.3 V. Remaining supplies are at typical operating conditions. Parameters are referred at RF pin.

Table 7.20. WLAN 2.4 GHz Receiver Characteristics on LP Mode

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Sensitivity for 20 MHz Bandwidth [1] [2]	SENS	802.11b 1 Mbps DSSS [4]	—	-95.5	—	dBm
		802.11b 11 Mbps CCK [4]	—	-87	—	dBm
		802.11g 6 Mbps OFDM [5]	—	-91	—	dBm
		802.11g 36 Mbps OFDM [5]	—	-80.5	—	dBm
		802.11n HT20 MCS0 Mixed Mode [6]	—	-90	—	dBm
		802.11n HT20 MCS4 Mixed Mode [6]	—	-78	—	dBm
Maximum Input Level for PER below 10%	RX_{SAT}	802.11b	—	-8	—	dBm
		802.11g	—	-0.5	—	dBm
		802.11n	—	-1	—	dBm
RSSI Accuracy Range	$RSSI_{RNG}$		—	+/-4	—	dB
Adjacent Channel Interference [7]	ACI	802.11b 1 Mbps DSSS [4] [8]	—	46	—	dB
		802.11b 11 Mbps CCK [4] [8]	—	33	—	dB
		802.11g 6 Mbps OFDM [5] [9]	—	42	—	dB
		802.11g 36 Mbps OFDM [5] [9]	—	26	—	dB
		802.11n HT20 MCS0 Mixed Mode [6] [9]	—	33	—	dB
		802.11n HT20 MCS4 Mixed Mode [6] [9]	—	20	—	dB
Alternate Adjacent Channel Interference [7]	AACI	802.11b 1 Mbps DSSS [4] [8]	—	49	—	dB
		802.11b 11 Mbps CCK [4] [8]	—	37	—	dB
		802.11g 6 Mbps OFDM [5] [9]	—	50	—	dB
		802.11g 36 Mbps OFDM [5] [9]	—	35	—	dB
		802.11n HT20 MCS0 Mixed Mode [6] [9]	—	50	—	dB
		802.11n HT20 MCS4 Mixed Mode [6] [9]	—	33	—	dB

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit

Note:

1. RX Sensitivity Variation is up to 2 dB for channels (1, 2, 3, 4, 5, 9, and 10) at typical / room temperature
2. RX Sensitivity may be degraded up to 3 dB for channels (6, 7, 8, 11, 12, 13, 14) at typical / room temperature
3. Sensitivity variation across temperature -40 °C to +85 °C is up to 3 dB
4. 802.11b, Packet size is 1024 bytes, < 8 % PER limit, Carrier modulation is non-DCM
5. 802.11g, Packet size is 1024 bytes, < 10 % PER limit, Carrier modulation is non-DCM
6. 802.11n, Packet size is 4096 bytes, < 10 % PER limit, Carrier modulation is non-DCM
7. ACI / AACI is calculated as Interferer Power (dBm) - Inband power (dBm)
8. Desired signal power is 6 dB above standard defined sensitivity level
9. Desired signal power is 3 dB above standard defined sensitivity level

7.5.4 Bluetooth Transmitter Characteristics on High-Performance (HP) Mode

Unless otherwise indicated, typical conditions are: T_A = 25 °C, VBATT = 3.3 V, and remaining supplies are at typical operating conditions. Parameters are referred at RF pin.

Table 7.21. Bluetooth Transmitter Characteristics on HP Mode 3.3 V

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Transmit Power [1]	POUT	LE 1 Mbps	—	17	—	dBm
		LE 2 Mbps	—	17	—	dBm
		LR 500 kbps[2]	—	17	—	dBm
		LR 125 kbps [2]	—	17	—	dBm
Power variation across channels	$POUT_{VAR\_CH}$		—	2	—	dB
Power variation across temperature	$POUT_{VAR\_T}$	-40 to +85 °C	—	3	—	dB
Adjacent Channel Power |M-N| = 2	ACP_{eq2}	LE	—	-34	—	dBm
Adjacent Channel Power |M-N| > 2	ACP_{gt2}	LE	—	-38	—	dBm
BLE Modulation Characteristics at 1 Mbps	MOD_{CHAR}	Δf1 Avg	—	248	—	kHz
		Δf2 Max	—	250	—	kHz
		Δf2 Avg/Δf1 Avg	—	1.5	—	

Note:

1. ETSI Max Power is limited to 10 dBm/MHz EIRP to meet PSD requirements, because device falls under DTS.
2. In FCC, LR 125 kbps and 500 kbps Max Power is limited to 11 dBm to meet PSD requirement, because device falls under DTS.
3. In MIC Max power is limited to 7 dBm to meet 10 dBm/MHz limit.

7.5.5 Bluetooth Transmitter Characteristics on Low-Power (LP) 0 dBm RF Mode

Unless otherwise indicated, typical conditions are: T_A = 25 °C, VBATT = 3.3 V, and remaining supplies are at typical operating conditions. Parameters are referred at RF pin.

Table 7.22. Bluetooth Transmitter Characteristics on Low-Power (LP) 0 dBm RF Mode

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Transmit Power	POUT	LE 1 Mbps	—	-1	—	dBm
		LE 2 Mbps	—	-1	—	dBm
		LR 500 kbps	—	-1	—	dBm
		LR 125 kbps	—	-1	—	dBm
Power variation across channels	$POUT_{VAR\_CH}$		—	2	—	dB
Power variation across temperature	$POUT_{VAR\_T}$	-40 °C to +85 °C	—	2	—	dB
Adjacent Channel Power |M-N| = 2	ACP_{eq2}	LE	—	-44	—	dBm
Adjacent Channel Power |M-N| > 2	ACP_{gt2}	LE	—	-48	—	dBm
BLE Modulation Characteristics at 1 Mbps	MOD_{CHAR}	Δf1 Avg	—	248	—	kHz
		Δf2 Max	—	250	—	kHz
		Δf2 Avg/Δf1 Avg	—	1.4	—	kHz

7.5.6 Bluetooth Receiver Characteristics for 1 Mbps Data Rate

Unless otherwise indicated, typical conditions are: T_A = 25 °C, VBATT = 3.3 V, remaining supplies are at typical operating conditions, packet length is 37 bytes, and parameters are referred at RF pin. Unless otherwise indicated, specifications apply to both HP and LP modes.

Table 7.23. Bluetooth Receiver Characteristics for 1 Mbps Data Rate

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Max usable receiver input level	RX_{SAT}	Signal is reference signal, 255 byte payload, BER = 0.017 %, HP Mode	—	2	—	dBm
		Signal is reference signal, 255 byte payload, BER = 0.017 %, LP Mode	—	-2	—	dBm
Sensitivity [1] [2]	SENS	Signal is reference signal, 37 byte payload, BER = 0.1 %	—	-94	—	dBm
		Signal is reference signal, 255 byte payload, BER = 0.017 %	—	-91.5	—	dBm
Signal to co-channel interferer [3]	C/I_{CC}	(see notes)[4] [5]	—	-10	—	dB
N ± 1 Adjacent channel selectivity [3]	C/I_1	Interferer is reference signal at +1 MHz offset[4] [5] [6] [7]	—	-1	—	dB
		Interferer is reference signal at -1 MHz offset[4] [5] [6] [7]	—	-4	—	dB
N ± 2 Alternate channel selectivity [3]	C/I_2	Interferer is reference signal at +2 MHz offset[4] [5] [6] [7]	—	22	—	dB
		Interferer is reference signal at -2 MHz offset[4] [5] [6] [7]	—	26	—	dB
N ± 3 Alternate channel selectivity [3]	C/I_3	Interferer is reference signal at +3 MHz offset[4] [5] [6] [7]	—	28	—	dB
		Interferer is reference signal at -3 MHz offset[4] [5] [6] [7]	—	40	—	dB
N ≥ | ± 4| Alternate channel selectivity[4]	C/I_4	Interferer is reference signal at ≥ | ± 4| MHz offset [4] [5] [6] [7]	—	33	—	dB
Selectivity to image frequency [3]	C/I_{IM}	Interferer is reference signal at image frequency[4] [5] [7] [8]	—	25	—	dB
Selectivity to image frequency ± 1 MHz [3]	C/I_{IM_1}	Interferer is reference signal at image frequency +1 MHz[4] [5] [7] [8]	—	33	—	dB
		Interferer is reference signal at image frequency -1 MHz[4] [5] [7] [8]	—	28	—	dB

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit

Note:

1. Sensitivities for channels 19, 39 are up to 2 dB lower performance
2. Sensitivity variation across temperature -40 to +85 °C is up to 4 dB
3. C/I is calculated as Interferer Power (dBm) - Inband power (dBm)
4. 0.1 % BER, 37 byte packet size
5. Desired signal = -67 dBm
6. Desired frequency 2402 MHz ≤ Fc ≤ 2480 MHz
7. With allowed exceptions
8. Image frequency is at +4 MHz offset

7.5.7 Bluetooth Receiver Characteristics for 2 Mbps Data Rate

Unless otherwise indicated, typical conditions are: T_A = 25 °C, VBATT = 3.3 V, remaining supplies are at typical operating conditions, packet length is 37 bytes, and parameters are referred at RF pin. Unless otherwise indicated, specifications apply to both HP and LP modes.

Table 7.24. Bluetooth Receiver Characteristics for 2 Mbps Data Rate

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Max usable receiver input level	RX_{SAT}	Signal is reference signal, 255 byte payload, BER = 0.017 %, HP mode	—	2	—	dBm
		Signal is reference signal, 255 byte payload, BER = 0.017 %, LP mode	—	-6	—	dBm
Sensitivity [1] [2]	SENS	Signal is reference signal, 37 byte payload, BER = 0.1 %	—	-91.5	—	dBm
		Signal is reference signal, 255 byte payload, BER = 0.017 %	—	-89.5	—	dBm
Signal to co-channel interferer [3]	C/I_{CC}	(see notes)[4] [5]	—	-7	—	dB
N ± 1 Adjacent channel selectivity [3]	C/I_1	Interferer is reference signal at +2 MHz offset[4] [6] [5] [7]	—	6	—	dB
		Interferer is reference signal at -2 MHz offset[4] [6] [5] [7]	—	3	—	dB
N ± 2 Alternate channel selectivity [3]	C/I_2	Interferer is reference signal at +4 MHz offset[4] [6] [5] [7]	—	16	—	dB
		Interferer is reference signal at -4 MHz offset[4] [6] [5] [7]	—	21	—	dB
Selectivity to image frequency [3]	C/I_{IM}	Interferer is reference signal at image frequency[4] [5] [7] [8]	—	16	—	dB
Selectivity to image frequency ± 2 MHz [3]	C/I_{IM_1}	Interferer is reference signal at image frequency +2 MHz[4] [5] [7] [8]	—	27	—	dB
		Interferer is reference signal at image frequency -2 MHz[4] [5] [7] [8]	—	6	—	dB

Note:

1. Sensitivities for channels 19, 39 are up to 2 dB lower performance
2. Sensitivity variation across temperature -40 to +85 °C is up to 4 dB
3. C/I is calculated as Interferer Power (dBm) - Inband power (dBm)
4. 0.1% BER, 37 byte packet size
5. Desired signal = -67 dBm
6. Desired frequency 2402 MHz ≤ Fc ≤ 2480 MHz
7. With allowed exceptions
8. Image frequency is at +4 MHz offset

7.5.8 Bluetooth Receiver Characteristics for 125 kbps Data Rate

Unless otherwise indicated, typical conditions are: T_A = 25 °C, VBATT = 3.3 V, remaining supplies are at typical operating conditions, packet length is 37 bytes, and parameters are referred at RF pin. Unless otherwise indicated, specifications apply to both HP and LP modes.

Table 7.25. Bluetooth Receiver Characteristics for 125 kbps Data Rate

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Max usable receiver input level	RX_{SAT}	Signal is reference signal, 255 byte payload, BER = 0.017 %, HP mode	—	3	—	dBm
		Signal is reference signal, 255 byte payload, BER = 0.017 %, LP mode	—	0	—	dBm
Sensitivity [1] [2]	SENS	Signal is reference signal, 37 byte payload, BER = 0.1 %	—	-105.5	—	dBm
		Signal is reference signal, 255 byte payload, BER = 0.017 %	—	-105.5	—	dBm

Note:
1. Sensitivities for channels 19, 39 are up to 5 dB lower performance
2. Sensitivity variation across temperature -40 to +85 °C is up to 4 dB

7.5.9 Bluetooth Receiver Characteristics for 500 kbps Data Rate

Unless otherwise indicated, typical conditions are: T_A = 25 °C, VBATT = 3.3 V, remaining supplies are at typical operating conditions, packet length is 37 bytes, and parameters are referred at RF pin. Unless otherwise indicated, specifications apply to both HP and LP modes.

Table 7.26. Bluetooth Receiver Characteristics for 500 kbps Data Rate

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Max usable receiver input level	RX_{SAT}	Signal is reference signal, 255 byte payload, BER = 0.017 %, HP Mode	—	3	—	dBm
		Signal is reference signal, 255 byte payload, BER = 0.017 %, LP Mode	—	0	—	dBm
Sensitivity [1] [2]	SENS	Signal is reference signal, 37 byte payload, BER = 0.1 %	—	-101.5	—	dBm
		Signal is reference signal, 255 byte payload, BER = 0.017 %	—	-99.5	—	dBm

Note:
1. Sensitivities for channels 19, 39 are up to 2 dB lower performance
2. Sensitivity variation across temperature -40 to +85 °C is up to 4 dB

7.6 Typical Current Consumption

Figure 7.9 Supply Connection for Current Measurements on page 48 shows the supply connection and measurement point for supply current numbers in this section. An external 32.726 kHz oscillator is used at UULP_VBAT_GPIO_3 pin.

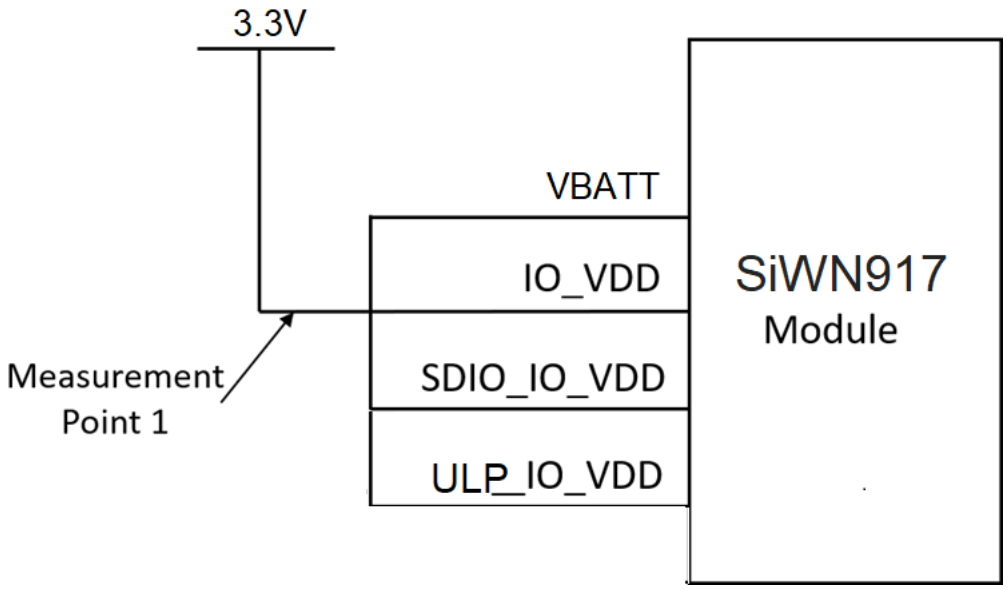


Figure 7.9. Supply Connection for Current Measurements

7.6.1 WLAN 2.4 GHz

T_A = 25 °C. VBATT = 3.3 V. Remaining supplies are at typical operating conditions. NWP clock is running at 80 MHz and Cortex-M4 is in PS0 mode.

Table 7.27. WLAN 2.4 GHz 3.3 V Current Consumption

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Listen current	I_{RX_LISTEN}	LP mode, 1 Mbps Listen	—	16.5	—	mA
Active Receive Current	I_{RX_ACTIVE}	1 Mbps RX Active, LP mode	—	22	—	mA
		HT20 MCS0, HP mode	—	51	—	mA
		HT20 MCS7, HP mode	—	51	—	mA
		HE20 MCS0, HP mode	—	51	—	mA
		HE20 MCS7, HP mode	—	51	—	mA
Transmit Current	I_{TX}	1 Mbps, HP mode	—	203	—	mA
		HT20 MCS0, HP mode	—	216	—	mA
		HT20 MCS7, HP mode	—	159	—	mA
		HE20 MCS0, HP mode	—	191	—	mA
		HE20 MCS7, HP mode	—	159	—	mA
Deep Sleep	I_{SLEEP}	No RAM retained	—	4.5	—	µA
		352 KB RAM retained	—	11	—	µA
Standby Associated, DTIM = 10	I_{STBY_ASSOC}	WLAN Keep Alive Every 30 s with 352 KB RAM Retained, Without TCP Keep Alive	—	71	—	µA
		WLAN Keep Alive Every 30 s with 352 KB RAM Retained, TCP Keep Alive Every 240s	—	84	—	µA
11ax TWT, Auto Config Enabled, Without TCP Keep Alive	I_{STBY_AX}	RX latency 2 s with 8 ms wakeup duration, WLAN Keep Alive Every 30 s with 352 KB RAM Retained	—	103	—	µA
		RX latency 30 s with 8 ms wakeup duration, WLAN Keep Alive Every 30 s with 352 KB RAM Retained	—	37	—	µA
		RX latency 60 s with 8 ms wakeup duration, WLAN Keep Alive Every 60 s with 352 KB RAM Retained	—	25	—	µA

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
11ax TWT, Auto Config Enabled, With TCP Keep Alive Every 240 s	$I_{STBY\_AX\_TCP}$	RX latency 2 s with 8 ms wakeup duration, WLAN Keep Alive Every 30 s with 352 KB RAM Retained	—	105	—	µA
		RX latency 30 s with 8 ms wakeup duration, WLAN Keep Alive Every 30 s with 352 KB RAM Retained	—	39	—	µA
		RX latency 60 s with 8 ms wakeup duration, WLAN Keep Alive Every 60 s with 352 KB RAM Retained	—	28	—	µA

Note:
1. The absolute maximum device current when transmitting at highest transmit power will not exceed 400 mA.

7.6.2 Bluetooth LE

T_A = 25 °C. VBATT = 3.3 V. Remaining supplies are at typical operating conditions. NWP clock running at 80 MHz.

Table 7.28. Bluetooth LE Current Consumption

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
TX Active Current	I_{TX}	LP mode, Tx Power Index 31 (0 dBm)	—	10	—	mA
		HP mode, Tx Power Index 16 (16 dBm)	—	172	—	mA
		HP mode, Tx Power Index 4 (4 dBm)	—	79	—	mA
RX Active Current	I_{RX}	LP mode	—	11	—	mA
Advertising, Unconnectable	I_{ADV_UC}	Advertising on all 3 channels, 37 Byte payload, Interval = 1.28 s, Tx Power = 0 dBm, LP mode	—	37	—	µA
Advertising, Connectable	I_{ADV_CN}	Advertising on all 3 channels, 37 Byte payload, Interval = 1.28 s, Tx Power = 0 dBm, LP mode	—	43	—	µA
Connected	I_{CONN}	Connection Interval = 200 ms, No data, Tx Power = 0 dBm, LP mode	—	141	—	µA
		Connection Interval = 1.28 s, No data, Tx Power = 0 dBm, LP mode	—	41	—	µA

8. Reference Schematics, BOM, and Layout Guidelines

Note:

1. Customers should include provision for programming or updating the firmware at manufacturing.
   a. If using UART, we recommend bringing out the HSPI or SDIO lines to test points, so designers could use the faster interface for programming the firmware as needed.
   b. If using HSPI or SDIO as host interface, then firmware programming or update can be done through the host MCU, or if designer prefers to program standalone at manufacturing, then it is recommended to have test points on the SPI or SDIO signals.
2. 3.3 V/1.8 V/VBATT must be supplied by external source.
3. VBATT, SDIO_IO_VDD, IO_VDD, ULP_IO_VDD must be powered using External/On-board Power.
4. FLASH_IO_VDD is powered by 1V8_LDO output.
5. Place all the Caps closer to the corresponding Module pins.

8.1 SiW917Y1GN Schematics for Parts with RF Pin

8.1.1 System Supplies

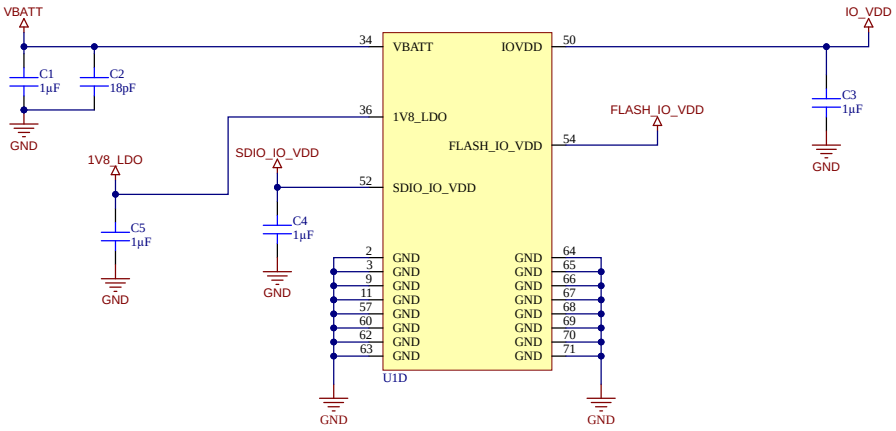


Figure 8.1. System Power Supplies

Note:

1. Place all the decoupling capacitors close to the module pins.
2. IO_VDD, SDIO_IO_VDD, ULP_IO_VDD can be powered independently by different voltage sources based on their corresponding signals voltage levels requirements. Voltages must be as per Table 7.2 Recommended Operating Conditions on page 28.
3. Even if GPIOs are not used, their respective IO domains must still be connected to the power supply.

8.1.2 RF, Debug, and Reset Connection

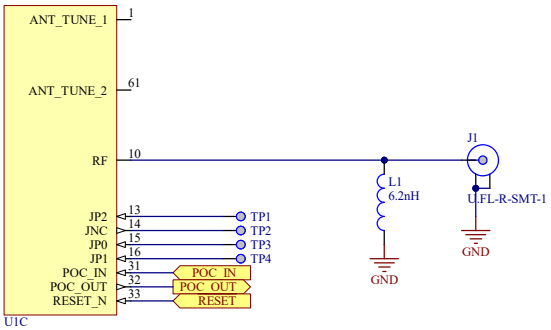


Figure 8.2. RF, Debug, and Reset Connection

Note:

1. Place L1 close to the RF pin.
2. It is mandatory to follow the reference schematics for optimal RF performance.
3. Maintain 50 ohm characteristic impedance for RF traces.
4. J1: In-built antenna or an external antenna (with U.FL connector) can be used.
5. It is recommended to add microwave coaxial switch connector (Example : Murata's MM8430-2610RA1) or U.FL connector for conducted measurements.
6. Additional matching circuit to be provided near the antenna, based on antenna used and location on the board.

8.1.3 GPIO Connection

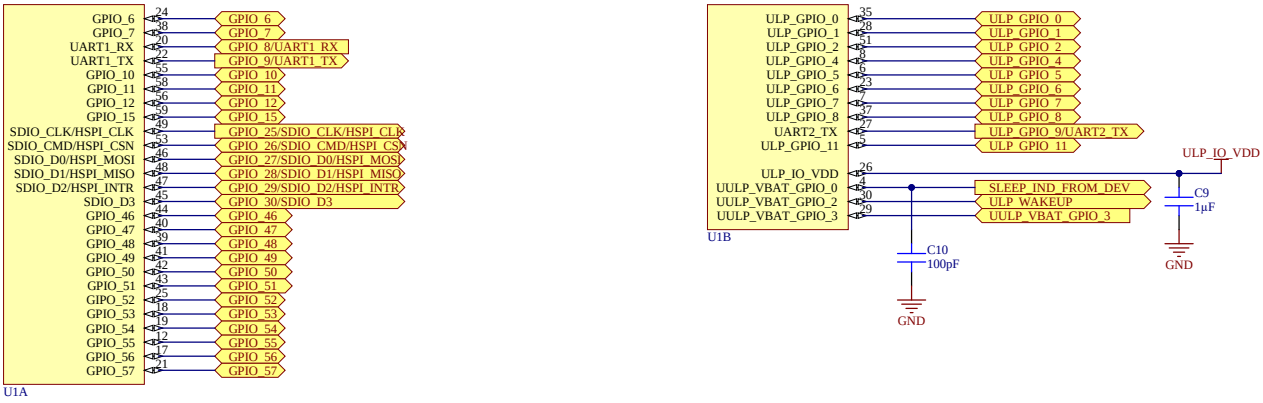


Figure 8.3. GPIO Connection

Note:

1. Place all the decoupling capacitors close to the module pins.
2. IO_VDD, SDIO_IO_VDD, ULP_IO_VDD can be powered independently by different voltage sources based on their corresponding signals voltage levels requirements. Voltages must be as per Table 7.2 Recommended Operating Conditions on page 28.
3. Even if GPIOs are not used, their respective IO domains must still be connected to the power supply.
4. Place filtering capacitor C10 close to Module Pin.
5. C10 has to be added irrespective of UULP_VBAT_GPIO_0 pin usage.

8.1.4 Reset

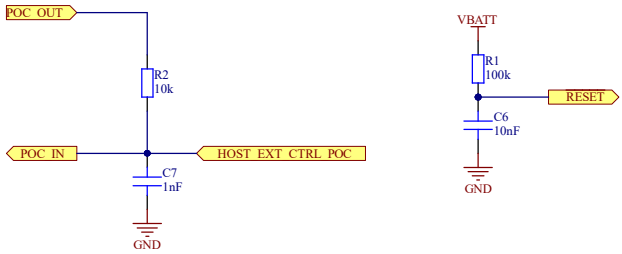


Figure 8.4. Reset Configuration

Note:

1. The configuration shown allows for blackout monitor functionality along with external reset of the SiWN917 module.
2. The POC_IN signal connects to the POC_IN pin on the SiWN917 module. POC_IN resets all the internal blocks of the IC.
3. The Si917_RESET signal connects to the RESET_N pin on the SiWN917 module. It is recommended to use the RC filter as shown. RESET_N is an open-drain output pin that will be pulled low when POC_IN goes low.
4. The POC_OUT signal connects to the POC_OUT pin on the SiWN917 module. POC_OUT is an active-low, push-pull output from the internal blackout monitor. In this configuration, it is isolated from the external HOST_EXT_CTRL_POC signal with a series resistor. In applications without external host control (HOST_EXT_CTRL_POC), POC_OUT may be directly connected to POC_IN. Without external host control to the POC_IN pin, the module cannot be reset multiple times after power-on.
5. The HOST_EXT_CTRL_POC signal connects to a GPIO of an external host processor. In this configuration, HOST_EXT_CTRL_POC must be an open-drain output to allow POC_OUT to control POC_IN.
6. HOST_EXT_CTRL_POC must be at the same voltage level as the VBATT supply pin.

8.1.5 LF Clock Option

Note: For Wi-Fi, BLE, and Co-Ex power saving use cases, Silicon Labs mandates an external clock to be used on ULP_VBAT_GPIO_3 pin for the low-frequency clock source to maintain timing accuracy requirements and optimize power consumption.

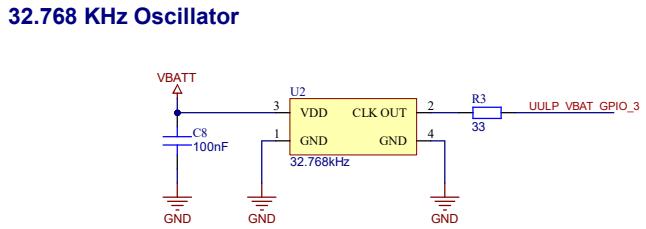


Figure 8.5. 32.768 kHz Clock Oscillator

8.1.6 Flash Memory Configurations

Figure 8.6. In-Package Flash Powered From On-Chip LDO Supply

8.1.7 Host Interface

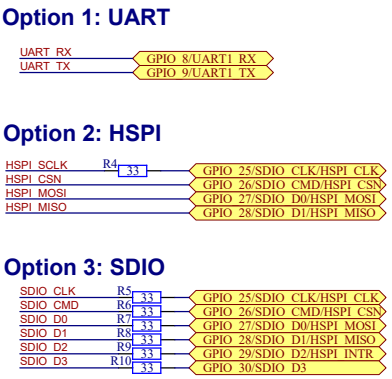


Figure 8.7. Host Interface Options

Note:

1. In UART mode, ensure that the input signals, UART_RX and UART_CTS are not floating when the device is powered up and reset is de-asserted. This can be done by ensuring that the host processor configures its signals (outputs) before de-asserting the reset.
2. In HSPI mode, ensure that the input signals, HSPI_CSN and HSPI_CLK are not floating when the device is powered up and reset is de-asserted. This can be done by ensuring that the external Host processor configures its signals (outputs) before de-asserting the reset. HSPI_INTR is the interrupt signal driven by the secondary device. This signal may be configured as Active-high or Active-low. If it is active-high, an external pull-down resistor is required. If it is active-low, an external pull-up resistor is required. The following actions can be carried out by the host processor during power-up of the device, and before/after ULP Sleep mode.
   a. To use the signal in the Active-high or Active-low mode, ensure that during the power up of the device, the Interrupt is disabled in the Host processor before de-asserting the reset. After de-asserting the reset, the Interrupt needs to be enabled only after the HSPI initialization is done and the Interrupt mode is programmed to either Active-high or Active-low mode as required.
   b. The Host processor needs to disable the interrupt before the ULP Sleep mode is entered and enable it after HSPI interface is reinitialized upon wakeup from ULP Sleep.
3. In SDIO mode, pull-up resistors should be present on SDIO_CMD & SDIO Data lines as per the SDIO physical layer specification version 2.0.
4. R4 to R10 are optional resistors for Signal Integrity.
5. 33 ohm on SDIO_CLK/HSPI_CLK has to be near the source of the clock, and not near the module.

8.1.8 Bill of Materials

Table 8.1. Bill of Materials

Line No	Quanti-ty	Designator	Value	Manufacturer	Manufacturer PN	Description	Toler-ance	Rating
1	5	C1, C3, C4, C5, C9	1 uF	—	—	CAP CER 0402 X5R 1 uF 10 V 10 %	10 %	10 V
2	1	C2	18 pF	—	—	CAP CER 0201 C0G 18 pF 25 V 2 %	2 %	25 V
3	1	C6	10 nF	—	—	CAP CER 0402 X7R 10 nF 16 V 10 %	10 %	16 V
4	1	C7	1 nF	—	—	CAP CER 0402 X7R 1 nF 16 V 10 %	10 %	16 V
5	1	C8	100 nF	—	—	CAP CER 0402 X7R 100 nF 50 V 10 %	10 %	50 V
6	1	C10	100 pF	—	—	CAP CER 0402 X7R 100 pF 50 V 10 %	2 %	50 V
7	1	J1	U.FL-R- SMT-1	—	—	CONN RF 50 OHM UFL_2.6x2.6 SMD	—	—
8	1	L1	6.2 nH	—	—	IND Fixed 0201 6.2 nH 300 mA 600 mOhm 3 %	3 %	300 mA
9	1	R1	100 k	—	—	RES 0402 33 R 1/16 W 1 %	1 %	63 mW
10	1	R2	10 k	—	—	RES 0402 10 K 1/16 W 5 %	1 %	63 mW
11	8	R3, R4, R5, R6, R7, R8, R9, R10	33	—	—	RES 0402 33R 1/16 W 1 %	1 %	63 mW
12	1	U1	SiW917Y1GN	Silicon Labs	—	PCB Module SiW917Y1GN	—	—
13	1	U2	32.768 kHz	SiTIME	SiT1532AI-J4-DCC-32.768	SiTIME Oscillator CSPBGA 32.768 kHz 10 pF 100 ppm	—	—

8.2 SiW917Y1GA Schematics for Parts with Integral Antenna

8.2.1 System Supplies

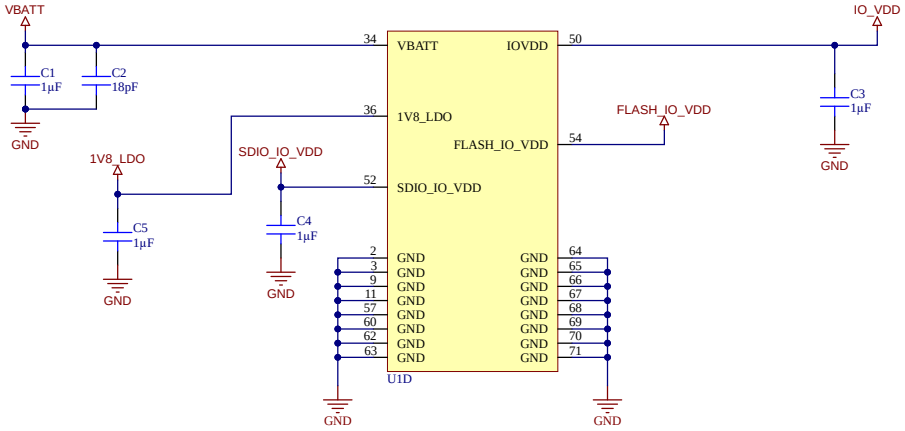


Figure 8.8. System Power Supplies

Note:

1. Place all the decoupling capacitors close to the module pins.
2. IO_VDD, SDIO_IO_VDD, ULP_IO_VDD can be powered independently by different voltage sources based on their corresponding signals voltage levels requirements. Voltages must be as per Table 7.2 Recommended Operating Conditions on page 28.
3. Even if GPIOs are not used, their respective IO domains must still be connected to the power supply.

8.2.2 RF, Debug, and Reset Connection

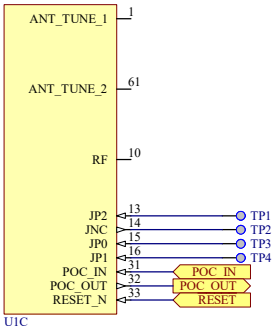


Figure 8.9. RF, Debug, and Reset Connection

Note:

1. It is mandatory to follow the reference schematics for optimal RF performance.

8.2.3 GPIO Connection

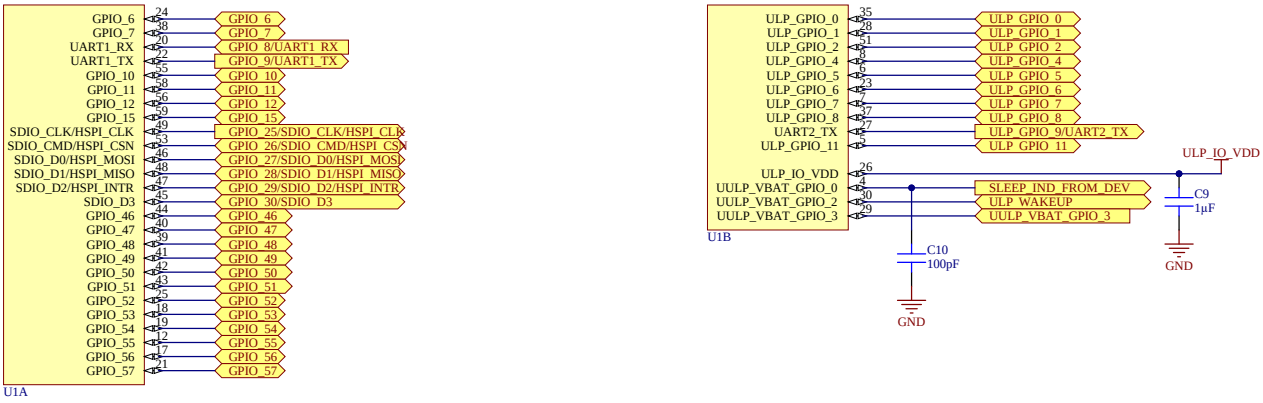


Figure 8.10. GPIO Connection

Note:

1. Place all the decoupling capacitors close to the module pins.
2. IO_VDD, SDIO_IO_VDD, ULP_IO_VDD can be powered independently by different voltage sources based on their corresponding signals voltage levels requirements. Voltages must be as per Table 7.2 Recommended Operating Conditions on page 28.
3. Even if GPIOs are not used, their respective IO domains must still be connected to the power supply.
4. Place filtering capacitor C10 close to Module Pin.
5. C10 has to be added irrespective of UULP_VBAT_GPIO_0 pin usage.

8.2.4 Reset

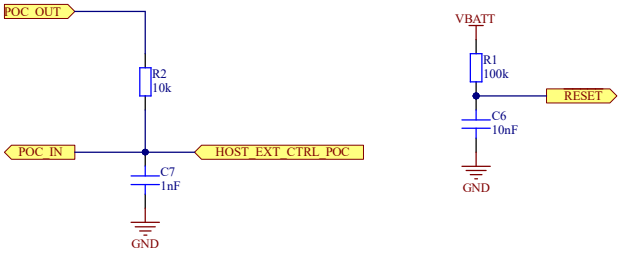


Figure 8.11. Reset Configuration

Note:

1. The configuration shown allows for blackout monitor functionality along with external reset of the SiWN917 module.
2. The POC_IN signal connects to the POC_IN pin on the SiWN917 module. POC_IN resets all the internal blocks of the IC.
3. The Si917_RESET signal connects to the RESET_N pin on the SiWN917 module. It is recommended to use the RC filter as shown. RESET_N is an open-drain output pin that will be pulled low when POC_IN goes low.
4. The POC_OUT signal connects to the POC_OUT pin on the SiWN917 module. POC_OUT is an active-low, push-pull output from the internal blackout monitor. In this configuration, it is isolated from the external HOST_EXT_CTRL_POC signal with a series resistor. In applications without external host control (HOST_EXT_CTRL_POC), POC_OUT may be directly connected to POC_IN. Without external host control to the POC_IN pin, the module cannot be reset multiple times after power-on.
5. The HOST_EXT_CTRL_POC signal connects to a GPIO of an external host processor. In this configuration, HOST_EXT_CTRL_POC must be an open-drain output to allow POC_OUT to control POC_IN.
6. HOST_EXT_CTRL_POC must be at the same voltage level as the VBATT supply pin.

8.2.5 LF Clock Option

Note: For Wi-Fi, BLE, and Co-Ex power saving use cases, Silicon Labs mandates an external clock to be used on UULP_VBAT_GPIO_3 pin for the low-frequency clock source to maintain timing accuracy requirements and optimize power consumption.

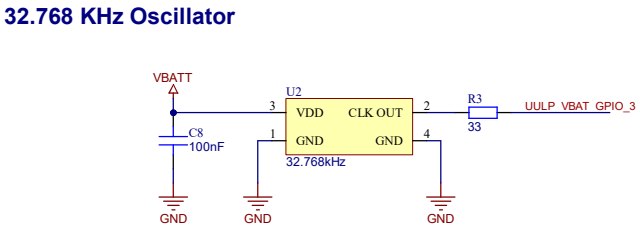


Figure 8.12. 32.768 kHz Clock Oscillator

8.2.6 Flash Memory Configurations

Figure 8.13. In-Package Flash Powered From On-Chip LDO Supply

8.2.7 Host Interface

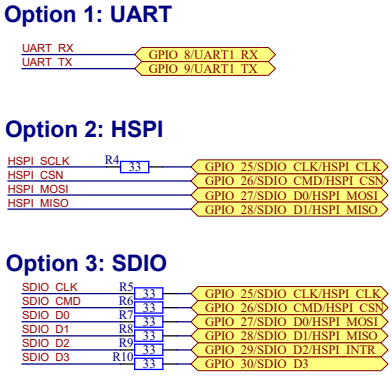


Figure 8.14. Host Interface Options

1. In UART mode, ensure that the input signals, UART_RX and UART_CTS are not floating when the device is powered up and reset is de-asserted. This can be done by ensuring that the host processor configures its signals (outputs) before de-asserting the reset.
2. In HSPI mode, ensure that the input signals, HSPI_CSN and HSPI_CLK are not floating when the device is powered up and reset is de-asserted. This can be done by ensuring that the external Host processor configures its signals (outputs) before de-asserting the reset. HSPI_INTR is the interrupt signal driven by the secondary device. This signal may be configured as Active-high or Active-low. If it is active-high, an external pull-down resistor is required. If it is active-low, an external pull-up resistor is required. The following actions can be carried out by the host processor during power-up of the device, and before/after ULP Sleep mode.
   a. To use the signal in the Active-high or Active-low mode, ensure that during the power up of the device, the Interrupt is disabled in the Host processor before de-asserting the reset. After de-asserting the reset, the Interrupt needs to be enabled only after the HSPI initialization is done and the Interrupt mode is programmed to either Active-high or Active-low mode as required.
   b. The Host processor needs to disable the interrupt before the ULP Sleep mode is entered and enable it after HSPI interface is reinitialized upon wakeup from ULP Sleep.
3. In SDIO mode, pull-up resistors should be present on SDIO_CMD & SDIO Data lines as per the SDIO physical layer specification version 2.0.
4. R4 to R10 are optional resistors for Signal Integrity.
5. 33 ohm on SDIO_CLK has to be near the source of the clock, and not near the module.

8.2.8 Bill of Materials

Table 8.2. Bill of Materials

Line No	Quanti-ty	Designator	Value	Manufacturer	MAnufacturer PN	Description	Toler-ance	Rating
1	5	C1, C3, C4, C5, C9	1 uF	—	—	CAP CER 0402 X5R 1 uF 10 V 10 %	10 %	10 V
2	1	C2	18 pF	—	—	CAP CER 0201 C0G 18 pF 25 V 2 %	2 %	25 V
3	1	C6	10 nF	—	—	CAP CER 0402 X7R 1 nF 16 V 10 %	10 %	16 V
4	1	C7	1 nF	—	—	CAP CER 0402 X7R 1 nF 16 V 10 %	10 %	16 V
5	1	C8	100 nF	—	—	CAP CER 0402 X7R 100 nF 50 V 10 %	10 %	50 V
6	1	C10	100 pF	—	—	CAP CER 0201 C0G 100 pF 50 V 2 %	2 %	50 V
7	1	R1	100 k	—	—	RES 0402 100 K 1/16 W 1 %	1 %	63 mW
8	1	R2	10 k	—	—	RES 0402 10 K 1/16 W 1 %	1 %	63 mW
9	8	R3, R4, R5, R6, R7, R8, R9, R10	33	—	—	RES 0402 33 R 1/16 W 1 %	1 %	63 mW
10	1	U1	SiW917Y1GA	Silicon Labs	—	PCB Module SiW917Y1GA	—	—
11	1	U2	32.768 kHz	SiTime	SiT1532AI-J4-DCC-32.768	SiTIME Oscillator CSPBGA 32.768 kHz 10 pF 100 ppm	—	—

8.3 Layout Guidelines

1. The RF (Module Pin No. 10) signal may be directly connected to an on-board chip antenna or terminated in an RF pin connector of any form factor for enabling the use of external antennas. RF pin can be left floating if not used.
2. Antenna clearance area is not necessary if you are using an external antenna attached to the RF pin.
3. The RF pin trace on RF pin should have a characteristic impedance of 50 Ohms. Any standard 50 Ohms RF pin trace (Microstrip or Coplanar wave guide) may be used. The width of the 50 Ohms line depends on the PCB stack, e.g., the dielectric of the PCB, thickness of the copper, thickness of the dielectric and other factors. Consult the PCB fabrication unit to get these factors right.
4. To evaluate transmit and receive performance like Tx Power, and EVM and Rx sensitivity, an RF pin connector would be required. A suggestion is to place a 'microwave coaxial connector with switch' between RF pin and the antenna.
5. Each GND pin must have a separate GND via. Place the ground vias as close to the ground pads as possible.
6. All decoupling capacitors placement must be as much close as possible to the corresponding power pins, and the trace lengths as short as possible.
7. Ensure all power supply traces widths are sufficient enough to carry corresponding currents.
8. Add GND copper pour underneath Module in all layers, for better thermal dissipation.
9. Add solid GND copper pour underneath Module for better emission performance.

8.3.1 Installation Guide for SiW917Y1GN Module

Figure 8.15 on page 60 below shows the recommended layout for SiW917Y1GN when using an u.fl connector for an external antenna. The short RF trace from the RF pad of the module to the pad of the u.fl connector must be 50 ohm and exactly the same width as the RF pad of the module, i.e., 700 µm. Figure 8.15 SiW917Y1GN Top Layer Application Layer with u.fl Connector on page 60 shows two examples on practical implementations of such a trace. The widths S is fixed to 700 um. The height h depends on the PCB stack-up, and the gap width W is adjusted until the impedance of the trace is exactly 50 ohm. Online calculators for coplanar waveguide with ground can be used to calculate the width W for any specific PCB stack-up. The integrator must consider using a unique connector, such as a "reverse polarity SMA" or "reverse thread SMA", if detachable antenna is offered with the host chassis.

Ground vias underneath the module must be used extensively especially around the rectangular GND pins to enable heat transfer from the bottom of the module to the GND plane of the host board. Routing signal lines elsewhere underneath the module is acceptable.

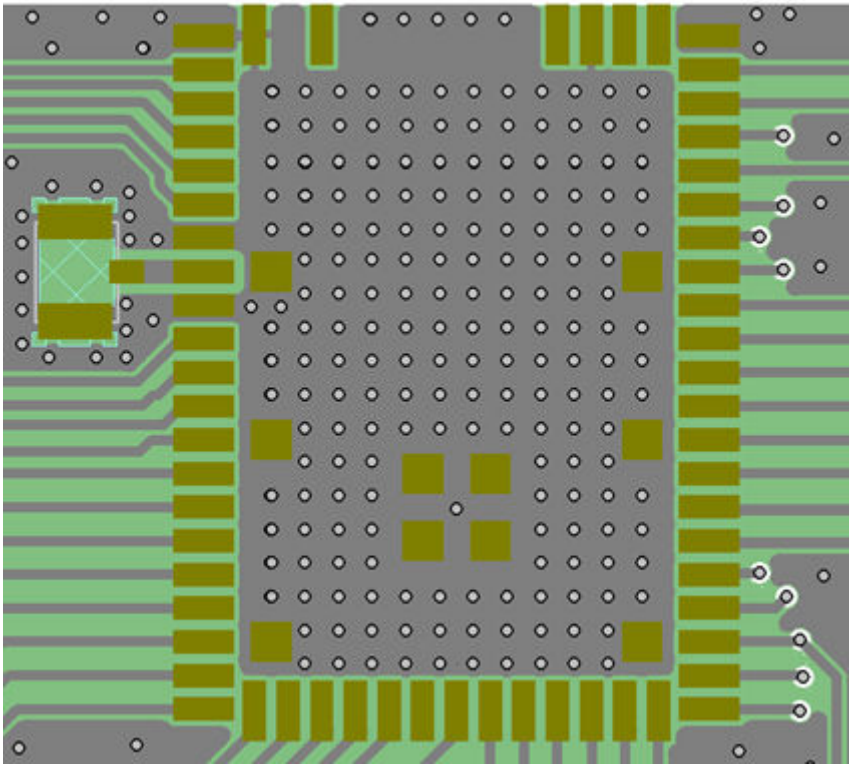


Figure 8.15. SiW917Y1GN Top Layer Application Layer with u.fl Connector

The typical permittivity of PCB laminate is 4.6. If assuming permittivity of 4.6, in the example shown in Figure 8.16 on page 61 the dimensions would be:

S = 700 um

h = 420 um

W = 332 um

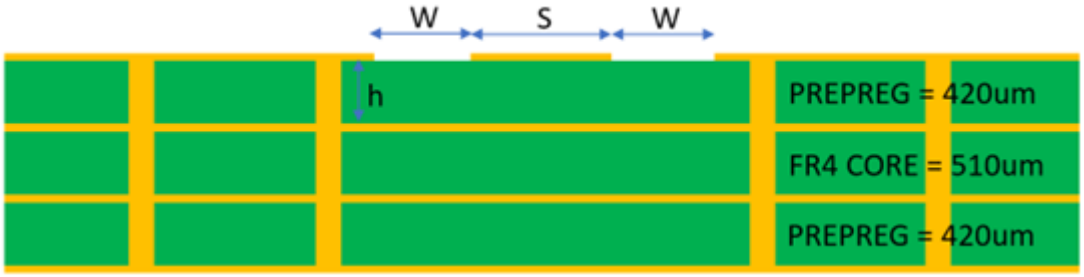


Figure 8.16. Example Implementation of a Co-planar Wave Guide with Ground and Thick Prepeg

Similarly, if assuming permittivity of 4.6, in the example shown in Figure 8.16 on page 61 the dimensions would be:

S = 700 um

h = 730 um

W = 132 um

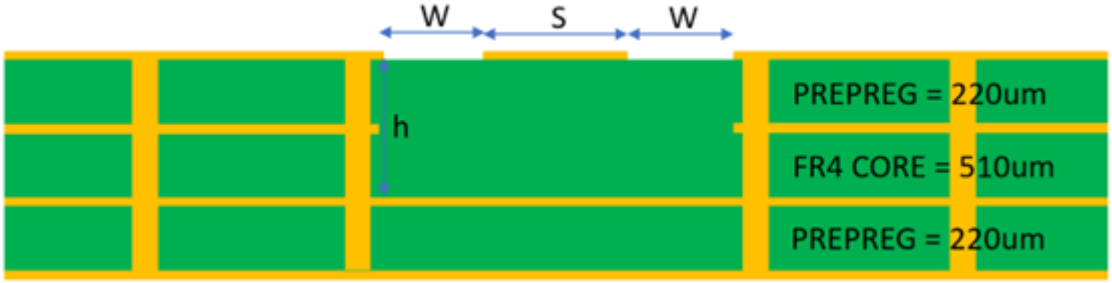
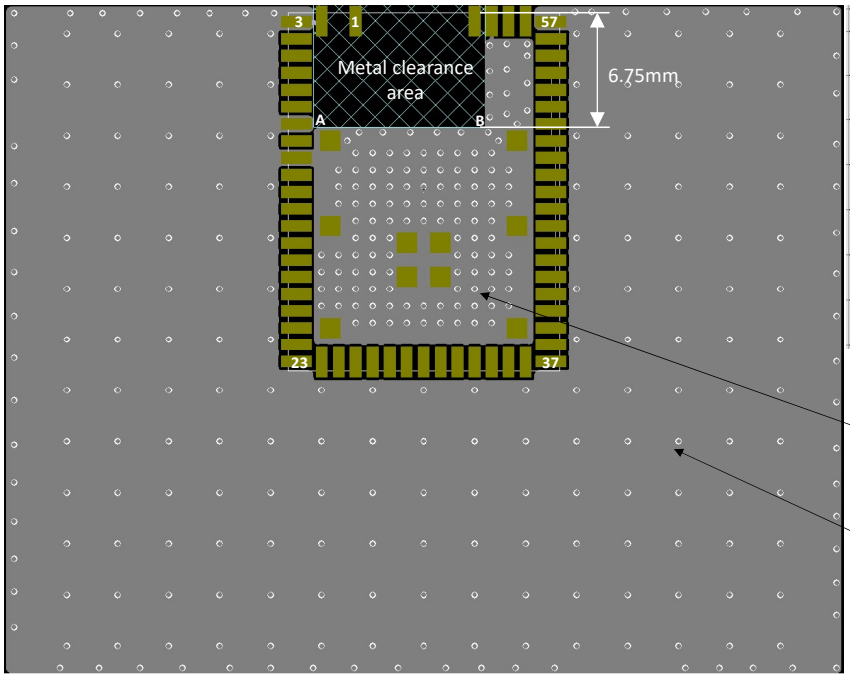


Figure 8.17. Example Implementation of a Co-planar Wave Guide with Ground and Thin Prepeg

8.3.2 Installation Guide for SiW917Y1GA Module



	X-cordinate (mm)	Y-cordinate (mm)
A (Corner of the metal clearance)	-6.5	3.8
B (Corner of the metal clearance)	3.6	3.8
1 (Center point of PAD1)	-4	10.05
3 (Center point of PAD3)	-7.5	10
23 (Center point of PAD23)	-7.5	-10
37 (Center point of PAD37)	7.5	-10
57 (Center point of PAD 57)	7.5	10

Figure 8.18. Application Layout of SiW917Y1GA

For optimal performance of the SiW917Y1GA:

- Place the module aligned to the edge of the application PCB, as illustrated in Figure 8.18 on page 62.
- Leave the antenna clearance area void of any traces, components, or copper on all layers of the application PCB.
- Connect all ground pads directly to a solid ground plane.
- Place the ground vias as close to the ground pads as possible.
- Avoid plastic or any other dielectric material in direct contact with the antenna.

Figure 8.19 Figure on page 63 shows example layout scenarios which will lead to degraded performance and possible EMC issues with the module.

Ground vias underneath the module must be used extensively especially around the rectangular GND pins to enable heat transfer from the bottom of the module to the GND plane of the host board. Routing signal lines elsewhere underneath the module is acceptable.

Antennas are by nature affected by the surrounding PCB design and in particular the size and shape of the ground surrounding the antenna. The wide band antenna of SiW917Y1GA is designed to operate in various size/shape application boards and the antenna is not sensitive to dielectric material near the antenna. However, in certain extreme circumstances, such as extremely small board or narrow board, the antenna can be detuned enough to have an impact to the range, EVM characteristics and in-band emissions. In such cases it is possible to fine tune the antenna by using one or two external capacitors or inductors connected between the ANT_TUNE1 and GND and/or ANT_TUNE2 and GND. An example is shown in the Figure 8.20 Figure on page 63. Finding the correct value for these components requires empirical testing and measuring the antenna return loss. Typically capacitor with value between 0.5 pF to 2 pF or inductor with value between 2 nH to 4 nH can be used for tuning. (See the 8.4.2 Proximity to Human Body below.)

The best antenna performance is achieved when the board width is 50 mm and the antenna is placed at the center of the board edge. Having wider or narrower PCB will have up to 25 % impact to the range. If the board is narrower than 35mm or wider than 100 mm, it is possible that external fine tuning becomes necessary to maintain the EVM performance.

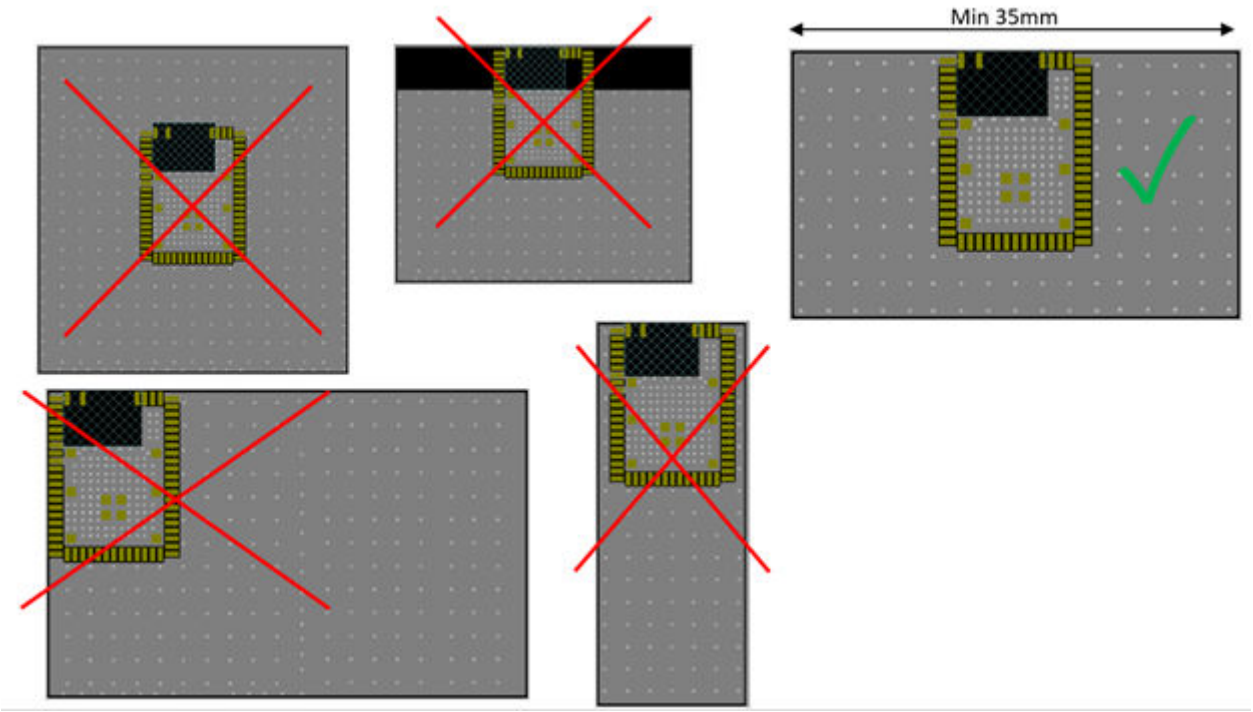


Figure 8.19. Layout Examples

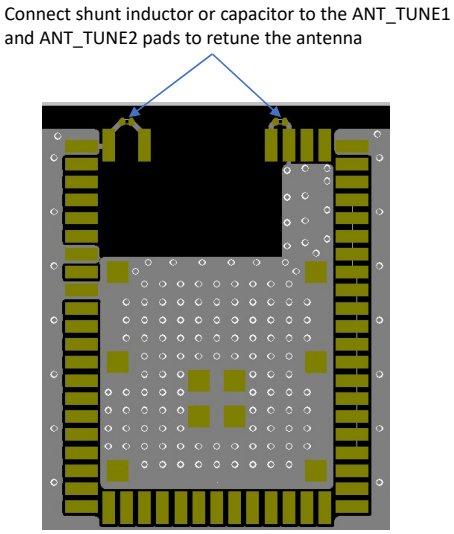


Figure 8.20. External Antenna Fine Tuning Option

8.4 SiW917Y1GA Antenna Radiation and Efficiency

Typical radiation patterns for the built-in antenna under optimal operating conditions are plotted in the figures that follow.

Table 8.3. Antenna Efficiency and Peak Gain

Parameter	With optimal layout	Note
Efficiency	-1 dB	Antenna gain and radiation patterns have a strong dependence on the size and shape of the application PCB the module is mounted on, as well as on the proximity of any mechanical design to the antenna. Refer to 8.3.2 Installation Guide for SiW917Y1GA Module for recommendations to achieve optimal antenna performance.
Peak gain	2.26 dBi	
VSWR	2:1	

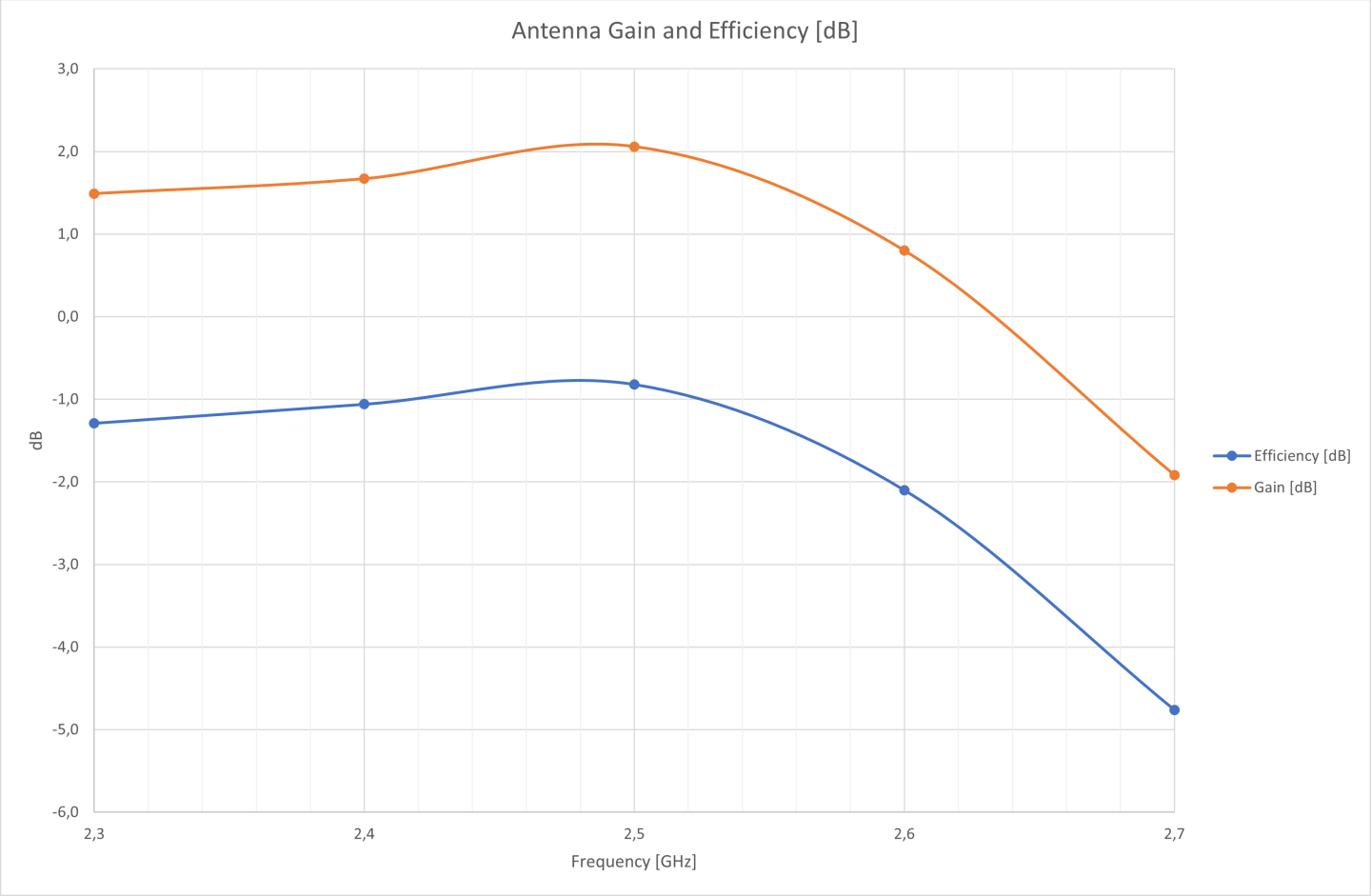


Figure 8.21. Efficiency and Gain of the Built-in Antenna

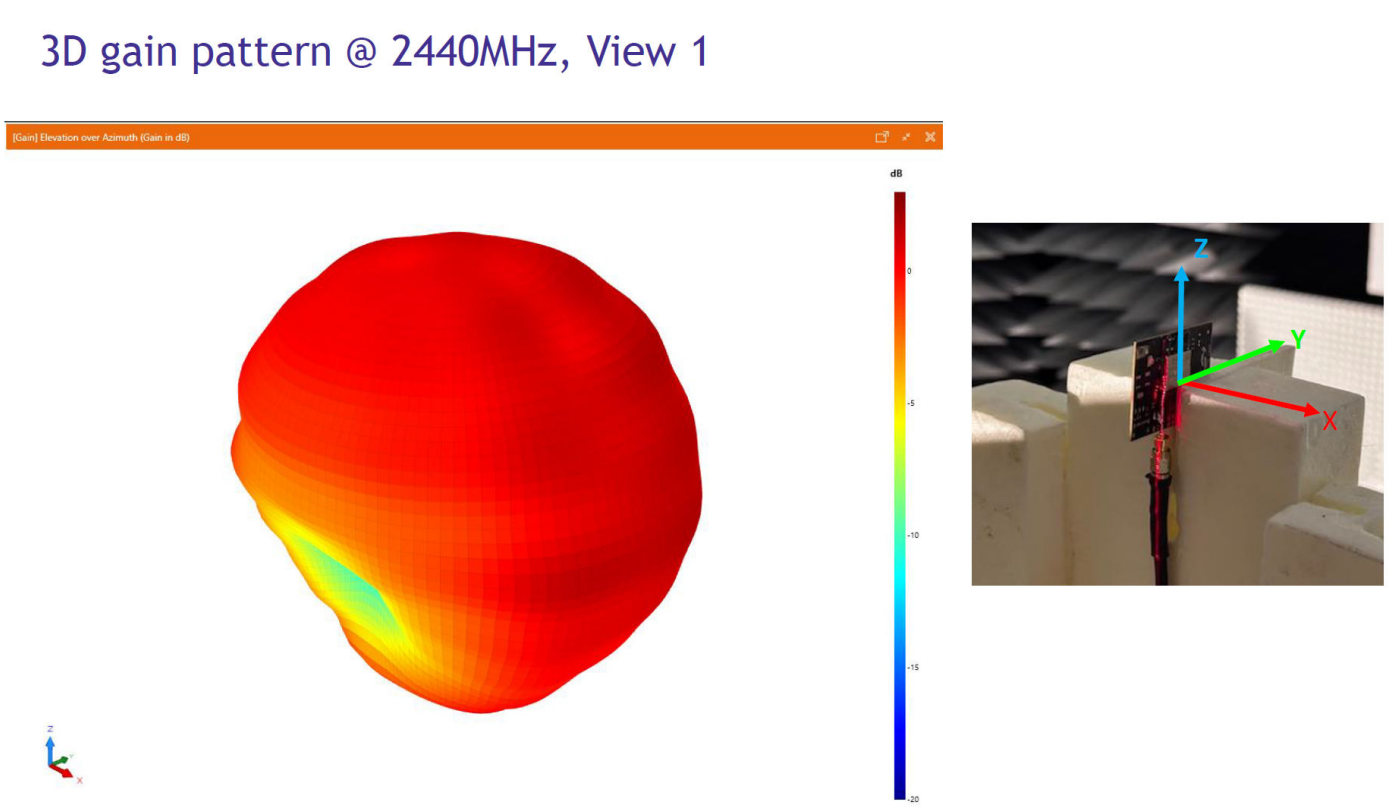


Figure 8.22. 3D Radiation Pattern of the Build-In Antenna

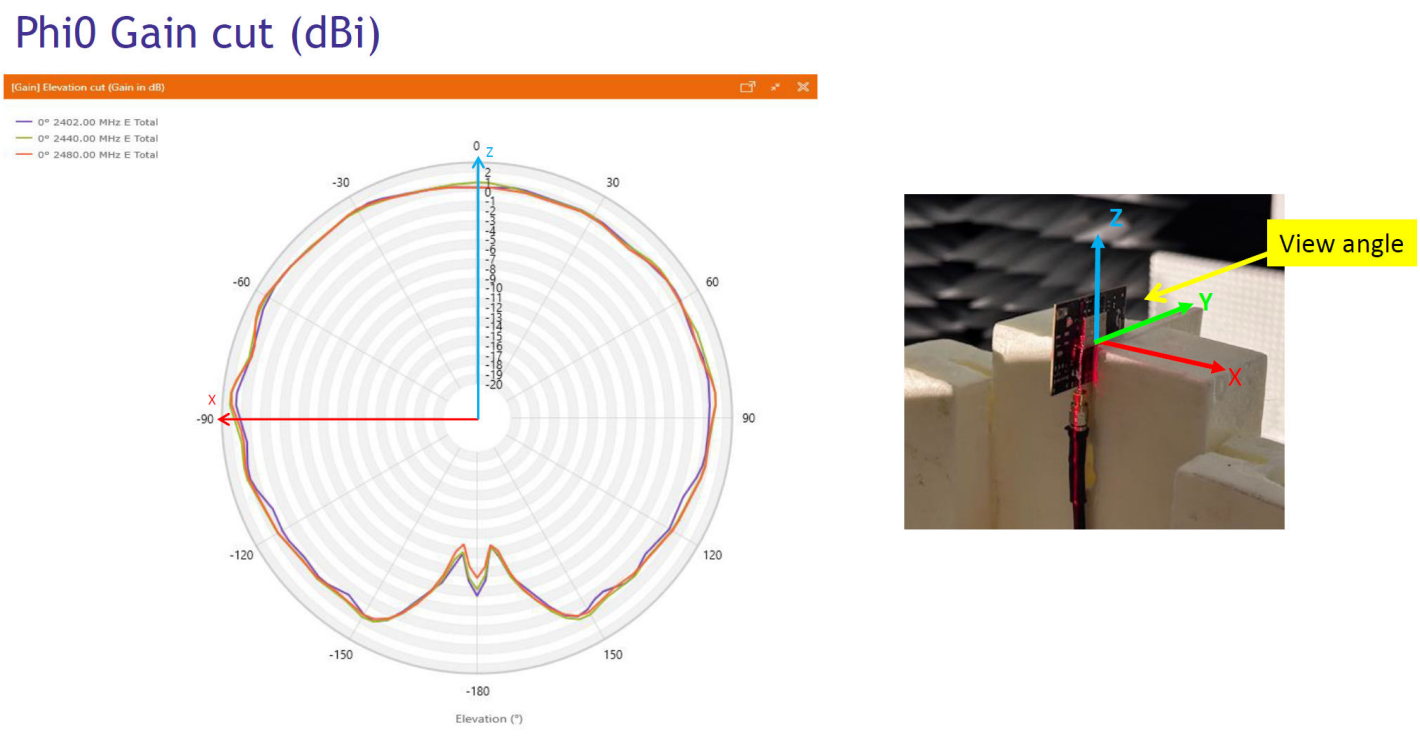


Figure 8.23. Typical 2D Antenna Radiation Patterns - Phi 0° (Side View) Gain (dBi)

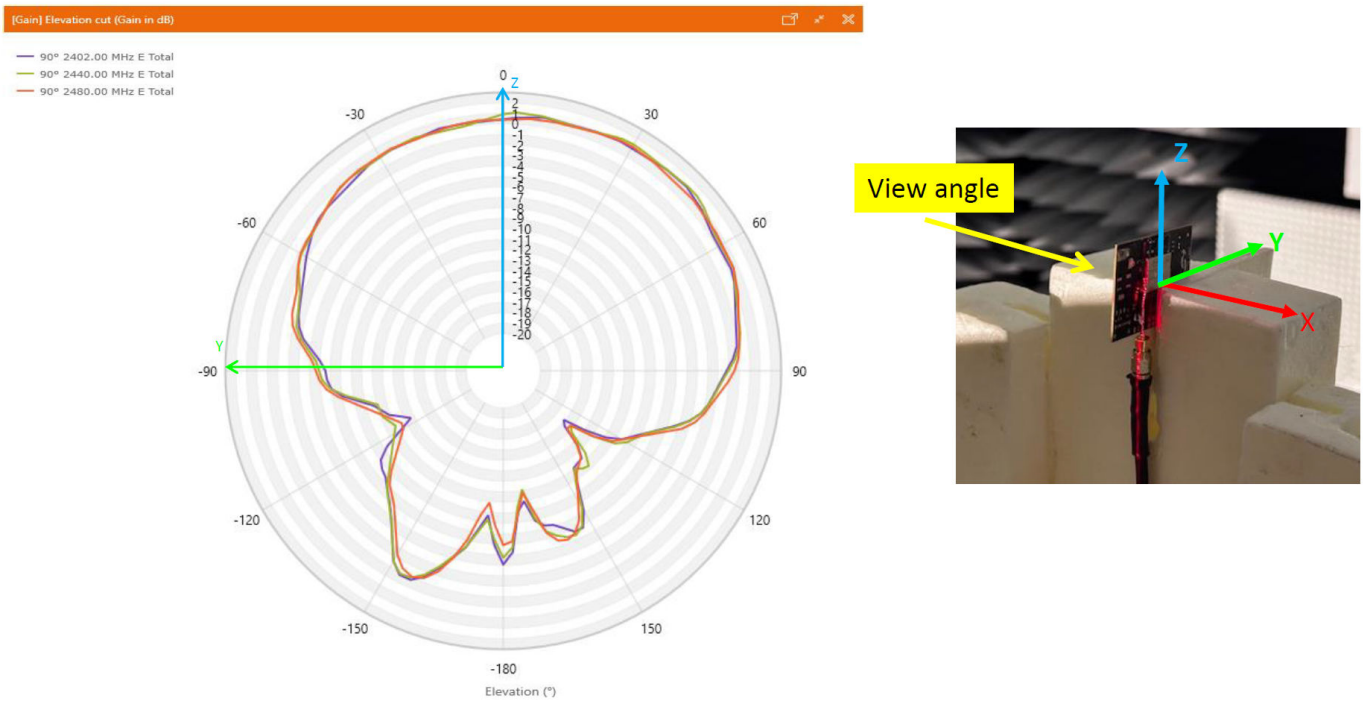


Figure 8.24. Typical 2D Antenna Radiation Patterns - Phi 90° (Top View) Gain (dBi)

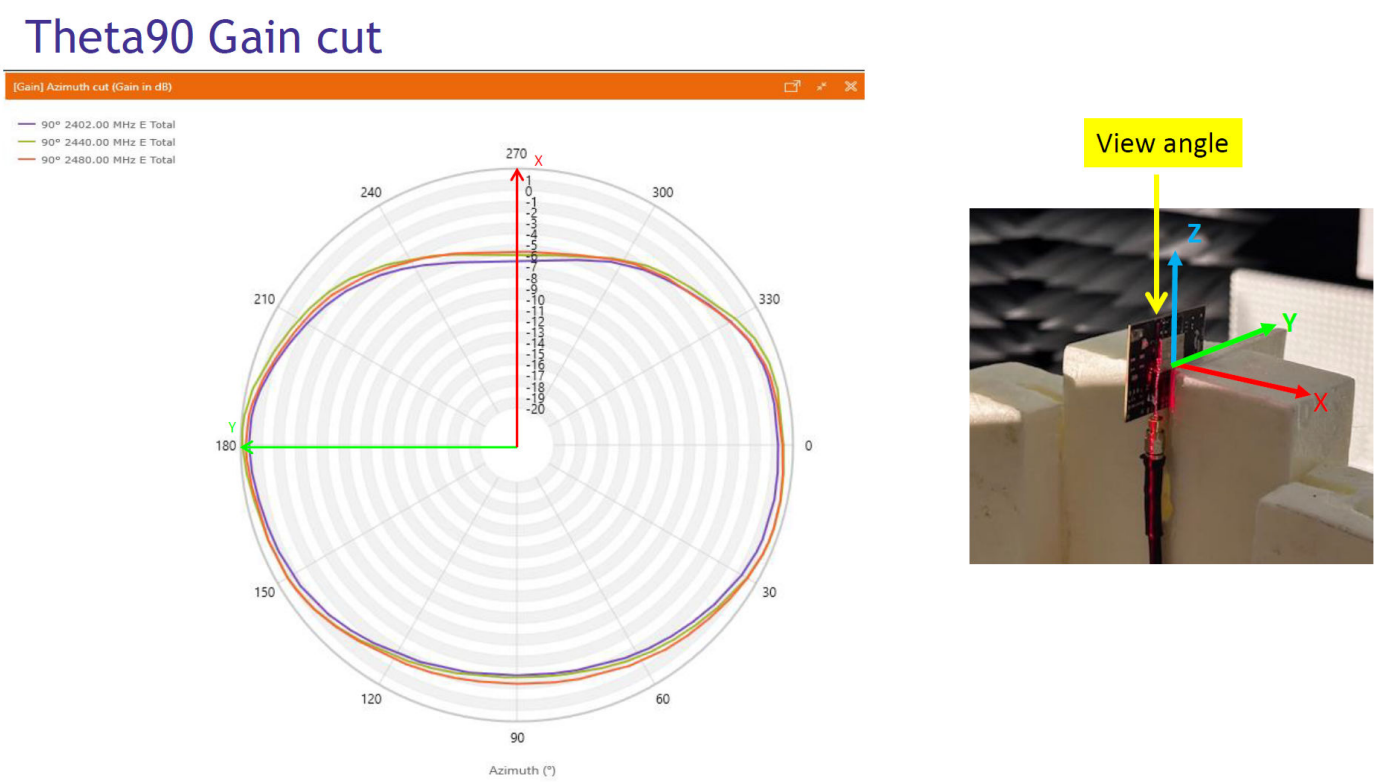


Figure 8.25. Typical 2D Antenna Radiation Patterns - Theta 90° (Front View) Gain (dBi)

8.4.1 Proximity to Other Materials

Avoid placing plastic or any other dielectric material in close proximity to the antenna. Conformal coating and other thin dielectric layers are acceptable directly on top of the antenna region, but this will also negatively impact antenna efficiency and reduce range.

Any metallic objects in close proximity to the antenna will prevent the antenna from radiating freely. The minimum recommended distance of metallic and/or conductive objects is 10 mm in any direction from the antenna except in the directions of the application PCB ground planes.

8.4.2 Proximity to Human Body

Placing the module in contact with or very close to the human body will negatively impact antenna efficiency and reduce range.

Note: When it comes to modular certifications, following the manufacturer's design guidelines is critical for ensuring that compliance is maintained and modular approvals remain valid, in particular with regards to the carrier (host) PCB size, thickness, relative permittivity, and/or module placement. A modular certification is still valid if no antenna tuning is applied to compensate for reduced performance in terms of range, which may result from sub-optimal carrier PCB size, thickness, relative permittivity, module placement, and/or proximity to other materials such as assembly housing. Conversely, a custom antenna tuning might invalidate a modular certification, unless it is done to compensate for the degradation caused by a printed circuit board deviating from the manufacturer’s best-case reference design in terms of size, thickness, relative permittivity, and/or module placement. In such case, a Permissive Change to a modular approval might become necessary, depending on the resulting performance of the end-product relative to the certified module's test reports, in particular with regards to spurious emission levels, as found during spot-checking. For example, in the FCC case, a Class 1 Permissive Change (C1PC) is considered if the host PCB modifications do not increase emissions. Class 2 Permissive Change (C2PC) is considered if the modifications degrade the emissions but remain below regulatory limits. Whether antenna tuning is applied or not, it is strongly recommended that spot-checking is performed in any case with the end-product having the transmitter(s) operating, to confirm that the host product meets all regulatory requirements under any circumstance. In the end, the emission levels established in the module certification are limits for the end device too and determine whether or not a Permissive Change should be considered. Since this is evaluated on a case-by-case basis, integrators must consult with the company providing certification services for their final product to identify the best approach.

9. Package Specifications

9.1 Dimensions

Table 9.1. Module Dimensions

Parameter	Value (LxWxH)	Units
Module Dimensions	21.10 x 16 x 2.30	mm
Tolerance	±0.2	mm

9.2 Package Outline

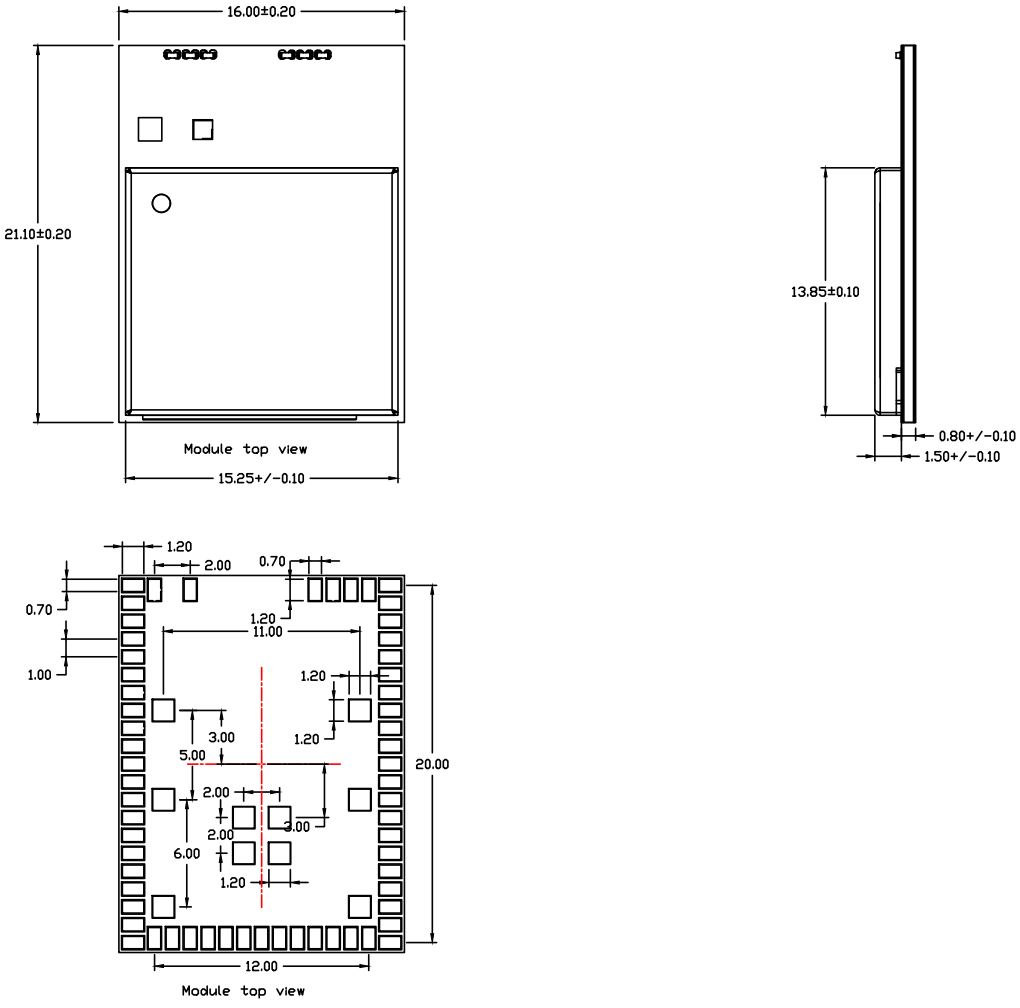


Figure 9.1. Package Outline

9.2.1 Pin Locations

Note: All coordinates in Table 9.2 Pin Locations on page 70 are in millimeters, and in TOP VIEW.

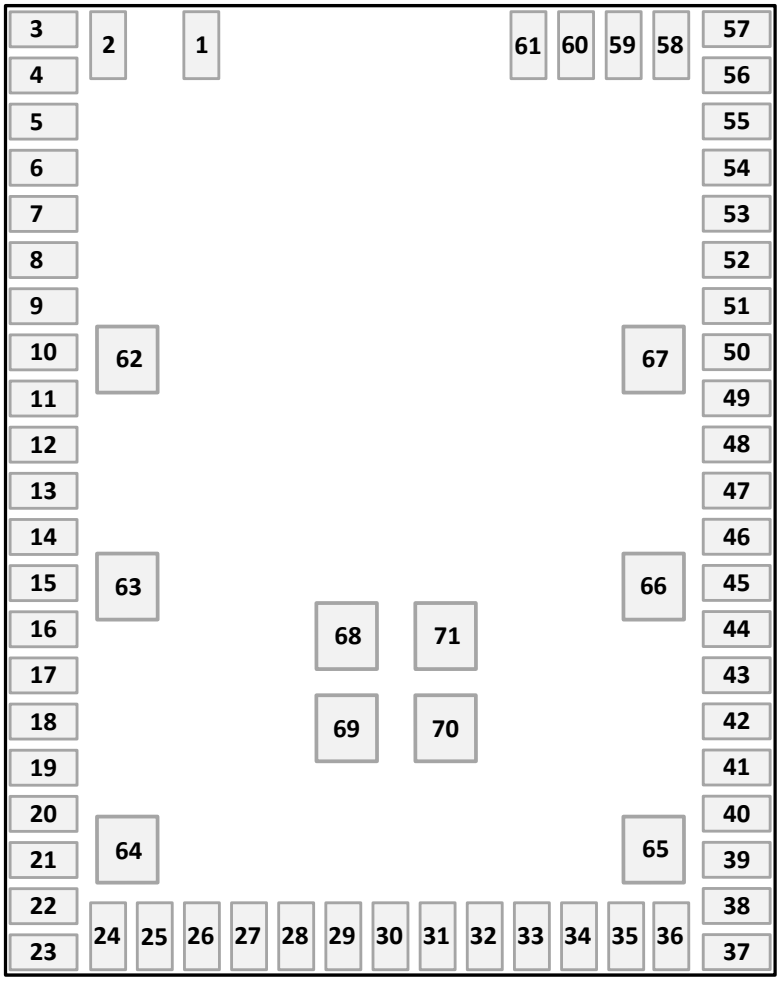


Figure 9.2. Pin Numbering

Table 9.2. Pin Locations

PAD X-Y Coordinates			
Pad #	**X**	**Y**	**Pad Size**
1	-4	9.75	(1.2 x 0.7) mm
2	-6	9.75	
3	-7.2	10	
23	-7.2	-10	
24	-6	-9.75	
36	6	-9.75	
37	7.2	-10	
57	7.2	-10	
58	6	9.75	
61	3	9.75	
62	-5.5	3	(1.2 x 1.2) mm
63	-5.5	-2	
64	-5.5	-8	
65	5.5	-8	
66	5.5	-2	
67	5.5	3	
68	-1	-3	
69	-1	-5	
70	1	-5	
71	1	-3	

9.3 PCB Landing Pattern

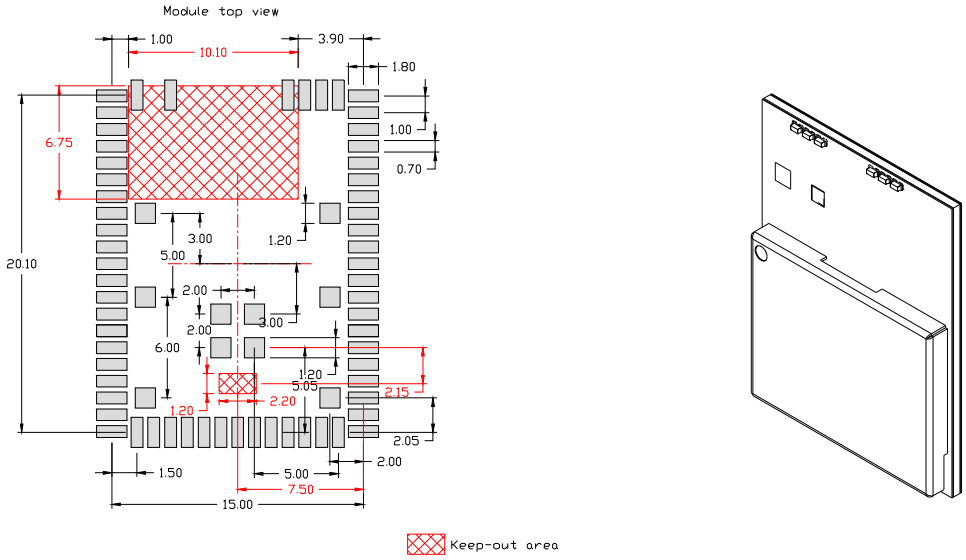


Figure 9.3. PCB Landing Pattern

Note:

1. We recommend allocating a dedicated hardware keep-out besides the antenna clearance area in the module layout to support future scalability within the same product series. Reserving this space enables smooth migration to upcoming part variants, minimizing the need for layout redesigns.
2. Both of the red-shaded areas shown above are keep-outs (metal clearance areas).

Table 9.3. PCB Landing Pattern Pin Locations

PAD X-Y Coordinates			
Pad #	**X**	**Y**	**Pad Size**
1	-4	10.05	(1.8 x 0.7) mm
2	-6	10.05	
3	-7.5	10	
23	-7.5	-10	
24	-6	-10.05	
36	6	-10.05	
37	7.5	-10	
57	7.5	10	
58	6	10.05	
61	3	10.05	

PAD X-Y Coordinates			
Pad #	**X**	**Y**	**Pad Size**
62	-5.5	3	(1.2 x 1.2) mm
63	-5.5	-2	
64	-5.5	-8	
65	5.5	-8	
66	5.5	-2	
67	5.5	3	
68	-1	-3	
69	-1	-5	
70	1	-5	
71	1	-3	

9.4 Module Marking Information

The figures below illustrate the markings on the single-band modules and the table explains the markings.

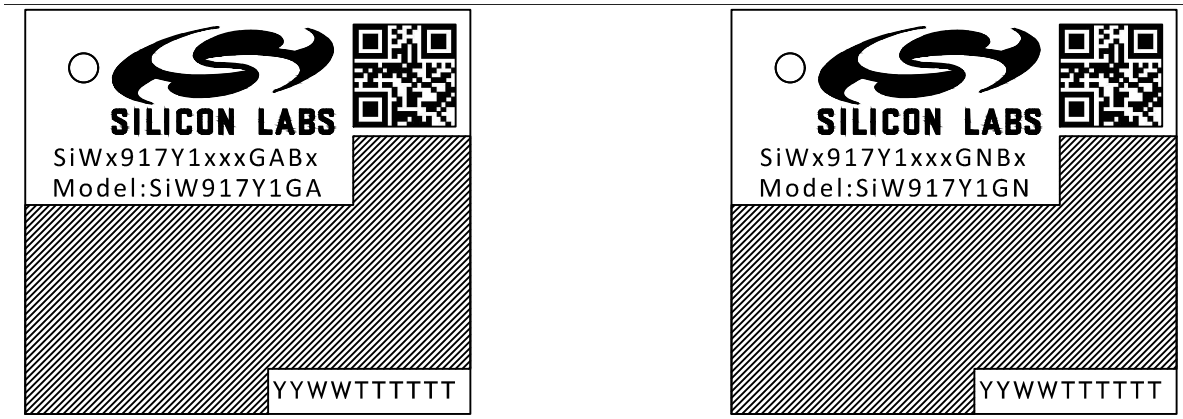


Figure 9.4. Module Marking Information

Marking		Description
Part	SiWx917Y1xxxGABx/ SiWx917Y1xxxGNBx	Orderable Part Number (OPN) designation
Model	SiW917Y1GA/SiW917Y1GN	Model Name designation, respectively for parts with integral antenna and RF pin
QR Code	YYWWMMABCDE	YY – Last two digits of the assembly year WW – Two-digit workweek when the device was assembled MMABCDE – Silicon Labs unit code
Lot Code	YYWWTTTTTT	YY – Last two digits of the assembly year WW – Two-digit workweek when the device was assembled TTTTTT – Manufacturing trace code. The first letter is the device revision
Compliance Marks	CE	Certification-related information, such as the CE and Giteki compliance marks, or the FCC and IC IDs, is being engraved on the hatched-out area, and/or printed on the back side of the module (silkscreen), in accordance with the requirements by regulatory bodies.

9.5 Moisture Sensitivity Level

SiWN917 modules are rated MSL3 (Moisture Sensitivity Level 3). Reels are delivered in packing which conforms to MSL3 requirements.

10. Soldering Recommendations

It is recommended that final PCB assembly of the SiWN917 follows the industry standard as identified by the Institute for Printed Circuits (IPC). This product is assembled in compliance with the J-STD-001 requirements and the guidelines of IPC-AJ-820. Surface mounting of this product by the end user is recommended to follow IPC-A-610 to meet or exceed class 2 requirements.

CLASS 1 General Electronic Products

Includes products suitable for applications where the major requirement is function of the completed assembly.

CLASS 2 Dedicated Service Electronic Products

Includes products where continued performance and extended life is required, and for which uninterrupted service is desired but not critical. Typically the end-use environment would not cause failures.

CLASS 3 High Performance/Harsh Environment Electronic Products

Includes products where continued high performance or performance-on-demand is critical, equipment downtime cannot be tolerated, end-use environment may be uncommonly harsh, and the equipment must function when required, such as life support or other critical systems.

Note: General SMT application notes are provided in AN1223: LGA Manufacturing Guidance.

11. Tape and Reel

The SiWN917 modules are delivered to the customer in cut tape (100 pcs) or reel (700 pcs) packaging having the dimensions below. All dimensions are given in mm unless otherwise indicated.

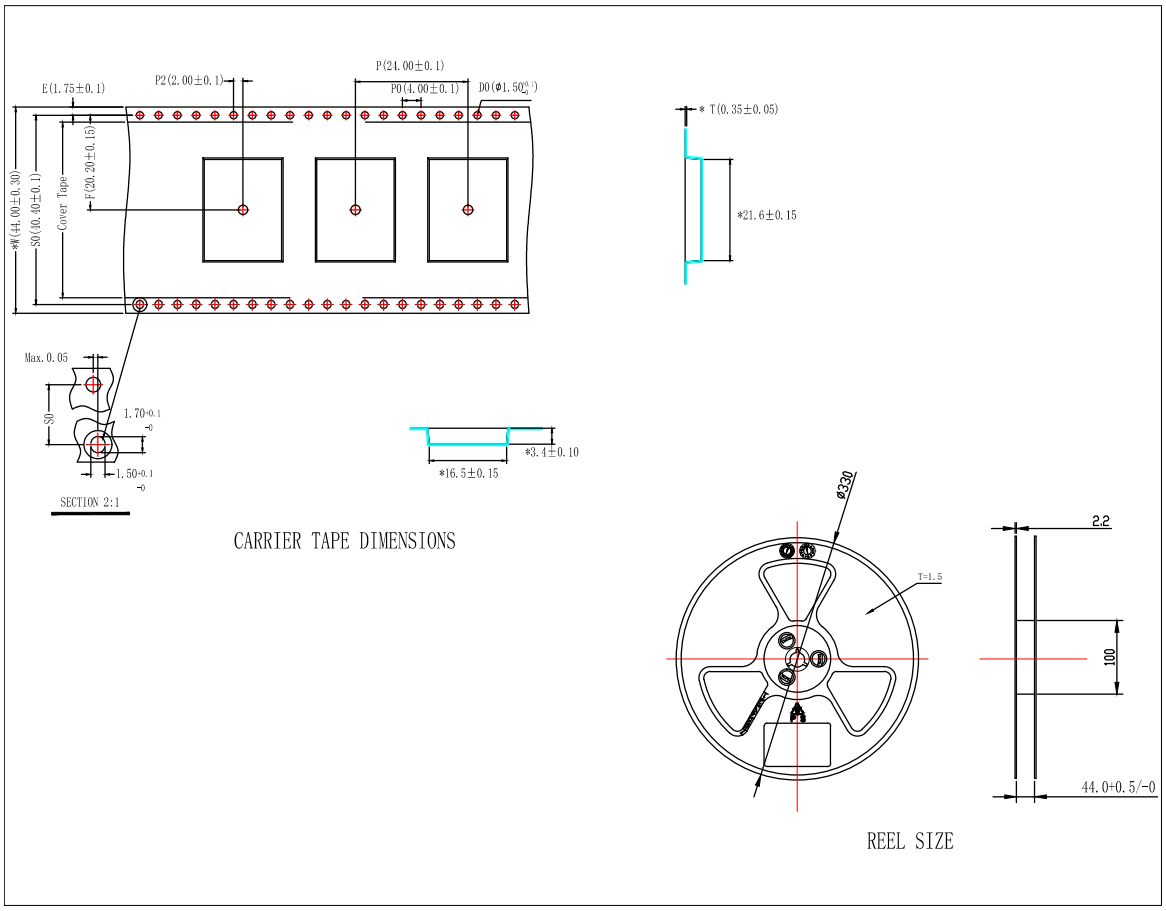


Figure 11.1. Carrier Tape Dimensions

12. Certifications

This section details the certification status of the SiW917Y1GA and SiW917Y1GN Connectivity Modules with regards to regional regulatory radio approvals. Where applicable, the status with the qualifications against the specifications of the supported global industrial wireless standards is given too.

The address of the legal manufacturer (technology owner) and certification applicant is:

SILICON LABS / SILICON LABORATORIES FINLAND OY
Alberga Business Park, Bertel Jungin aukio 3,
02600 Espoo, Finland

The SiW917Y1GA and SiW917Y1GN Connectivity Modules have brand name of "SILICON LABS".

"SILICON LABS" (and "Silicon Labs") is a trademark globally owned by the Silicon Laboratories Inc. corporation, and all branches and subsidiaries, including the above applicant, holds the right to use it.

12.1 Qualified Antennas

The SiW917Y1GA and SiW917Y1GN Connectivity Modules have been tested and certified for the use with respectively the built-in integral antenna and a reference external antenna attached to the module's RF pin denoted as RF_PORT. The intended antenna impedance is 50 Ω.

Performance characteristics for the built-in antenna are presented in 8.4 SiW917Y1GA Antenna Radiation and Efficiency. The details of the qualified external antenna(s) are summarized in Table 12.1 Qualified External Antenna(s) for the SiW917Y1GN Modules on page 76. The qualified external antenna(s) is(are) meant to be directly connected to the module's RF pin, with no active/non-linear component(s) along the RF path in between.

Table 12.1. Qualified External Antenna(s) for the SiW917Y1GN Modules

Manufacturer and Model	Type	Peak Gain	Impedance
TE Connectivity Ltd. (previously Linx Technologies Inc.), ANT-2.4-CW-CT-RPS	Connectorized Coaxial Dipole	+2.8 dBi	50 Ω

Any external antenna of the same general type and of equal or less peak directional gain compared to the one listed in the above table, and having similar in-band and out-of-band characteristics, can be used in the regulatory areas that have modular radio type approvals, such as USA and Canada, as long as spot-check testing of the host is performed to verify that no performance changes compromising compliance have been introduced. In the particular FCC case, to comply with e-CFR Title 47, Part 15, Subpart C, Section 15.203, the module integrator using an external antenna must ensure it has a unique connector or it is nondetachable.

When using instead an external antenna of a different type (such as a chip antenna, a host PCB trace antenna, or a patch) and/or having non-similar in-band and out-of-band characteristics, but still with a gain less than or equal to the maximum gain listed in the table above, in principle it can be added to the existing modular grant/certificate by means of a permissive change, for example with FCC and ISED. Typically, some radiated emission testing is demanded, but no modular or end-product re-certification is required. Please consult your certification house and/or a certification body and/or the module manufacturer for a confirmation of the correct procedures and for any authorization to perform a FCC's Change in ID and/or a ISED's Multiple Listing followed by the intended permissive changes.

On the other hand, products designed to be used with an external antenna having higher peak gain than the maximum gain listed in the table above are very likely to require full new end-product's radio type approvals, with certification IDs under the host manufacturer's ownership. Since the exact permissive change or registration or re-certification procedure is chosen on a case-by-case basis, consult your certification house and/or a certification body for understanding the correct approach based on your unique design.

In countries applying the ETSI standards, where manufacturers issue a self-Declaration of Conformity before placing their end-products in the market, like in the EU countries (and in the UK), the radiated emissions are always evaluated with the end-product and the external antenna type is not critical, but antennas with higher gain may violate some of the EIRP regulatory limits.

For Japan, where compliance testing is done conductively, the allowed external antennas are listed in the certificate and/or test report(s). Any other external antenna will have to be formally added to the list of approved antennas by the certificate holder: in this case, please reach out to the module manufacturer to discuss such addition, or consider certifying the end-product itself as an alternative.

12.2 CE and UKCA - EU and UK

The SiW917Y1GA and SiW917Y1GN modules have been tested against the relevant harmonized/designated standards and are in conformity with the essential requirements and other relevant requirements of the EU's Radio Equipment Directive (RED) (2014/53/EU) and of the UK's Radio Equipment Regulations (RER) (S.I. 2017/1206).

The modules are therefore entitled to carry the CE and UKCA compliance marks, while the respective formal Declarations of Conformity (DoCs) are available at the product web page, which is reachable starting from www.silabs.com.

Note that every final product integrating the SiW917Y1GA or the SiW917Y1GN Connectivity Module will need to go through full Safety and EMC assessments, for example in accordance with the ETSI 301 489-x applicable standards. In fact, Safety and EMC tests performed on a bare radio module are generally not supposed to provide confidence of Safety and EMC compliance of the final radio product as a whole.

Furthermore, it is ultimately the responsibility of the manufacturers to ensure the compliance of their complete final products also with respect to the RF performance. The specific product assembly is likely to have an impact on the RF radiated characteristics, when compared to the bare module. Hence, manufacturers should carefully consider RF radiated testing with the final product assembly, especially taking into account the gain of the external antenna if any, and the possible deviations in the PSD, EIRP and spurious emissions measurements, as defined in the ETSI EN 300 328 standard.

OEMs must also consider the importance of applying the compliance mark(s) to a visible location on their final products, on top of the need to writing down and signing the legal manufacturer's Declaration of Conformity for the final product itself. More in general, module customers assume full responsibility with regards to learning the guidelines and meeting the requirements for the compliance in each region where their end-products are marketed.

12.3 FCC - USA

This device complies with FCC's e-CFR Title 47, Part 15, Subpart C, Section 15.247 (and related relevant parts of the ANSI C63.10 standard) when operating with the built-in integral antenna or with an external antenna type as discussed in chapter 11.1.

Operation is subject to the following two conditions:

1. This device may not cause harmful interference, and
2. This device must accept any interference received, including interference that may cause undesirable operation.

Any changes or modifications not expressly approved by Silicon Labs could void the user’s authority to operate the equipment.

FCC RF Radiation Exposure Statement

This equipment complies with FCC radiation exposure limits set forth for an uncontrolled environment. End users must follow the specific operating instructions for satisfying the RF exposure compliance.

This transmitter meets the Mobile requirements at a distance of 20 cm and above from the human body, in accordance to the limit(s) exposed in the RF Exposure Analysis. This transmitter also meets the Portable requirements at distances equal or above those being reported in Minimum Separation Distances for SAR Evaluation Exemption.

This transmitter must not be co-located or operating in conjunction with any other antenna or transmitter except in accordance with FCC multi-transmitter product procedures.

OEM Responsibilities to Comply with FCC Regulations

This module has been tested for compliance to FCC Part 15.

OEM integrators are responsible for testing their end-product for any additional compliance requirements needed with this module installed (for example, digital device emissions, PC peripheral requirements, etc.)

Additionally, investigative measurements and spot-check testing (with all transmitters active, if other co-located radios than the module itself exist on the host), are strongly recommended in order to verify that the full system's compliance is maintained when the module is integrated, even with the module having a full modular approval, in accordance with the "Host Product Testing Guidance" in FCC's KDB 996369 D04 Module Integration Guide.

- **General Considerations**

  This transmitter module is tested as a subsystem and its certification does not cover the FCC Part 15 Subpart B (unintentional radiator) rule requirement, which is typically applicable to the final host. The final host will still need to be assessed for compliance to this portion of the rule requirements, if applicable.

- **Manual Information to the End User**

  The OEM integrator has to be aware not to provide information to the end-user regarding how to install or remove this RF module, or how to change RF related parameters, in the user's manual of the final product which integrates this module.

  The end user manual shall include all required regulatory information/warnings as shown in this manual.

- **Host Manufacturer Responsibilities**

  Host manufacturers are ultimately responsible for the full compliance of their host system. The final product is supposed to be assessed against all the essential requirements of the FCC rules, such as FCC Part 15 Subpart B, before it can be placed on the US market. This includes re-assuring the compliance of the radio transmitter with the RF and EMF essential requirements of the FCC rules. The modular radio transmitter must not be incorporated into any other radio-equipped device or system without retesting for compliance as multi-radio and combined equipment.

For more details about integrating the Single Modular Transmitter, refer to the following FCC document:

- KDB 996369 D04 Module Integration Guide

For understanding better the process leading to obtaining a Full Modular Approval, see the following documents instead:

- KDB 996369 D01 Transmitter Module Equipment Authorization Guide
- KDB 996369 D02 Frequently Asked Questions and Answers about Modules

The two documents above give an insight of the FCC requirements from the module manufacturer's perspective, and will help to realize the need by the integrators to follow the integration instructions and design guidance, and to take into account for example the RF Exposure limitations, if any. Should a deviation occur, keep in mind the possible need to work with the manufacturer in order to proceed with a permissive change (following a *Change in ID*), in accordance with the FCC guidelines found in the following documents:

- KDB 178919 D01 Permissive Change Policy
- KDB 178919 D02 Permissive Change Frequently-Asked Questions

Separation

- To meet the SAR exemption for portable conditions, the minimum separation distances indicated in Minimum Separation Distances for SAR Evaluation Exemption must be maintained between the human body and the radiator (antenna) at all times.
- This transmitter module is tested in a standalone RF Exposure condition, and in case of any co-located radio transmitter being allowed to transmit simultaneously, or in case of portable use at closer distances from the human body than those allowing the exceptions rules to be applied, a separate additional SAR evaluation, or a reduction in the max output power or in the duty-cycle, might be required for the host, ultimately leading to a Class II Permissive Change, or more rarely to a new grant.
- **Important Note:** In the event that the conditions for the exemption cannot be met, the final product will likely have to undergo additional testing to evaluate the RF Exposure, or go through some re-configuration of the max output power and/or duty-cycle in order for the FCC authorization to remain valid, and a permissive change will have to be applied. The SAR evaluation (and/or reconfiguration) is in the responsibility of the end-product's manufacturer, as well as the permissive change that can be carried out with the help of the customer's own Telecommunication Certification Body, following a *Change in ID* authorization by the module's original grant holder.

End Product Labeling

The SiW917Y1GA and SiW917Y1GN modules are labeled with their own FCC ID. In all those cases when the module's label is not visible, for example after the module becomes enclosed inside the end-product casing, or if the FCC ID is printed on the module's PCB silkscreen, then the outside of the device into which the module is installed must also have a label with a reference to the embedded module. In that case, the final product must be labeled in a visible area with the following:

"Contains Transmitter Module FCC ID: QOQ-917AC"

or

"Contains FCC ID: QOQ-917AC"

Final note:

As long as all the conditions in this and all the above chapters are met, further RF testing of the transmitter will not be strictly required. However, still consider the good practice and the FCC strong recommendation to ensure the compliance of the host by spot-checking. Nevertheless, the OEM integrator is still responsible for testing their end-product for any additional compliance requirements which might be mandatory with this module installed.

12.4 ISED - Canada

This radio transmitter (with IC: 5123A-917AC and PMN: *Bluetooth Low Energy and 802.11b/g/n/ax wireless radio module*) has been approved by *Innovation, Science and Economic Development Canada* (*ISED Canada*, formerly *Industry Canada*) to operate with the built-in integral antenna or with the external antenna type(s) listed in Qualified Antennas, having the maximum permissible gain indicated in the table. External antenna types not included in this list, or having a gain greater than the maximum gain listed, are strictly prohibited for use with this device.

This radio-equipped device complies with ISED's license-exempt RSS standards. Operation is subject to the following two conditions:

1. This device may not cause interference.
2. This device must accept any interference, including interference that may cause undesired operation of the device.

RF Exposure Statement

Exception from routine SAR evaluation limits are given in RSS-102 Issue 5.

The module meets the requirements for Mobile use cases when the minimum separation distance from the human body is 20 cm or greater, in accordance to the limit(s) exposed in the RF Exposure Analysis.

For Portable use cases, RF exposure or SAR evaluation is not required when the separation distances from the human body are equal or above those reported in Table 12.2 Minimum Separation Distances for SAR Evaluation Exemption on page 86.

If the separation distance from the human body is less than the values stated in Table 12.2 Minimum Separation Distances for SAR Evaluation Exemption on page 86, then the OEM integrator is responsible for evaluating the SAR with the end-product, or for the re-configuration of the radio module in the host in terms of lowering the max RF TX power and/or the duty-cycle. A permissive change would be required too, under the responsibility of the host manufacturer, following a *Multiple Listing* authorization by the module's original certificate holder.

OEM Responsibilities to comply with IC Regulations

The SiW917Y1GA and SiW917Y1GN modules have been certified for integration into products only by OEM integrators, under the following conditions:

- The module must be installed in such a way that the intended minimum separation distances are maintained between the radiator (antenna) and all persons at all times. Table 12.2 Minimum Separation Distances for SAR Evaluation Exemption on page 86 indicates the distances in accordance to the use cases.
- The transmitter module must not be co-located or operating in conjunction with any other antenna or transmitter.

Important Note: In the event that the above conditions cannot be met, the final product will have to undergo additional testing to evaluate the RF Exposure, or go through some re-configuration of the max output power and/or duty-cycle in order for the ISED authorization to remain valid; a permissive change will have to be applied too**.** The RF Exposure evaluation (SAR, or possibly a re-configuration) is in the responsibility of the end-product's manufacturer, as well as the permissive change that can be carried out with the help of the customer's own Telecommunication Certification Body, following a *Multiple Listing* authorization by the module's original certificate holder.

End Product Labeling

The SiW917Y1GA and SiW917Y1GN modules are labeled with their own IC ID. In all those cases when the module's label is not visible, for example after the module becomes enclosed inside the end-product casing, or if the IC ID is printed on the module's PCB silkscreen, then the outside of the device into which the module is installed must also have a label with a reference to the embedded module. In that case, the final product must be labeled in a visible area with the following:

“**Contains Transmitter Module IC: 5123A-917AC**”

or

“**Contains IC: 5123A-917AC**"

Final notes:

The OEM integrator has to be aware not to provide information to the end user regarding how to install or remove this RF module or change RF related parameters in the user manual of the end-product.

As long as all the conditions above are met, further transmitter testing will not be required. However, the OEM integrator is still responsible for testing their end-product for any additional compliance requirements required with this module installed (for example, digital device emissions, PC peripheral requirements, etc.)

ISED (Français)

Le présent émetteur radio (IC: 5123A-917AC, PMN: *Bluetooth Low Energy and 802.11b/g/n/ax wireless radio module*) a été approuvé par *Innovation, Sciences et Développement Économique Canada* (*ISED Canada*, anciennement *Industrie Canada*) pour fonctionner avec l'antenne intégrée et le ou les types d'antenne énumérés à la section Qualified Antennas, avec le gain maximal admissible indiqué. Les types d'antenne non inclus dans cette liste, ayant un gainsupérieur au gain maximal indiqué, sont strictement interdits d'utilisation avec cet appareil.

L'émetteur/récepteur exempt de licence contenu dans le présent appareil est conforme aux CNR d'Innovation, Sciences et Développement économique Canada applicables aux appareils radio exempts de licence. L'exploitation est autorisée aux deux conditions suivantes:

1. L'appareil ne doit pas produire de brouillage;
2. L'appareil doit accepter tout brouillage radioélectrique subi, même si le brouillage est susceptible d'en compromettre le fonctionnement.

Déclaration d'exposition RF

Les exceptions aux limites de l'évaluation SAR sont données dans le numéro 5 de la publication RSS-102.

Le module répond aux exigences pour les cas d'utilisation Mobile lorsque la distance minimale de séparation du corps humain est de 20 cm ou plus, conformément à la (aux) limite(s) exposée(s) dans l'analyse de l'exposition RF.

Pour les cas d'utilisation portables, l'évaluation de l'exposition RF ou l'évaluation SAR n'est pas requise lorsque les distances de séparation du corps humain sont égales ou supérieures à celles indiquées dans Table 12.2 Minimum Separation Distances for SAR Evaluation Exemption on page 86.

Si la distance de séparation du corps humain est inférieure aux valeurs indiquées dans Table 12.2 Minimum Separation Distances for SAR Evaluation Exemption on page 86, l'intégrateur OEM est responsable de l'évaluation du SAR avec le produit final, ou de la reconfiguration du module radio dans l'hôte en termes de réduction de la puissance RF TX maximale et/ou du rapport cyclique. Une modification permissive serait également nécessaire, sous la responsabilité du fabricant de l'hôte, suite à une autorisation de cotation multiple par le titulaire du certificat du module d'origine.

Responsabilités du fabricant de se conformer à la réglementation IC

Le module a été certifié pour l'intégration dans les produits uniquement par les intégrateurs OEM dans les conditions suivantes:

- Le module émetteur doit être installée de manière à maintenir une distance de séparation minimale, comme indiqué ci-dessus, entre le radiateur (antenne) et toutes les personnes à tout moment.
- Le module émetteur ne doit pas être localisé ou fonctionner conjointement avec une autre antenne ou un autre émetteur.

Remarque Importante: au cas où ces conditions ne pourraient pas être remplies, le produit final devra être soumis à des tests supplémentaires pour évaluer l'exposition RF, ou passer par une reconfiguration de la puissance de sortie maximale et/ou du rapport cyclique, afin que l'autorisation ISED reste valable; une modification permissive devra également être appliqué. L'évaluation de l'exposition aux radiofréquences (SAR, ou éventuellement une reconfiguration) est sous la responsabilité du fabricant du produit final, ainsi que le changement permissif qui peut être effectué avec l'aide de l'organisme de certification des télécommunications du client, après autorisation de cotation multiple par le titulaire de la certification du module.

Étiquetage des produits finis

Les modules SiW917Y1GA / SiW917Y1GN sont étiquetés avec leur propre IC ID. Dans tous ces cas, si l'ID IC n'est pas visible après l'installation du module à l'intérieur d'un autre appareil, alors l'extérieur de l'appareil dans lequel le module est installé doit également afficher une étiquette faisant référence au module inclus. Dans ce cas, le produit final doit être étiqueté dans une zone visible avec les éléments suivants:

"**Contient le module transmetteur IC: 5123A-917AC**"

ou

"**Contient IC: 5123A-917AC**"

Remarques finales:

L'intégrateur OEM doit être conscient de ne pas fournir à l'utilisateur final d'informations sur la procédure d'installation ou de retrait de ce module RF ni sur la modification des paramètres liés à la RF dans le manuel d'utilisation du produit final.

Tant que toutes les conditions ci-dessus sont remplies, aucun test supplémentaire de l'émetteur ne sera nécessaire. Toutefois, l'intégrateur OEM reste responsable de l'essai de son produit final pour déterminer les exigences de conformité supplémentaires requises avec ce module installé (par exemple, émissions d'appareils numériques, exigences relatives aux périphériques PC, etc.)

12.5 MIC - Japan

The SiW917Y1GA and SiW917Y1GN modules are certified in Japan with following certification number:

- 203-JN1379

While the module manufacturer takes all reasonable steps to prevent non-compliant operation, it is still the end-product manufacturer's responsibility to ensure that a module is configured to meet the compliance requirements, for example in relation to the maximum allowed RF TX power. When applicable, refer to the SDK documentation and/or API reference manuals and/or integration and certification guides, to learn how to configure (limit) the maximum RF TX power for ensuring the compliance of the end-product during regular operation, if need be. Refer as well to the power setting table(s) and measurements in the test report(s) in order to realize the maximum output power levels allowed for the regulatory compliance in Japan.

Manufacturers integrating a certified radio module into their host equipment are supposed to make the Technical Conformity Mark and the certification number visible on the outside of their device. This combination of mark and number, and their relative placement, is depicted in the Figure 12.1 Example of "Giteki" Mark with Placeholder for Actual Certification Number on page 82 below, and depending on the overall size it might also appear among the top shield markings of the radio module. The Technical Conformity Mark and the certification number must be placed close to the text in the Japanese language which is provided below. This requirement in the Radio Law has been made in order to enable users of the combination of host and radio module to verify if they are actually using a radio-equipped device which is approved for use in Japan.

Certification text to be placed on the outside surface of the host equipment:

当該機器には電波法に基づく、技術基準適合証明等を受けた特定無線設備を装着している。

Translation of the text:

“This equipment contains specified radio equipment that has been certified to the Technical Regulation Conformity Certification under the Radio Law.”

The "Giteki" Technical Conformity Mark, together with the actual module's certification number, as shown in the following example figures, must be affixed to an easily noticeable section of the specified radio-enabled host equipment. Notice that such section may be required to contain additional information if the end-device embedding the module is also subject to a Telecom approval.

The manufacturer of the final product is also responsible to provide a Japanese language version of the User Manual and/or Installation Instructions as a companion document coming with the final product when placed on the market in Japan. Such a document will have to mention the integrated radio component and the related certification information.

Figure 12.1. Example of "Giteki" Mark with Placeholder for Actual Certification Number

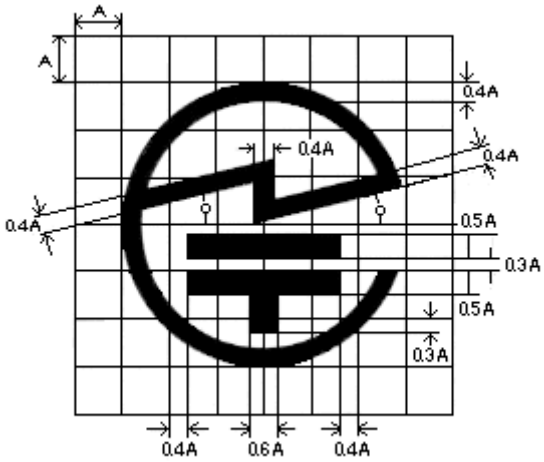


Figure 12.2. Detail of "Giteki" Technical Conformity Mark

12.6 KC - South Korea

The SiW917Y1GA and SiW917Y1GN modules have a RF registration for import and use in South Korea.

Registration number is KC ID: R-R-BGT-917AC

These modules are meant to be integrated into end-products, which then become exempted from doing the RF emission testing, as long as the recommended design guidance is followed, and as long as, where applicable, the approved external antennas are used and any additional transmit power backoff is implemented in accordance to the measurements and configurations seen in the formal test report(s).

EMC testing and any other relevant test applicable to the end-product as a whole, plus appropriate labeling of the end-product, might still be required for the full regulatory compliance in the country.

12.7 NCC - Taiwan

The SiW917Y1GA and SiW917Y1GN modules are certified in Taiwan with NCC certification numbers as follows:

SiW917Y1GA 和 SiW917Y1GN 模組已在台灣獲得認證，NCC 認證編號如下：

SiW917Y1GA: CCAL25Y10200T5

SiW917Y1GN: CCAL25Y10201T7

Manufacturers are required to mark their end-products with the following sentence: *"This product contains a radio frequency module with certification number CCAL25Y1020xTx"*, where CCAL25Y1020xTx corresponds to the above-listed certification number of the embedded module.

系統製造商應在平台上放置以下聲明：“本產品包含認證編號為 CCAL25Y1020xTx 的無線電模組”，其中 CCAL25Y1020xTx 對應於上面列出的嵌入式模組的認證編號。

Note: The outer packaging of the final product must also be marked with the NCC conformity mark by the manufacturer.

注意：最終產品的外包裝也必須由製造商打上 NCC 合格標誌。

Additionally, the final product will have to be listed in the NCC database of approved radio-equipped devices. Consequently, the end manufacturer is also supposed to contact a certification body or the certification house that originally released the modular approval and apply for the registration of their platform under the applicable certification number above. Fees might apply, and an authorization by the module manufacturer might be required too.

此外，最終產品必須列入 NCC 的核准無線電設備資料庫中。因此，最終製造商也應聯繫最初協助頒發模組化核准的認證機構或認證公司，並申請在上述適用的認證編號下註冊其平台。可能需要列出費用和模組製造商的授權。

NCC Statement
- For low-power radio frequency equipment that has been certified, companies, firms, or users are not allowed to change the frequency, increase the power, or change the characteristics and functions of the original design without further NCC approval. - The use of low-power radio frequency equipment shall not affect flight safety and interfere with legal communications. - If interference is found, it shall be immediately stopped, and the equipment can be brought back into use only after it has been improved, so that interference is found no more. - The aforementioned legal communication refers to radio communications operating in accordance with the provisions of the Telecommunications Management Act. - Low-power radio frequency equipment must withstand interference from legitimate communications or radiating electrical equipment for industrial, scientific, and medical applications.
NCC 警語
取得審驗證明之低功率射頻器材，非經核准，公司、商號或使用者均不得擅自變更頻率、加大功率或變更原設計之特性及功能。 低功率射頻器材之使用不得影響飛航安全及干擾合法通信。 經發現有干擾現象時，應立即停用，並改善至無干擾時方得繼續使用。 前述合法通信，指依電信管理法規定作業之無線電通信。 低功率射頻器材須忍受合法通信或工業、科學及醫療用電波輻射性電機設備之干擾。

12.8 SRRC - China

The SiW917Y1GA module has a full modular radio type approval for re-use by the OEM integrators:

Certificate No.: 2025-9477

CMIIT ID: 25J99MY6Q954

The SiW917Y1GN module has a limited modular radio type approval for re-use by the OEM integrators:

Certificate No.: 2025-9493

CMIIT ID: 25J99MY60583(M)

Note for modules with a full modular approval: every end-product integrating the module must be labeled with the following statement (alternatively, in case of lack of space, the statement will have to go to the end-product's user manual):

本设备包含一个无线电发射器模块，型号核准代码为：CMIIT ID：25J99MY6Q954

(Translation: *"This equipment contains a radio transmitter module with type approval code: CMIIT ID: 25J99MY6Q954"*)

SRRC – 中国

SiW917Y1GA 模塊具有完整的模塊化認證，可供 OEM 集成商重複使用：

认证编号：2025-9477

CMIIT ID : 25J99MY6Q954

SiW917Y1GN 模塊具有有限的模塊化認證，可供 OEM 集成商重複使用：

认证编号：2025-9493

CMIIT ID : 25J99MY60583(M)

具有完全模塊化批准的模塊注意事項：以下聲明必須出現在嵌入模塊的最終產品的標籤和/或用戶手冊中：

本设备包含一个无线电发射器模块，型号核准代码为：CMIIT ID：25J99MY6Q954

12.9 ACMA - Australia

The SiW917Y1GA and SiW917Y1GN modules are in compliance with the Australian RCM requirements, and are labelled with the RCM Compliance Mark. The formal Declaration of Conformity (DoC) is available at www.silabs.com. With the DoC and RCM compliance mark, the modules are also covered for the use in New Zealand (RSM).

12.10 RF Exposure and Proximity to Human Body

When using the SiW917Y1GA and SiW917Y1GN modules in an application where the radio-equipped end-product is located close to the human body, the human RF Exposure must be taken into account. FCC, ISED, and CE/UKCA all have different standards and rules for evaluating the RF Exposure. In particular, each regulator has different requirements when it comes to the exemption from having to perform RF Exposure evaluation and/or SAR (Specific Absorption Rate) measurements, and the minimum separation distances between the module's antenna and the human body varies accordingly. The properties of the SiW917Y1GA and SiW917Y1GN modules allow the minimum separation distances detailed in Table 12.2 Minimum Separation Distances for SAR Evaluation Exemption on page 86 for the SAR measurement exemption in the Portable use cases (less than 20 cm from the human body). These modules are approved for the Mobile use case (more than 20 cm) without any need for RF Exposure evaluation.

Table 12.2. Minimum Separation Distances for SAR Evaluation Exemption

Certification	SiW917Y1GA	SiW917Y1GN
FCC	BLE: 22 mm 802.11b/g/n/ax: 37 mm All protocols in use (overall): 37 mm	BLE: 23 mm 802.11b/g/n/ax: 39 mm All protocols in use (overall): 39 mm
ISED	BLE: 30 mm 802.11b/g/n/ax: 45 mm All protocols in use (overall): 45 mm	BLE: 30 mm 802.11b/g/n/ax: 45 mm All protocols in use (overall): 45 mm
CE / UKCA	The RF exposure should always be evaluated with the end-product when transmitting with EIRP power levels higher than 20 mW (13 dBm) while operating at distances closer than 20 cm from the human body. With the SiW917Y1GA and SiW917Y1GN modules, this is the case only with the 802.11b/g/n/ax protocols transmitting at full power. In all other cases, modules are inherently in compliance with the requirements of the relevant standard(s), given the condition that the max RF TX output power levels are below the exclusion limits at all times.	

The exemption minimum distances above, calculated for reference in the full output power use-case, are based on the rules in force at the time of originally writing this data sheet. Even though changes happen rarely, always ensure to apply the rules in force at the time of placing the end-product into the market.

In the cases of FCC and ISED, it is allowed to use a module at its max RF TX power in an end-product where the typical separation distance from the human body is smaller than mentioned above, but it requires evaluating the RF Exposure in the final assembly and applying for a *Class 2 Permissive Change* to the FCC and ISED approvals of the module. In order to proceed with the permissive changes, first the module manufacturer should be asked for an authorization to do an FCC's *Change in ID* and an ISED's *Multiple Listing*; then, the new Portable condition will be added to the new parallel grants owned by the end-product manufacturer, for extending the approvals to their unique host under their unique configuration and mode of use.

For those end-products where the embedded module is configured to implement only a single wireless protocol which would allow for the exemption at a shorter distance than the overall minimum distance, there would be no need the evaluate the RF Exposure at such a shorter distance and above. However, a permissive change would still be needed as a mean to notify the FCC / ISED of the reason why in the field the module is allowed to operate at a shorter distance than the overall minimum distance in Table 12.2 Minimum Separation Distances for SAR Evaluation Exemption on page 86.

An example of another use case where the module could operate at a shorter distance than in Table 12.2 Minimum Separation Distances for SAR Evaluation Exemption on page 86, without having to do the RF Exposure evaluation / SAR measurement, is when the power or the duty-cycle is reduced during normal operation. However, the new minimum distance for the exemption should be re-calculated, and still a permissive change would be needed to notify the regulators of the new conditions.

For the CE/UKCA compliance, RF Exposure must be considered and evaluated by the OEM in all cases (if any) when the end-product is transmitting at higher power level than indicated in Table 12.2 Minimum Separation Distances for SAR Evaluation Exemption on page 86.

Note: Placing the module in touch or very close to the human body will have a negative impact on the efficiency of the antenna thus a reduced range is to be expected.

12.11 Bluetooth Qualification

The SiW917Y1GA and SiW917Y1GN modules have the following Qualified Products with corresponding Qualified Design Identification (QDID) based on the Bluetooth Core Specification 5.4:

1. **QDID 230044**
   - This Core Layer Design is for the Low Energy RF-PHY Radio interface.
2. **QDID 226688**
   - This Core Layer Design is for Host Controller Interface and Low Energy Link Layer.
3. **QDID 227553**
   - This Core-Controller Configuration Design combines the above QDID 230044 and QDID 226688. It encompasses the Low Energy RF-PHY Radio interface and the Low Energy Link Layer, plus the Host Controller Interface, for easier integration when doing a Core-Complete Configuration Design in order to make a Product.

13. Documentation and Support

Silicon Labs offers a set of documents which provide further information required for evaluating, and developing products and applications using SiWN917. These documents will be available on the Silicon Labs website. The documents include information related to Software releases, Evaluation Kits, User Guides, Programming Reference Manuals, Application Notes, and others.

For further assistance, you can contact Silicon Labs Technical Support here.

Resource Location

SiWN917 Document Library : https://docs.silabs.com/wiseconnect/latest/wiseconnect-developing-with-wiseconnect-sdk/

Technical Support : http://www.silabs.com/support/

14. Revision History

Revision 1.1

December, 2025

- Added Host Interface Peripherals information in 1. Feature List.
- Updated key features in 5.3 Bluetooth and 1. Feature List.
- Added 5.5 Host Interfaces and 5.5.1 Auto Host Detection.
- Added 7.4.4 UART.
- Updated 8.1.3 GPIO Connection and 8.2.3 GPIO Connection.
- Updated 8.1.6 Flash Memory Configurations and 8.2.6 Flash Memory Configurations.
- Updated Figure 9.3 PCB Landing Pattern on page 71 to include an additional keep-out area.
- Added certification details:
  - KC (South Korea) — 12.6 KC - South Korea
  - SRRC (China) — 12.8 SRRC - China

Revision 1.0

June, 2025

- Version updated fron 0.7 to 1.0
- Updated Cover page: KEY FEATURES are updated.
- Updated 1. Feature List: Following sub-sections features are updated:
  - Memory
  - Security
  - Wi-Fi
  - Intelligent Power Management
  - Software and Regulatory Certifications
  - Bluetooth
  - Embedded Wi-Fi Stack
  - Wireless Sub-system Power Consumption
  - Operating Conditions
- Updated 2. Ordering Information: Table 2.1 Orderable Part Number (OPN) Decoder on page 4 and Table 2.2 Part Ordering Options on page 5 are updated.
- Updated 3. Applications: Details in "Other Applications (Medical, Industrial, Retail, Agricultural, Smart City, etc.)" are updated.
- Updated the following in 5. System Overview
  - 5.3 Bluetooth Key features are updated.
    - 5.3.2 Baseband Processing: Details are updated.
  - 5.8 Power Architecture: 5.8.1 Highlights are updated.
  - 5.10 Low Power Modes: 5.10.1 ULP Mode details are updated.
- Updated the following in 6. Pinout and Pin Description
  - 6.2.3 Peripheral Interfaces: Table 6.4 Chip Packages - Peripheral Interfaces on page 20 is updated.
- Updated the following in 7. Electrical Specifications
  - 7.1 Absolute Maximum Ratings: Updated Table 7.1 Absolute Maximum Ratings on page 27.
  - 7.2 Recommended Operating Conditions: Updated Table 7.2 Recommended Operating Conditions on page 28.
  - 7.3.1 RESET_N Pin and POC_IN Pins: Updated Table 7.3 RESET_N Pin and POC_IN Pins on page 28
  - 7.3.2 Power On Control (POC) and Reset: Updated the content.
  - Added: 7.3.3 Thermal Characteristics.
  - 7.4.1.1 Low Frequency Clock: Updated Table 7.7 32 kHz RC Oscillator on page 32 and Table 7.8 32.768 kHz External Oscillator Specifications on page 32.
  - Added: 7.4.1.2 High- Frequency Crystal (HFXO).
  - 7.5 RF Characteristics: All the sub-sections and their respective tables are updated. All the parameter values are updated in the respective table.
  - 7.6 Typical Current Consumption: Following are the updates:
    - 7.6.1 WLAN 2.4 GHz: Table 7.27 WLAN 2.4 GHz 3.3 V Current Consumption on page 49 is updated.
    - 7.6.2 Bluetooth LE: Table 7.28 Bluetooth LE Current Consumption on page 50 is updated.
- Updated the following in 8. Reference Schematics, BOM, and Layout Guidelines:
  - 8.1 SiW917Y1GN Schematics for Parts with RF Pin: Following are the updates:
    - All the figures are updated in this section with additional details
    - 8.2.8 Bill of Materials: Table 8.2 Bill of Materials on page 59 complete table is updated.
  - 8.4 SiW917Y1GA Antenna Radiation and Efficiency: Following are the updates:
    - All the figures are updated in this section with additional details
    - 8.2.8 Bill of Materials: Table 8.2 Bill of Materials on page 59 complete table is updated.
  - 8.3 Layout Guidelines: Following are the updates:
    - 8.3.2 Installation Guide for SiW917Y1GA Module: Updated content in the paragraph "Antennas are by……(See the 8.4.2 Proximity to Human Body note below.)".
  - 8.4 SiW917Y1GA Antenna Radiation and Efficiency: Updated Table 8.3 Antenna Efficiency and Peak Gain on page 64.
- Updated the following in 9. Package Specifications:
  - 9.1 Dimensions: Table 9.1 Module Dimensions on page 68 is updated. The value of Module Dimensions parameter is updated to 21.10 x 16 x 2.30 respectively.
- Updated 11. Tape and Reel: The cut tape and reels packaging values are updated to 1000 pcs and 700pcs respectively.

Revision 0.7

November, 2024

- Updated Cover page
- Updated 1. Feature List
- Updated 3. Applications
- Removed Host Interfaces
- Updated 6.2 Pin Description
- Updated 6.2.3 Peripheral Interfaces
- Updated the following Electrical Specifications:
  - 7.1 Absolute Maximum Ratings
  - 7.2 Recommended Operating Conditions
  - 7.3.1 RESET_N Pin and POC_IN Pins
  - 7.3.2 Power On Control (POC) and Reset
  - 7.3.4 Digital I/O Signals
  - 7.4.2 SDIO 2.0 Secondary
  - 7.4.3 HSPI Secondary
  - Removed UART
  - 7.4.5 GPIO Pins
  - 7.4.6 In-Package Flash Memory
  - Removed SGPIO/MC-PWM/QEI/SCT Timer/SIO Interfaces and USART
- Added Note to 8.4.2 Proximity to Human Body

Revision 0.52

October, 2024

- Updated Notes for 1. Feature List
- Updated 2. Ordering Information
- Reformatted all the tables in Section
- Updated Section 7.5 RF Characteristics
- Updated Table 12.2 Minimum Separation Distances for SAR Evaluation Exemption on page 86
- Updated 12.11 Bluetooth Qualification

Revision 0.5

June, 2024

- Updated Features List
- Updated Ordering Information
- Updated Block Diagrams
- Updated System Overview
- Updated Pin Definitions
- Updated Electrical Specifications
- Updated Reference Schematics, BOM and Layout Guidelines
- Added Certifications

Revision 0.1

September, 2023

- Preliminary version.

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